MC33772C

Battery cell controller IC

Rev. 4.0 — 16 July 2024

Product data sheet



1 General description

The MC33772C is a SMARTMOS lithium-ion battery cell controller IC designed for automotive applications, such as hybrid electric (HEV) and electric vehicles (EV) along with industrial applications, such as energy storage systems (ESS) and uninterruptible power supply (UPS) systems.

The device performs ADC conversions of the differential cell voltages and current, as well as battery coulomb counting and battery temperature measurements. The information is transmitted to MCU using one of the microcontroller interfaces: serial peripheral interface (SPI) or isolated daisy chain communication interface [also referred as transformer physical layer (TPL)] which supports both capacitive and inductive isolation between nodes of the IC. The product is AEC-Q100 qualified and operates up to 125 °C ambient temperature.

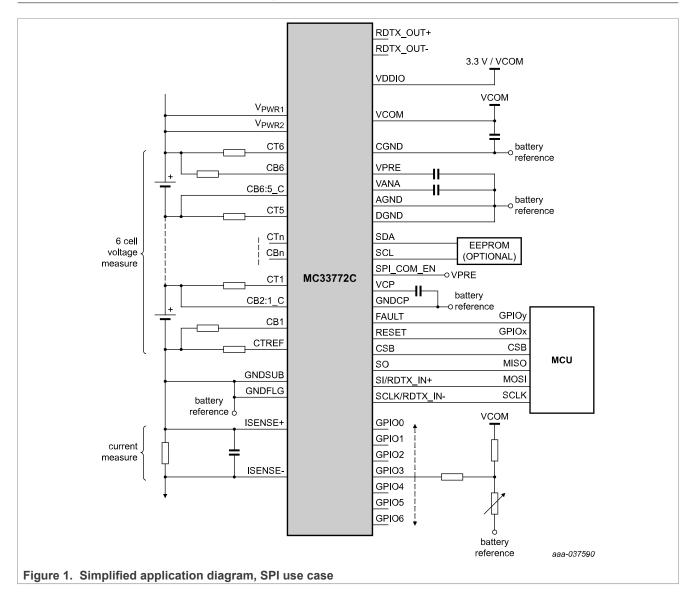
2 Features

- 5.0 V ≤ V_{PWR} ≤ 30 V operation, 40 V transient
- 3 to 6 cells management
- · Isolated 2.0 Mbit/s differential communication or 4.0 Mbit/s SPI
- · Addressable on initialization
- Bi-directional transceiver to support up to 63 nodes in daisy chain
- · 0.8 mV total voltage measurement error
- · Synchronized cell voltage/current measurement with coulomb count
- Averaging of cell voltage measurements
- · Total stack voltage measurement
- Seven GPIO/temperature sensor inputs
- 5.0 V at 5.0 mA reference supply output
- · Automatic over/undervoltage and temperature detection routable to fault pin
- Integrated sleep mode over/undervoltage and temperature monitoring
- Onboard 300 mA passive cell balancing with diagnostics
- · Hot plug capable
- Detection of internal and external faults, as open lines, shorts, and leakage
- Designed to support ISO 26262, up to ASIL D safety system
- Fully compatible with the MC33771C and the MC33664
- Qualified in compliance with AEC-Q100

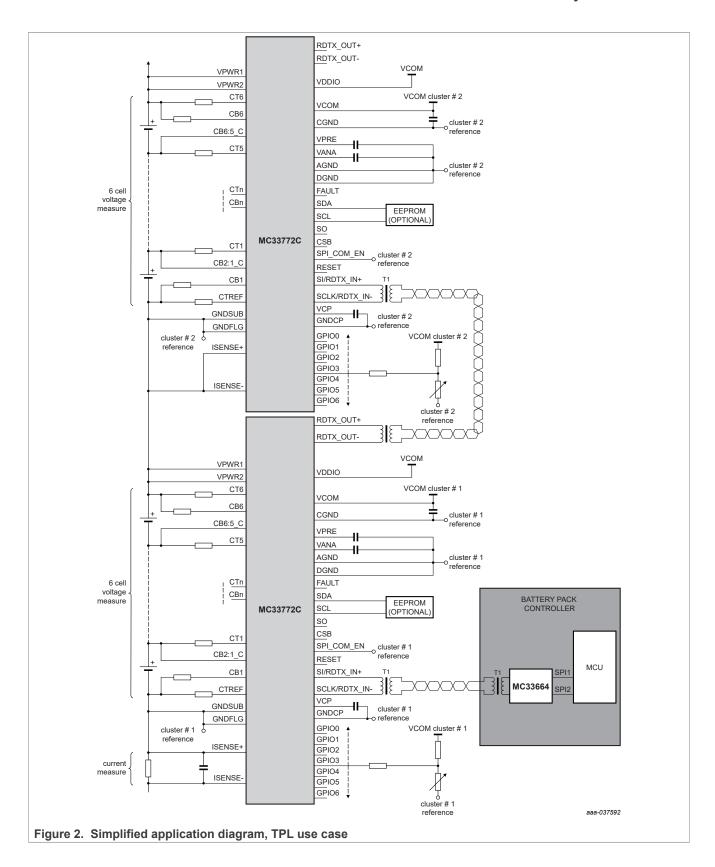


Battery cell controller IC

3 Simplified application diagram



Battery cell controller IC



Battery cell controller IC

4 Applications

- Automotive: 12 V and high-voltage battery packs
- E-bikes, e-scooters, drones
- Energy storage systems
- Uninterruptible power supply (UPS)
- Battery junction box

5 Ordering information

5.1 Part numbers definition

MC33772C \underline{x} \underline{y} \underline{z} AE/R2

Table 1. Part number breakdown

Code	Option	Description
Х	Т	x = T (TPL communication type)
	А	y = A (Advanced)
у	С	y = C (Current)
	Р	y = P (Premium)
	0	z = 0 (0 channels)
z	1	z = 1 (3 to 6 channels)
	2	z = 2 (3 to 4 channels)
	AE	Package suffix
	R2	Tape and reel indicator

Battery cell controller IC

5.2 Part numbers list

This section describes the part numbers available to be purchased along with their differences. Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to http://www.nxp.com.

Table 2. Advanced orderable part table

Package type is 48-pin LQFP-EP

Orderable part	Number of channels	OV/UV	Precision GPIO as temperature channels and OT/UT	Current channel or coulomb count
TPL differential com	munication protoc	ol		
MC33772CTA1AE	3 to 6	Yes	Yes	No
MC33772CTA2AE	3 to 4	Yes	Yes	No

Table 3. Premium orderable part table

Package type is 48-pin LQFP-EP

Orderable part	Number of channels	OV/UV	Precision GPIO as temperature channels and OT/UT	Current channel or coulomb count
TPL differential com	munication protoc	ol with current n	neasurement option	
MC33772CTP1AE	3 to 6	Yes	Yes	Yes
MC33772CTP2AE	3 to 4	Yes	Yes	Yes

Table 4. Current orderable part table

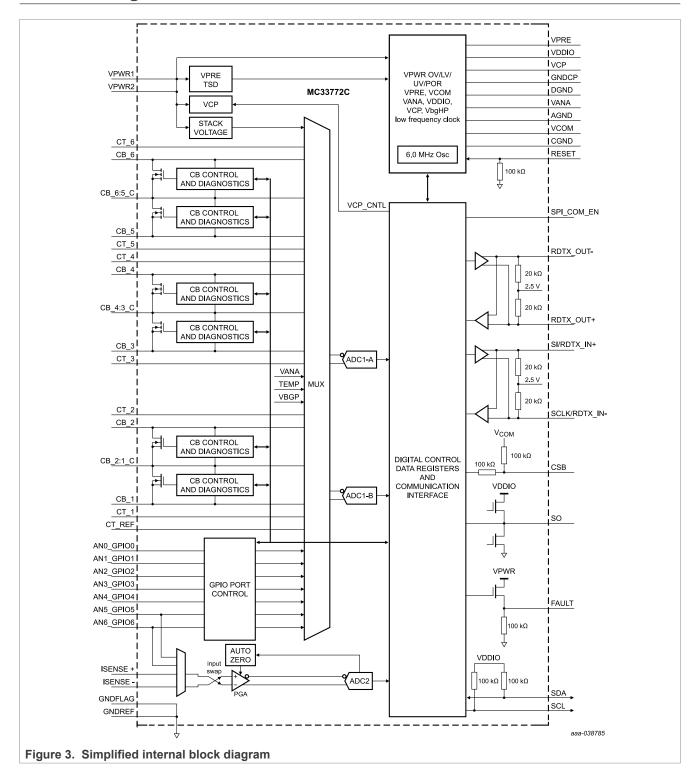
Package type is 48-pin LQFP-EP

Orderable part	Number of channels	OV/UV		Current channel or coulomb count
TPL differential com	munication protoc	ol		
MC33772CTC0AE	0	No	Yes	Yes
MC33772CTC1AE	1	No	Yes	Yes

Note: To order parts in tape and reel, add an R2 suffix to the part number.

Battery cell controller IC

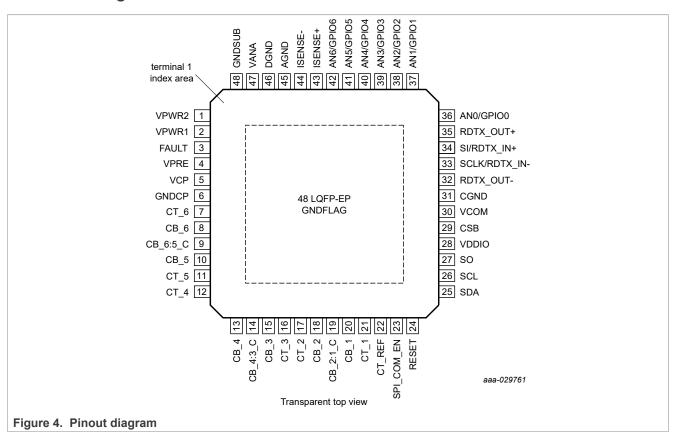
6 Block diagram



Battery cell controller IC

7 Pinning information

7.1 Pinout diagram



7.2 Pin definitions

Table 5. Pin definitions

Pin number	Pin name	Pin function	Definition
1	VPWR2	Input	Power supply input to the MC33772C
2	VPWR1	Input	Power supply input to the MC33772C
3	FAULT	Output	Fault output dependent on user defined internal or external faults. If not used, it must be left open
4	VPRE	Output	Pre-regulator voltage. Connect to a 470 nF capacitor
5	VCP	Output	Charge pump. Decouple with a 10 nF capacitor
6	GNDCP	Ground	Charge pump capacitor ground
7	CT_6	Input	Cell terminal pin 6 input. Terminate to LPF resistor
8	CB_6	Output	Cell balance driver. Terminate to cell 6 cell balance load resistor
9	CB_6:5_C	Output	Cell balance 6:5 common. Terminate to cell 6 and 5 common pin
10	CB_5	Output	Cell balance driver. Terminate to cell 5 cell balance load resistor
11	CT_5	Input	Cell terminal pin 5 input. Terminate to LPF resistor
12	CT_4	Input	Cell terminal pin 4 input. Terminate to LPF resistor
13	CB_4	Output	Cell balance driver. Terminate to cell 4 cell balance load resistor

MC33772C

All information provided in this document is subject to legal disclaimers.

Battery cell controller IC

Table 5. Pin definitions...continued

Pin number	Pin name	Pin function	Definition
14	CB_4:3_C	Output	Cell balance 4:3 common. Terminate to cell 4 and 3 common pin
15	CB_3	Output	Cell balance driver. Terminate to cell 3 cell balance load resistor
16	CT_3	Input	Cell terminal pin 3 input. Terminate to LPF resistor
17	CT_2	Input	Cell pin 2 input. Terminate to LPF resistor
18	CB_2	Output	Cell balance driver. Terminate to cell 2 cell balance load resistor
19	CB_2:1_C	Output	Cell balance 2:1 common. Terminate to cell 2 and 1 common pin
20	CB_1	Output	Cell balance driver. Terminate to cell 1 cell balance load resistor
21	CT_1	Input	Cell pin 1 input. Terminate to LPF resistor
22	CT_REF	Input	Cell terminal REF input. Terminate to LPF resistor
23	SPI_COM_EN	Input	SPI communication enable input. Wire to VPRE to use SPI communication, else wire to ground to use TPL communication
24	RESET	Input	RESET is an active high input. RESET has an internal pull down. If not used, it can be shorted to GND
25	SDA	I/O	I ² C data
26	SCL	I/O	I ² C clock
27	SO	Output	SPI serial output
28	VDDIO	Input	IO voltage for I ² C and SPI interfaces. Voltage level corresponding to logic 1 will be the same as VDDIO
29	CSB	Input	SPI active low chip select. If not used, it must be shorted to ground
30	VCOM	Output	Communication regulator output. Decouple with 2.2 µF to CGND
31	CGND	Ground	Communication decoupling ground, terminate to GNDSUB
32	RDTX_OUT-	I/O	TPL receive/transmit output negative
33	SCLK/RDTX_IN-	I/O	SPI clock or TPL receive/transmit input negative
34	SI/RDTX_IN+	I/O	SPI serial input or TPL receive/transmit input positive
35	RDTX_OUT+	I/O	TPL receive/transmit output positive
36	AN0 GPIO0	I/O	General purpose input/output
37	AN1 GPIO1	I/O	General purpose input/output
38	AN2 GPIO2	I/O	General purpose input/output
39	AN3 GPIO3	I/O	General purpose input/output
40	AN4 GPIO4	I/O	General purpose input/output
41	AN5 GPIO5	I/O	General purpose input/output
42	AN6 GPIO6	I/O	General purpose input/output
43	ISENSE+	Input	Current measurement input +
44	ISENSE-	Input	Current measurement input -
45	AGND	I/O	Analog ground, terminate to GNDSUB
46	DGND	I/O	Digital ground, terminate to GNDSUB
47	VANA	Output	Precision ADC analog supply. Decouple with 47 nF capacitor to AGND
48	GNDSUB	Ground	Ground reference for device, terminate to reference of battery cluster
49	GNDFLAG	Ground	Exposed pad, terminate to lowest potential of the battery cluster and to heat dissipation area of PCB

Battery cell controller IC

8 General product characteristics

8.1 Ratings and operating requirements relationship

The operating voltage range pertains to the VPWR pins referenced to the AGND pins.

Table 6. Ratings vs. operating requirements

Fatal range	Lower limited operating range	Normal operating range	Upper limited operating range	Fatal range
Permanent failure may occur	No permanent failure, but IC functionality is not guaranteed	100 % functional		Permanent failure may occur
V _{PWR} < -0.3 V	5.0 V ≤ V _{PWR} ≤ 6.0 V (SPI)	6.0 V ≤ V _{PWR} ≤ 30 V (SPI)	30 V < V _{PWR} ≤ 40 V	40 V < V _{PWR}
	$6.4 \text{ V} \le \text{V}_{PWR} \le 7.0 \text{ V (TPL)}$	$7.0 \text{ V} \le \text{V}_{\text{PWR}} \le 30 \text{ V (TPL)}$		
	Reset range:		IC parameters	
	$-0.3 \text{ V} \le \text{V}_{PWR} \le 5.0 \text{ V (SPI)}$		might be out of	
	$-0.3 \text{ V} \le \text{V}_{PWR} \le 6.4 \text{ V (TPL)}$		specification. Detection of V _{PWR}	
	POR with V _{PWR} falling:		overvoltage is	
	4.8 V ≤ V _{PWR} < 5.0 V (SPI)		functional	
	6.1 V ≤ V _{PWR} < 6.4 V (TPL)			
	POR with V _{PWR} rising:			
	$5.6 \text{ V} \le \text{V}_{PWR} < 6.0 \text{ V (SPI)}$			
	6.6 V ≤ V _{PWR} < 7.0 V (TPL)			
	Handling ra	ange - No permanent failure		

In both upper and lower limited operating range, no information can be provided about IC performance. Only the detection of V_{PWR} overvoltage is guaranteed in the upper limited operating range.

Performance in normal operating range is guaranteed only if there is a minimum of three battery cells in the stack.

8.2 Maximum ratings

Table 7. Maximum ratings

All voltages are with respect to ground unless otherwise noted. Exceeding these ratings might cause a malfunction or permanent damage to the device.

Symbol	Description (rating)	Min	Max	Unit
Electrical ratings				
VPWR1, VPWR2	Supply input voltage	-0.3	40	V
СТ6	Cell terminal voltage	-0.3	40	V
VPWR to CT6	Voltage across VPWR1,2 pins pair and CT6 pin	-10	10	V
CT _N to CT _{N-1}	Cell terminal differential voltage [1]	-0.3	6.7	V
CT _{N(CURRENT)}	Cell terminal input current	_	±500	μA
CB _N to CB _{N:N-1_C} CB _{N:N-1_C} to CB _{N-1}	Cell balance differential voltage	_	10	V
CB _{N-1} to CT _{N-1}	Cell balance input to cell terminal input	-10	+10	V
VISENSE	ISENSE+ and ISENSE– pin voltage	-0.5	2.5	V
VCOM	Maximum voltage may be applied to VCOM pin from external source	_	5.8	V
VANA	Maximum voltage may be applied to VANA pin	_	3.1	V

MC33772C

All information provided in this document is subject to legal disclaimers.

© 2024 NXP B.V. All rights reserved.

Document feedback

Battery cell controller IC

Table 7. Maximum ratings...continued

All voltages are with respect to ground unless otherwise noted. Exceeding these ratings might cause a malfunction or permanent damage to the device.

Symbol	Description (rating)	Min	Max	Unit
VPRE	Maximum voltage which may be applied to VPRE pin from external source	_	7.0	V
VCP	Maximum voltage which may be applied to VCP pin from external source	_	14	V
VDDIO	Maximum voltage which may be applied to VDDIO pin from external source	_	5.8	V
V _{GPIO0}	GPIO0 pin voltage	-0.3	6.5	V
V _{GPIOx}	GPIOx pins (x = 1 to 6) voltage	-0.3	VCOM + 0.5	V
V_{DIG}	Voltage I ² C pins (SDA, SCL)	-0.3	VDDIO + 0.5	V
V _{RESET}	RESET pin	-0.3	6.5	V
V _{CSB}	CSB pin	-0.3	6.5	V
V _{SPI_COMM_EN}	SPI_COMM_EN	-0.3	7.0	V
V _{SO}	SO pin	-0.3	VDDIO + 0.5	V
V _{GPIO5,6}	Maximum voltage for GPIO5 and GPIO6 pins used as current input	-0.3	2.5	V
FAULT	Maximum applied voltage to pin	-0.3	7.0	V
I _{pin_unpowered}	Input current in a pin when the device is unpowered	-2	2	mA
V _{COMM}	Maximum voltage to pins RDTX_OUT+, RDTX_OUT-, SI/RDTX_IN+, CLK/RDTX_IN-	-10	10	V
V _{ESD1}	ESD voltage Human body model (HBM) Charge device model (CDM) Charge device model corner pins (CDM)	_ _ _	±2000 ±500 ±750	V
V _{ESD2}	ESD voltage (VPWR1, VPWR2, CTx, CBx, GPIOx, ISENSE+, ISENSE-, RDTX_OUT+, RDTX_OUT-, SI/RDTX_IN+, SCLK/ RDTX_IN-) Human body model (HBM)	[2]	±4000	V
V _{ESD3}	ESD voltage (CTREF, CTx, CBx, GPIOx, ISENSE+, ISENSE-, RDTX_OUT+, RDTX_OUT-, SI/RDTX_IN+, SCLK/ RDTX_IN-) IEC 61000-4-2, Unpowered (Gun configuration: $330~\Omega$ / $150~pF$) HMM, Unpowered (Gun configuration: $330~\Omega$ / $150~pF$) ISO 10605:2009, Unpowered (Gun configuration: $2~k\Omega$ / $150~pF$) ISO 10605:2009, Powered (Gun configuration: $2~k\Omega$ / $330~pF$)	[3] — — —	±8000 ±8000 ±8000 ±8000	V

Adjacent CT pins may experience an overvoltage that exceeds their maximum rating during OV/UV functional verification test or during open line [1] diagnostic test. Nevertheless, the IC is completely tolerant to this special situation.

ESD testing is performed in accordance with the human body model (HBM) (C_{ZAP} = 100 pF, R_{ZAP} = 1500 Ω). These voltage values can be sustained only if ESD caps are used as described in Section 13.2.

Battery cell controller IC

8.3 Thermal characteristics

Table 8. Thermal ratings

All voltages are with respect to ground unless otherwise noted. Exceeding these ratings might cause a malfunction or permanent damage to the device.

Symbol	Description (rating)		Min	Max	Unit
Thermal ratin	ngs				
	Operating temperature				°C
T _A	Ambient (SPI application)		-40	+125	
T _A	Ambient (TPL application)		-40	+105	
T_J	Junction ^[1]		-40	+150	
T _{STG}	Storage temperature		-55	+150	°C
T _{PPRT}	Peak package reflow temperature	[2] [3]	_	260	°C
Thermal resis	stance and package dissipation ratings				
R _{OJB}	Junction-to-board (bottom exposed pad soldered to board) 48 LQFP EP	[4]	_	11	°C/W
$R_{\Theta JA}$	Junction-to-ambient, natural convection, single-layer board (1s) 48 LQFP EP	[5] [6]	_	72	°C/W
R _{⊝JA}	Junction-to-ambient, natural convection, four-layer board (2s2p) 48 LQFP EP	[5] [6]	_	30	°C/W
R _{OJCTOP}	Junction-to-case top (exposed pad) 48 LQFP EP	[7]	_	24	°C/W
R _{OJCBOTTOM}	Junction-to-case bottom (exposed pad) 48 LQFP EP	[8]	_	0.98	°C/W
ΨJT	Junction to package top, natural convection	[9]	_	4	°C/W

- [1] The user must ensure that the average maximum operating junction temperature (Tj) is not exceeded.
- [2] Pin soldering temperature limit is for 10 seconds maximum duration. Not designed for immersion soldering. Exceeding these limits may cause a malfunction or permanent damage to the device.
- [3] NXP's Package Reflow capability meets Pb-free requirements for JEDEC standard J-STD-020C. For Peak Package Reflow Temperature and Moisture Sensitivity Levels (MSL), go to www.nxp.com, search by part number (remove prefixes/suffixes) and enter the core ID to view all orderable parts, and review parametrics.
- [4] Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
- [5] Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
- [6] Per JEDEC JESD51-6 with the board (JESD51-7) horizontal.
- [7] Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1), with the cold plate temperature used for the case temperature.
- [8] Thermal resistance between the die and the solder pad on the bottom of the package based on simulation without any interface resistance.
- [9] Thermal characterization parameter indicating the temperature difference between the package top and the junction temperature per JEDEC JESD51-2.

Battery cell controller IC

8.4 Electrical characteristics

Table 9. Static and dynamic electrical characteristics

		Min	Тур	Max	Unit
ent					
Supply voltage					V
Full parameter specification (SPI application)		6.0	_	30	
Full parameter specification (TPL application)		7.0	_	30	
Supply current (base value)					mA
Normal mode, cell balance OFF, ADC inactive, SPI		_	6.0	7.0	
,				_	
		_	8.0		
communication inactive, IVCOM = 0 mA				10	
				_	
Supply current adder when TPL communication active		_	_	8.3	mA
with only one device in daisy chain					
Supply current adder when TPL communication active	[1]	_	_	10	mA
with multiple devices in daisy chain					
Supply current adder to set all 6 cell balance switches		_	2.0	_	mA
ON					
Delta supply current to perform ADC conversions	[2]				mA
			4.7	7.0	
ADC2 continuously converting		<u> </u>	'''		
, ,			1.0	2.0	
	Full parameter specification (SPI application) Full parameter specification (TPL application) Supply current (base value) Normal mode, cell balance OFF, ADC inactive, SPI communication inactive, IVCOM = 0 mA Normal mode, cell balance OFF, ADC inactive, TPL communication inactive, IVCOM = 0 mA Supply current adder when TPL communication active with only one device in daisy chain Supply current adder when TPL communication active with multiple devices in daisy chain Supply current adder to set all 6 cell balance switches ON Delta supply current to perform ADC conversions (addend) ADC1-A,B continuously converting	Full parameter specification (SPI application) Full parameter specification (TPL application) Supply current (base value) Normal mode, cell balance OFF, ADC inactive, SPI communication inactive, IVCOM = 0 mA Normal mode, cell balance OFF, ADC inactive, TPL communication inactive, IVCOM = 0 mA Supply current adder when TPL communication active with only one device in daisy chain Supply current adder when TPL communication active with multiple devices in daisy chain Supply current adder to set all 6 cell balance switches ON Delta supply current to perform ADC conversions (addend) ADC1-A,B continuously converting	Full parameter specification (SPI application) Full parameter specification (TPL application) Supply current (base value) Normal mode, cell balance OFF, ADC inactive, SPI communication inactive, IVCOM = 0 mA Normal mode, cell balance OFF, ADC inactive, TPL communication inactive, IVCOM = 0 mA Supply current adder when TPL communication active with only one device in daisy chain Supply current adder when TPL communication active with multiple devices in daisy chain Supply current adder to set all 6 cell balance switches ON Delta supply current to perform ADC conversions (addend) ADC1-A,B continuously converting	Full parameter specification (SPI application) Full parameter specification (TPL application) Full parameter specification (TPL application) Supply current (base value) Normal mode, cell balance OFF, ADC inactive, SPI communication inactive, IVCOM = 0 mA Normal mode, cell balance OFF, ADC inactive, TPL communication inactive, IVCOM = 0 mA Supply current adder when TPL communication active with only one device in daisy chain Supply current adder when TPL communication active with multiple devices in daisy chain Supply current adder to set all 6 cell balance switches ON Delta supply current to perform ADC conversions (22) (addend) ADC1-A,B continuously converting — 4.7	Full parameter specification (SPI application) Full parameter specification (TPL application) Full parameter specification (TPL application) Supply current (base value) Normal mode, cell balance OFF, ADC inactive, SPI communication inactive, IVCOM = 0 mA Normal mode, cell balance OFF, ADC inactive, TPL communication inactive, IVCOM = 0 mA Supply current adder when TPL communication active with only one device in daisy chain Supply current adder when TPL communication active with multiple devices in daisy chain Supply current adder to set all 6 cell balance switches ON Delta supply current to perform ADC conversions (addend) ADC1-A,B continuously converting

Battery cell controller IC

Table 9. Static and dynamic electrical characteristics...continued

Characteristics noted under conditions: $6.0 \text{ V} \le V_{PWR} \le 30 \text{ V}$ (SPI mode) or $7.0 \text{ V} \le V_{PWR} \le 30 \text{ V}$ (TPL mode), $-40 \text{ °C} \le T_A \le 125 \text{ °C}$ (SPI mode) or $-40 \text{ °C} \le T_A \le 105 \text{ °C}$ (TPL mode), GND = 0 V, unless otherwise stated. Typical values refer to $V_{PWR} = 24 \text{ V}$, $T_A = 25 \text{ °C}$, unless otherwise noted.

Symbol	Parameter	Min	Тур	Max	Unit
I _{VPWR(SS)}	Supply current in sleep and idle modes, communication inactive, cell balance off, oscillator monitor on, cyclic measurement off				
	SPI mode (T _A = 25 °C)	_	32	_	μA
	SPI mode (−40 °C ≤ T _A ≤ 85 °C)	_	_	60	
	SPI mode (T _A = 125 °C)	_	42	80 —	
	TPL mode (T _A = 25 °C)	_	75	_	
	TPL mode (-40 °C ≤ T _A ≤ 85 °C)	_	_	100	
	TPL mode (T _A = 125 °C)	_	_	138	
I _{VPWR(CKMON)}	Clock monitor current consumption	_	5	8 —	μΑ
V _{VPWR_CT}	Voltage drop across CT6 and VPWR without accuracy degradation	-0.5	_	0.5	V
V _{PWR(OV_FLAG)}	V _{PWR} overvoltage fault threshold (flag)	31 —	— 33.5	36 —	V
V _{PWR(LV_FLAG)}	V _{PWR} low-voltage warning threshold (flag)	7.5 —	— 7.8	8.1 —	V
V _{PWR(UV_POR)}	V _{PWR} undervoltage shutdown threshold (POR), falling VPWR				V
	SPI mode	4.8	_	5.0	
	TPL mode	6.1	4.9	6.4	
		— O.1	— 6.25	— 0.4 —	
V _{PWR(UV_RIS)}	V _{PWR} undervoltage shutdown threshold (POR), rising VPWR				V
	SPI mode	5.6	_	6.0	
	TPL mode	_	5.8	<u> </u>	
		6.6	— 6.8	7.0	
t	V _{PWR} OV, LV filter	_	50		μs
t _{VPWR(FILTER)} VPRE power su			50		μs
-	T				14
VPRE	Pre-regulator voltage range - decouple with 470 nF SPI mode, ILoad = 15 mA	5.6	_	5.9	V
	SPI mode, ILoad = 15 mA, 5.0 V ≤ VPWR < 6.0 V	_	5.75	_	
	TPL mode, ILoad = 70 mA	4.9	_	_	
		4.9	_	_	
		6.3	— 6.5	6.7	
· · · · · · · · · · · · · · · · · · ·	DDC underveltere threehold leading to a sect	4.0	6.5	4.5	V
$V_{PRE(UV_TH)}$	PRE undervoltage threshold leading to a reset	4.0	4.25	4.5	V
VCP power sup	ply				
VCP	Charge pump voltage range	2 × V _{PRE} – 2	_	2 × V _{PRE}	V
		2 × V _{PRE} – 2		2 × V _{PRE}	
V _{CP(UV_TH)}	Undervoltage threshold for VCP minus VPRE	0.9	1.5	2.2	V

MC33772C

Battery cell controller IC

Table 9. Static and dynamic electrical characteristics...continued

Characteristics noted under conditions: $6.0 \text{ V} \leq V_{PWR} \leq 30 \text{ V}$ (SPI mode) or $7.0 \text{ V} \leq V_{PWR} \leq 30 \text{ V}$ (TPL mode), $-40 \text{ °C} \leq T_A \leq 125 \text{ °C}$ (SPI mode) or $-40 \text{ °C} \leq T_A \leq 105 \text{ °C}$ (TPL mode), GND = 0 V, unless otherwise stated. Typical values refer to $V_{PWR} = 24 \text{ V}$, $T_A = 25 \text{ °C}$, unless otherwise noted.

otherwise noted.						
Symbol	Parameter		Min	Тур	Max	Unit
					_	
VDDIO power sı						
$V_{\rm DDIO}$	IO supply for I ² C and SPI interfaces - voltage range		3.1	<u> </u>	5.2 —	V
VCOM power su	ipply					
V _{COM}	VCOM output voltage		4.9 —	5.0	5.2 —	V
I _{VCOM}	VCOM output current allocated for external use		_		5.0 5.0	mA
V _{COM(UV)}	VCOM undervoltage fault threshold	1 undervoltage fault threshold			4.6	V
V _{COM_HYS}	VCOM undervoltage hysteresis		_	100	_	mV
t _{VCOM(FLT_TIMER)}	VCOM undervoltage fault timer		_	10	_	μs
t _{VCOM(RETRY)}	VCOM fault retry timer		_	10	_	ms
V _{COM(OV)}	VCOM overvoltage fault threshold		5.4 5.4	_ _	5.9 5.9	V
I _{LIM(OC)}	VCOM current limit in TPL mode VCOM current limit SPI mode	65 65 35 35	_ _ _ _	140 140 140 140	mA	
R _{VCOM(SS)}	VCOM sleep mode pulldown resistor		1.0	2.0	5.0	kΩ
t _{VCOM}	VCOM rise time (CL = 2.2 μF ceramic X7R only)	[4]	_	_ _	400 400	μs
VANA power su	pply					
V _{ANA}	VANA output voltage (not used by external circuits) Decouple with 47 nF X7R 0603 or 0402		2.6	2.65	2.7 —	V
V _{ANA(UV)}	VANA undervoltage fault threshold		2.28 —	2.4	2.5 —	V
V _{ANA_HYS}	VANA undervoltage hysteresis		_	50	_	mV
V _{ANA(FLT_TIMER)}	VANA undervoltage fault timer		_	11	_	μs
V _{ANA(OV)}	VANA overvoltage fault threshold		2.77	2.8	2.85	V
t _{VANA(RETRY)}	VANA fault retry timer		_	10	_	ms
I _{LIM(OC)}	VANA current limit		5.0 5		10 10	mA
R _{VANA_RPD}	VANA sleep mode pull-down resistor		_	1.0	_	kΩ
t _{VANA}	VANA rise time (CL = 47 nF ceramic X7R only)	[4]	_	_ _	100 100	μs
ADC1-A, ADC1-	 B			1	<u>I</u>	
CTn _(LEAKAGE)	Cell terminal input leakage current		_	10	100	nA

MC33772C

Battery cell controller IC

Table 9. Static and dynamic electrical characteristics...continued

Symbol	Parameter		Min	Тур	Max	Unit
CT _N	Cell terminal input current during conversion		_	50	_	nA
R _{PD}	Cell terminal open load detection pulldown resistor		850 —	950	1250 —	Ω
V _{VPWR_RES}	VPWR terminal measurement resolution		_	2.44148	_	mV/LSB
V _{VPWR_RNG}	VPWR terminal measurement range SPI application TPL application		6.0 7.0		36 36	V
VPWR _{TERM_ERR}	VPWR terminal measurement accuracy	[5]	-0.5	_	0.5	%
V_{CT_RNG}	ADC differential input voltage range for CTn to CTn-1	[6]	0.0	_	4.85	V
V _{CT_ANx_RES}	Cell voltage and ANx resolution in 15-bit MEAS_xxxx registers		_	152.58789	_	μV/LSB
V _{ANx_RATIO_RES}	ANx resolution in 15-bit MEAS_xxxx registers in ratiometric mode	_	VCOM × 30.51758	_		
V _{ERR}	Cell voltage measurement error 0.1 V \leq V _{CELL} \leq 4.85 V, -40 °C \leq T _A \leq 105 °C (or -40 °C \leq T _J \leq 125 °C)	-5.5 —	±0.7	5.5 —	mV	
V _{ERR_1}	Cell voltage measurement error $0 \text{ V} \leq \text{V}_{\text{CELL}} \leq 1.5 \text{ V}, -40 \text{ °C} \leq \text{T}_{\text{A}} \leq 60 \text{ °C}$ $(\text{or } -40 \text{ °C} \leq \text{T}_{\text{J}} \leq 85 \text{ °C})$	-1.5 —	±0.4	1.5 —	mV	
V _{ERR_2}	Cell voltage measurement error 1.5 V \leq V _{CELL} \leq 2.7 V, -40 °C \leq T _A \leq 60 °C (or -40 °C \leq T _J \leq 85 °C)	-2.0 —	±0.4	2.0	mV	
V _{ERR_3}	Cell voltage measurement error [7] [8] $2.7 \text{ V} \leq \text{V}_{\text{CELL}} \leq 3.7 \text{ V}, -40 \text{ °C} \leq \text{T}_{\text{A}} \leq 60 \text{ °C}$ (or $-40 \text{ °C} \leq \text{T}_{\text{J}} \leq 85 \text{ °C}$)		-2.0 —	±0.5	2.0	mV
V _{ERR_4}	Cell voltage measurement error 3.7 V \leq V _{CELL} \leq 4.3 V, -40 °C \leq T _A \leq 60 °C (or -40 °C \leq T _J \leq 85 °C)	[7] [8]	-2.8 —	±0.7	2.8	mV
V _{ERR_5}	Cell voltage measurement error 1.5 V \leq V _{CELL} \leq 4.5 V, -40 °C \leq T _A \leq 105 °C (or -40 °C \leq T _J \leq 125 °C)	[7] [8]	-4.5 	±0.7	4.5 —	mV
V _{ERR_A}	Cell voltage measurement error After aging, 0.1 V \leq V _{CELL} \leq 4.85 V, -40 °C \leq T _A \leq 105 °C (or -40 °C \leq T _J \leq 125 °C)	[7] [9]	-8.0	±0.8	8.0	mV
V _{ERR_1A}	Cell voltage measurement error After aging, 0 V \leq V _{CELL} \leq 1.5 V, -40 °C \leq T _A \leq 60 °C (or -40 °C \leq T _J \leq 85 °C)	[7] [9]	-2.0	±0.5	2.0	mV
V _{ERR_2A}	Cell voltage measurement error After aging, 1.5 V ≤ V _{CELL} ≤ 2.7 V, -40 °C ≤ T _A ≤ 60 °C (or -40 °C ≤ T _J ≤ 85 °C)		-2.5	±0.5	2.5	mV
V _{ERR_3A}	Cell voltage measurement error after aging, 2.7 V \leq V _{CELL} \leq 3.7 V, -40 °C \leq T _A \leq 60 °C (or -40 °C \leq T _J \leq 85 °C)	[7] [9]	-3.2	±0.4	3.2	mV
V _{ERR_4A}	Cell voltage measurement error after aging, 3.7 V ≤ V _{CELL} ≤ 4.3 V, −40 °C ≤ T _A ≤ 60 °C (or −40 °C ≤ T _J ≤ 85 °C)	[7] [9]	-3.9	±0.7	3.9	mV

Battery cell controller IC

Table 9. Static and dynamic electrical characteristics...continued

Characteristics noted under conditions: $6.0 \text{ V} \le V_{PWR} \le 30 \text{ V}$ (SPI mode) or $7.0 \text{ V} \le V_{PWR} \le 30 \text{ V}$ (TPL mode), $-40 \text{ °C} \le T_A \le 125 \text{ °C}$ (SPI mode) or $-40 \text{ °C} \le T_A \le 105 \text{ °C}$ (TPL mode), GND = 0 V, unless otherwise stated. Typical values refer to $V_{PWR} = 24 \text{ V}$, $T_A = 25 \text{ °C}$, unless otherwise noted.

Symbol	Parameter		Min	Тур	Max	Unit
V _{ERR 5A}	Cell voltage measurement error	[7] [9]				
2.1.12071	after aging, 1.5 V \leq V _{CELL} \leq 4.5 V, -40 °C \leq T _A \leq		-6.0	±0.7	6.0	mV
	105 °C (or –40 °C ≤ T _J ≤ 125 °C)					
V _{ANx ERR}	Magnitude of ANx error in the entire measurement	[7] [9]				mV
7.07_2.00	range:					
	Ratiometric measurement		-16	_	16	
	Absolute measurement, input in the range [1.0, 4.		-10	_	10	
	5] V					
	Absolute measurement, input in the range [0, 4. 85] V for -40 °C < T _A < 60 °C		-8.0	_	8.0	
	Absolute measurement after soldering		-11	_	11	
	and aging, input in the range [0, 4.85] V					
	for -40 °C < T _A < 105 °C					
CONV	Single channel net conversion time					μs
	13-bit resolution		_	6.77	_	
	14-bit resolution		_	9.43	_	
	15-bit resolution		_	14.75	_	
	16-bit resolution		_	25.36	_	
V _{V NOISE}	Conversion noise					μVrms
V_14010L	13-bit resolution		_	1800	_	Ι'
	14-bit resolution		_	1000	_	
	15-bit resolution		_	600	_	
	16-bit resolution			400	_	
ADC2/current se	nse module					
V _{INC}	ISENSE+/ISENSE- input voltage (reference to AGND)		-300	_	300	mV
V _{IND}	ISENSE+/ISENSE- differential input voltage range		-150	_	150	mV
V _{ISENSEX(OFFSET)}	ISENSE+/ISENSE- input voltage offset error	[10]	_	_	0.5	μV
I _{SENSEX(BIAS)}	ISENSE+/ISENSE- input bias current		-100	_	100	nA
I _{SENSE(DIF)}	ISENSE+/ISENSE- differential input bias current		-5.0	_	5.0	nA
I _{GAINERR}	ISENSE error including nonlinearities	[11]	-0.5	_	0.5	%
I _{ISENSE OL}	ISENSE open load injected current	[12]	109	130	151	μA
			_		_	
V _{ISENSE_OL}	ISENSE open load detection threshold		340	460	600	mV
* ISENSE_OL	To Entrol open road detection amounted		_	100	_	•
	Current sense user register resolution			0.6		μV/LSE
V _{2RES}	-			0.0		
V_{PGA_SAT}	PGA saturation half-range					mV
	Gain = 256		_	4.9	-	
	Gain = 64		_	19.5	_	
	Gain = 16		_	78.1	_	
	Gain = 4		_	150		
V _{PGA_ITH}	Voltage threshold for PGA gain increase					mV
_	Gain = 256		_	-	_	
	Gain = 64			2.344	_	
	Gain = 16			9.375	_	
	Gain = 4		_	37.50	_	
V _{PGA_DTH}	Gain = 4 Voltage threshold for PGA gain decrease			37.50	_	mV

MC33772C

All information provided in this document is subject to legal disclaimers.

Battery cell controller IC

Table 9. Static and dynamic electrical characteristics...continued

Characteristics noted under conditions: $6.0 \text{ V} \le V_{PWR} \le 30 \text{ V}$ (SPI mode) or $7.0 \text{ V} \le V_{PWR} \le 30 \text{ V}$ (TPL mode), $-40 \text{ °C} \le T_A \le 125 \text{ °C}$ (SPI mode) or $-40 \text{ °C} \le T_A \le 105 \text{ °C}$ (TPL mode), GND = 0 V, unless otherwise stated. Typical values refer to $V_{PWR} = 24 \text{ V}$, $T_A = 25 \text{ °C}$, unless otherwise noted.

Symbol	Parameter		Min	Тур	Max	Unit
	Gain = 64		_	17.188	_	
	Gain = 16		_	68.750	_	
	Gain = 4		_	_	_	
t _{AZC_SETTLE}	Time to perform auto-zero procedure after enabling the current channel		_	200	_	μs
t _{ICONV}	ADC conversion time including PGA settling time					μs
	13-bit resolution		_	19.00	_	
	14-bit resolution		_	21.67	_	
	15-bit resolution		_	27.00	_	
	16-bit resolution		_	37.67	_	
V_{I_NOISE}	Noise at 16-bit conversion	[10]	_	3.01	_	μVrms
V_{I_NOISE}	Noise error at 13-bit conversion		_	8.33	_	μVrms
ADC _{CLK}	ADC2 and ADC1-A,B clocking frequency		5.7 —	6.0	6.3 —	MHz
Diagnostic thre	esholds			1		
V _{OL_DETECT}	Cell terminal open load V detection threshold					mV
	1.5 V ≤ VCELL ≤ 2.7 V		_	50	_	
	2.5 V ≤ VCELL ≤ 3.7 V		_	100	_	
	2.5 V ≤ VCELL ≤ 4.3 V		_	150	_	
V_{LEAK}	Cell terminal leakage detection level	[7]	–15	_	15	mV
V _{REF_DIAG}	ISENSE diagnostic reference with PGA having gain 4		123.5	_	129.5	mV
V _{OFF_DIAG}	ISENSE diagnostic common mode offset voltage [13]		_	_	37.2	μV
V _{REF_ZD}	Precision diagnostic zener reference for cell voltage channel functional verification			_	4.85	V
V _{CVFV}	Cell voltage channel functional verification allowable error in CT verification measurement	[7]	-22	_	6	mV
V_{BGP}	Band gap reference used in ADC1-A,B functional verification		_	1.18	_	V
ADC1a _{FV} , ADC1b _{FV}	ADC1-A and ADC1-B functional verification (maximum tolerance between ADC1-A, B and diagnostic reference 1.5 V ≤ VCELL ≤ 4.3 V)		- 5	_	5	mV
CTx_UV_TH	Undervoltage functional verification threshold in diagnostic mode					mV
	1.5 V ≤ VCELL ≤ 2.7 V		390	_	_	
	2.5 V ≤ VCELL ≤ 3.7 V		650	_	_	
	2.5 V ≤ VCELL ≤ 4.3 V		1200	_	_	
CTx_OV_TH	Overvoltage functional verification threshold in diagnostic mode					mV
	1.5 V ≤ VCELL ≤ 2.7 V		_	_	1800	
	2.5 V ≤ VCELL ≤ 3.7 V		_	_	3500	
	2.5 V ≤ VCELL ≤ 4.3 V		_	_	4000	
Cell balance dr	ivers					
V _{DS(CLAMP)}	Cell balance driver VDS active clamp voltage		10	11	12 —	V
V _{OUT(FLT_TH)}	Output fault detection voltage threshold					V
OUI(FLI_IH)	Balance off (open load)		0.3	0.55	0.75	"

MC33772C

All information provided in this document is subject to legal disclaimers.

Battery cell controller IC

Table 9. Static and dynamic electrical characteristics...continued

Characteristics noted under conditions: $6.0 \text{ V} \le V_{PWR} \le 30 \text{ V}$ (SPI mode) or $7.0 \text{ V} \le V_{PWR} \le 30 \text{ V}$ (TPL mode), $-40 \text{ °C} \le T_A \le 125 \text{ °C}$ (SPI mode) or $-40 \text{ °C} \le T_A \le 105 \text{ °C}$ (TPL mode), GND = 0 V, unless otherwise stated. Typical values refer to $V_{PWR} = 24 \text{ V}$, $T_A = 25 \text{ °C}$, unless otherwise noted.

Symbol	Parameter		Min	Тур	Max	Unit
	Balance on (shorted load)		_		_	
R _{PD_CB}	Output OFF open load detection pull-down resistor					kΩ
	Balance off, open load detect disabled		1.7	2.0	2.9	
			_		_	
I _{OUT(LKG)}	Output leakage current					μΑ
	Balance off, open load detect disabled at V _{DS} = 4. 0 V		_	_	1.0	
R _{DS(on)}	Drain-to-source on resistance					Ω
	I _{OUT} = 300 mA, T _J = 125 °C		_	_	0.80	
	I _{OUT} = 300 mA, T _J = 25 °C		_	0.5	_	
	I _{OUT} = 300 mA, T _J = -40 °C	_	0.4	_		
I _{LIM_CB}	Driver current limitation (shorted resistor)		310	_	950	mA
t _{ON}	Cell balance driver turn on	[14]				μs
	$R_L = 15 \Omega$		_	350	450	
		F4.41			_	
t _{OFF}	Cell balance driver turn off	[14]				μs
	R _L = 15 Ω			200		
t _{BAL_DEGLICTH}	Short/open detect filter time		19	20	42.1	μs
			_			
Internal temperat	ture measurement					
IC_TEMP1_ERR	IC temperature measurement error	-3.0	_	3.0	K	
IC_TEMP1_RES	IC temperature resolution	_	0.032	_	K/LSB	
TSD_TH	SD_TH Thermal shutdown		155	170	185	°C
			_		_	
TSD_HYS	Thermal shutdown hysteresis		5.0	10	12.2	°C
			_		_	
Default operation	nal parameters					
V _{CTOV(TH)}	Cell overvoltage threshold (8 bits)		0.0	4.2	5.0	V
V _{CTOV(RES)}	Cell overvoltage threshold resolution		_	19.53125	_	mV/LSB
V _{CTUV(TH)}	Cell undervoltage threshold (8 bits)		0.0	2.5	5.0	V
V _{CTUV(RES)}	Cell undervoltage threshold resolution		_	19.53125	_	mV/LSB
V _{GPIO_OT(TH)}	GPIOx configured as ANx input overtemperature threshold from POR		_	1.16	_	V
V _{GPIO OT(RES)}	Overtemperature voltage threshold resolution		_	4.8828125	_	mV/LSB
V _{GPIO_UT(TH)}	GPIOx configured as ANx input undertemperature threshold from POR		_	3.82	_	V
V _{GPIO_UT(RES)}	Undertemperature voltage threshold resolution		_	4.8828125	_	mV/LSB
	input/output GPIOx					
V _{IH}	Input high-voltage (3.3 V compatible)	[15]	2.0	_	_	V
V _{IL}	Input low-voltage (3.3 V compatible)	[15]	_	_	1.0	V
V _{HYS}	Input hysteresis	[15]	_	100		mV
	Input leakage current			100		nA
I _{IL}	Input leakage cultetit					11174

MC33772C

Battery cell controller IC

Table 9. Static and dynamic electrical characteristics...continued

Characteristics noted under conditions: $6.0 \text{ V} \le V_{PWR} \le 30 \text{ V}$ (SPI mode) or $7.0 \text{ V} \le V_{PWR} \le 30 \text{ V}$ (TPL mode), $-40 \text{ °C} \le T_A \le 125 \text{ °C}$ (SPI mode) or $-40 \text{ °C} \le T_A \le 105 \text{ °C}$ (TPL mode), GND = 0 V, unless otherwise stated. Typical values refer to $V_{PWR} = 24 \text{ V}$, $T_A = 25 \text{ °C}$, unless otherwise noted.

Symbol	Parameter		Min	Тур	Max	Unit	
I _{IDL}	Differential input leakage current GPIO 5,6 GPIO 5,6 configured as digital inputs for current measurement		-30	_	30	nA	
V _{OH}	Output high-voltage I _{OH} = −0.5 mA		V _{COM} - 0.8	_	_	V	
V _{OL}	Output low-voltage I _{OL} = +0.5 mA		_	_	0.8	V	
V _{ADC}	Analog ADC input voltage range for ratiometric measurements		AGND	_	V _{COM}	V	
V _{OL(TH)}	Analog input open pin detect threshold	[16]	0.1 —	0.15	0.23 —	V	
R _{OPENPD}	Internal open detection pull-down resistor	[17]	3.8	5.0	6.2	kΩ	
t _{GPIO0_WU}	GPIO0 WU de-glitch filter		47 —	50	85 —	μs	
t _{GPIO0_FLT}	GPIO0 daisy chain de-glitch filter both edges	19 —	20	48	μs		
t _{GPIO2_SOC}	GPIO2 convert trigger de-glitch filter	1.9 —	2.0	2.1	μs		
t _{GPIOx_DIN}	GPIOx configured as digital input de-glitch filter		2.5	_	5.6	μs	
Reset input							
V _{IH_RST}	Input high-voltage (3.3 V compatible)		2.0	_	_	V	
V _{IL_RST}	Input low-voltage (3.3 V compatible)		_	_	1.0	V	
V _{HYS}	Input hysteresis		_	0.6	_	V	
t _{RESETFLT}	RESET de-glitch filter		_	100	_	μs	
R _{RESET_PD}	Input logic pull down (RESET)		_	100	_	kΩ	
SPI_COM_EN	input						
V _{IH}	Input high-voltage (3.3 V compatible)		2.0	_	_	V	
V _{IL}	Input low-voltage (3.3 V compatible)		_	_	1.0	V	
V _{HYS}	Input hysteresis		_	450	_	mV	
Digital interfa	ce		I.				
V _{FAULT_HA}	FAULT output (high active, I_{OH} = 1.0 mA) FAULT output (high active, I_{OH} = 1.0 mA), SPI mode, 5.0		3.9	4.9 —	6.0	V	
	≤ VPWR < 6.0 V		2.9		6.0		
I _{FAULT_CL}	FAULT output current limit		3.0		25	mA	
R _{FAULT_PD}	FAULT output pulldown resistance		_	100	_	kΩ	
V _{IH_COMM}	Voltage threshold to detect the input as high SI/RDTX_IN+, SCLK/RDTX_IN-, CSB, SDA, SCL (NOTE: needs to be 3.3 V compatible)		_	_	2.0	V	
V _{IL_COMM}	Voltage threshold to detect the input as low SI/RDTX_IN+, SCLK/RDTX_IN-, CSB, SDA, SCL		0.8	_	_	V	
V _{HYS}	Input hysteresis SI/RDTX_IN+, SCLK/RDTX_IN-, CSB, SDA, SCL		_	100	_	mV	
I _{LOGIC_SS}	Sleep state input logic current					nA	

MC33772C

Battery cell controller IC

Table 9. Static and dynamic electrical characteristics...continued

Symbol	Parameter		Min	Тур	Max	Unit
	CSB		-100	_	100	
R _{SCLK_PD}	Input logic pulldown resistance (SCLK/RDTX_IN-, SI/RDTX+)		_	20	_	kΩ
R _{I_PU}	Input logic pullup resistance to V _{COM} (CSB, SDA, SCL)		_	100	_	kΩ
I _{SO_TRI}	3-state SO input current 0 V to V _{COM}		-2.0	_	2.0	μΑ
V _{SO_HIGH}	SO high-state output voltage with I _{SO(HIGH)} = −2.0 mA		V _{DDIO} - 0.4	_	_	V
V _{SO_LOW}	SO, SDA, SLK low-state output voltage with $I_{SO(HIGH)} = -2.0$ mA		_	_	0.4	V
CSB _{WU_FLT}	CSB wake-up de-glitch filter, low to high transition		_	50	65 —	μs
System timing						
t _{CELL_CONV}	Time needed to acquire all 6 cell voltages and the current after an on demand conversion 13-bit resolution	[18]	20	44	40	μs
	14-bit resolution		38	41 57	43	
	15-bit resolution		53	89	60	
	16-bit resolution			152	_	
			84		93	
					_	
			144		160	
t _{SYNC}	V/I synchronization time	[18]				μs
01110	ADC1-A,B at 13 bit, ADC2 at 13 bit		_	41.39	_	
	ADC1-A,B at 14 bit, ADC2 at 13 bit		_	42.71		
	ADC1-A,B at 15 bit, ADC2 at 13 bit		_	47.37	_	
	ADC1-A,B at 16 bit, ADC2 at 13 bit		_	95.14	_	
t _{SYNC}	V/I synchronization time	[18]				μs
	ADC1-A,B at 13 bit, ADC2 at 14 bit		_	46.73		
	ADC1-A,B at 14 bit, ADC2 at 14 bit		_	48.05	_	
	ADC1-A,B at 15 bit, ADC2 at 14 bit		_	50.71	_	
	ADC1-A,B at 16 bit, ADC2 at 14 bit		_	92.47	_	
t _{SYNC}	V/I synchronization time	[18]				μs
	ADC1-A,B at 13 bit, ADC2 at 15 bit		_	57.39	_	
	ADC1-A,B at 14 bit, ADC2 at 15 bit		_	58.71	_	
	ADC1-A,B at 15 bit, ADC2 at 15 bit		_	61.37		
	ADC1-A,B at 16 bit, ADC2 at 15 bit	[40]	_	87.14	_	
t _{sync}	V/I synchronization time	[18]				μs
	ADC1-A,B at 13 bit, ADC2 at 16 bit		-	78.73	_	
	ADC1-A,B at 14 bit, ADC2 at 16 bit		-	80.05	_	
	ADC1-A,B at 15 bit, ADC2 at 16 bit		_	82.71	_	
	ADC1-A,B at 16 bit, ADC2 at 16 bit		_	88.02	_	
t _{VPWR(READY)}	Time after VPWR connection for the IC to be ready for initialization		_	_	5.0	ms
t _{WAKE-UP}	Power up duration		_	_	440	μs
t _{WAKE_DELAY}	Time between wake pulses		500	600	700	μs
_			_		_	

Battery cell controller IC

Table 9. Static and dynamic electrical characteristics...continued

Symbol	Parameter		Min	Тур	Max	Unit
tnowup	Time, starting from the first SOM received, to go back to Sleep/Idle mode time after receiving incomplete TPL bus wake-up sequence			_	1.3 1.3	ms
t _{IDLE}	Idle timeout after POR		54 —	60	66 —	s
t _{BALANCE}	Cell balance timer range		0.5	_	511	min
t _{CYCLE}	Cyclic acquisition timer range		0.0	_	8.5	s
t _{FAULT}	Fault detection to activation of fault pin Normal mode		_	_	56	μs
t _{DIAG}	Diagnostic mode timeout		0.047	1.0	8.5	s
t _{EOC}	SOC to data ready (includes post processing of data) 13-bit resolution 14-bit resolution 15-bit resolution 16-bit resolution	[18]	140 — 190 — 291 — 494 —	148 201 307 520	156 — 211 — 323 — 546 —	μs
t _{SETTLE}	Time after SOC to begin converting with ADC1-A,B	[18]	11.67 —	12.28	12.90 —	μs
t _{CLST_TPL}	Time needed to send an SOC command and read back 6 cell voltages, 7 temperatures, 1 current, and 1 coulomb counter with TPL communication working at 2.0 Mbit/s and ADC1-A,B configured as follows (with ADC_CFG[AVG] = 0): 13-bit resolution 14-bit resolution 15-bit resolution 16-bit resolution		_ _ _ _	0.79 0.85 0.95 1.16	_ _ _ _	ms
t _{CLST_} SPI	Time needed to send an SOC command and read back 6 cell voltages, 7 temperatures, 1 current, and 1 coulomb counter with SPI communication working at 4.0 Mbit/s and ADC1-A,B configured as follows (with ADC_CFG[AVG] = 0): 13-bit resolution 14-bit resolution 15-bit resolution 16-bit resolution		_ _ _ _	0.48 0.54 0.64 0.86	_ _ _ _	ms
t _{I2C_DOWNLOAD}	Time to download EEPROM calibration after POR		_	_	1.0	ms
t _{12C_ACCESS}	EEPROM access time, EEPROM write (depends on device selection)		_	5.0	_	ms
tWAVE_DC_BITx	Daisy chain duty cycle off time t _{WAVE_DC_BITx} = 00		450 —	500	550 —	μs
twave_dc_bitx	Daisy chain duty cycle off time t _{WAVE_DC_BITx} = 01		0.90	1.0	1.10	ms

Battery cell controller IC

Table 9. Static and dynamic electrical characteristics...continued

Daisy chain duty cycle off time twave_dc_bitx = 10 Daisy chain duty cycle off time twave_dc_bitx = 11 Daisy chain duty cycle on time Time out to reset the IC in the absence of communication Sequential data transfer delay in SPI mode (N) SCLK frequency SCLK high time (A) SCLK period (A+B)	[19]	9 — 90 — 450 — —	10 100 500 1024	11 — 110 — 550 —	ms ms µs ms
Daisy chain duty cycle off time twave_DC_BITx = 11 Daisy chain duty cycle on time Time out to reset the IC in the absence of communication Sequential data transfer delay in SPI mode (N) SCLK frequency SCLK high time (A) SCLK high time (B) SCLK period (A+B)	[19]	90 — 450 —	100	110 —	μs
twave_dc_bitx = 11 Daisy chain duty cycle on time Time out to reset the IC in the absence of communication Sequential data transfer delay in SPI mode (N) SCLK frequency SCLK high time (A) SCLK high time (B) SCLK period (A+B)	[19]	450 — —	500	_	μs
twave_dc_bitx = 11 Daisy chain duty cycle on time Time out to reset the IC in the absence of communication Sequential data transfer delay in SPI mode (N) SCLK frequency SCLK high time (A) SCLK high time (B) SCLK period (A+B)	[19]	450 — —	500	_	μs
Daisy chain duty cycle on time Time out to reset the IC in the absence of communication Sequential data transfer delay in SPI mode (N) SCLK frequency SCLK high time (A) SCLK high time (B) SCLK period (A+B)	[19]	450 — —	500	_	<u> </u>
Time out to reset the IC in the absence of communication Sequential data transfer delay in SPI mode (N) SCLK frequency SCLK high time (A) SCLK high time (B) SCLK period (A+B)	[19]	<u> </u>		550 — —	<u> </u>
Time out to reset the IC in the absence of communication Sequential data transfer delay in SPI mode (N) SCLK frequency SCLK high time (A) SCLK high time (B) SCLK period (A+B)	[19]	<u> </u>			<u> </u>
Sequential data transfer delay in SPI mode (N) SCLK frequency SCLK high time (A) SCLK high time (B) SCLK period (A+B)	[19]	1.0	1024	_	ms
SCLK frequency SCLK high time (A) SCLK high time (B) SCLK period (A+B)	[19]	1.0			
SCLK frequency SCLK high time (A) SCLK high time (B) SCLK period (A+B)	[19]	1.0			
SCLK high time (A) SCLK high time (B) SCLK period (A+B)		_	_	_	μs
SCLK high time (A) SCLK high time (B) SCLK period (A+B)				4.0	MHz
SCLK high time (B) SCLK period (A+B)	[19]	125	_	_	ns
SCLK period (A+B)					ns
	(40)				ns
SCLK falling time		250	_	15	ns
SCLK rising time		_	15	ns	
	20	_	10	ns	
SCLK setup time (O)		_	_		
SCLK hold time (P)		20	_	_	ns
			_	_	ns
. ,		40	_	_	ns
SO data valid, rising edge of SCLK to SO data valid (I)		_	_	40	ns
SO enable time (H)		_	_	40	ns
SO disable time (K)		_	_	40	ns
CSB lead time (L)	[19]	100	_	_	ns
CSB lag time (M)	[19]	100	_	_	ns
CU)					
Time between two consecutive message request transmitted by MCU	[20]	4.0	_	_	μs
Time the MCU shall wait after sending first wake-up message per MC33772C IC	[21]	0.75	_	_	ms
C33772C)	'		,	1	
Sequential data transfer delay in TPL mode	[22][23]	3.8	4.0	4.25 —	μs
Transmit pulse duration		_	208	_	ns
Port delay introduced by each repeater in MC33772C	[24]	_	_	0.95	μs
	[23][25]	4.0	5.0	9	μs
· -		_		_	
Differential receiver threshold		480	580	680	mV
	SI setup time (F) SI hold time (G) SO data valid, rising edge of SCLK to SO data valid (I) SO enable time (H) SO disable time (K) CSB lead time (L) CSB lag time (M) Time between two consecutive message request transmitted by MCU Time the MCU shall wait after sending first wake-up message per MC33772C IC 33772C) Sequential data transfer delay in TPL mode Transmit pulse duration Port delay introduced by each repeater in MC33772C Slave response after read command	Schribit time (F) SI setup time (F) SI hold time (G) SO data valid, rising edge of SCLK to SO data valid (I) SO enable time (H) SO disable time (K) CSB lead time (L) CSB lag time (M) (I9) (I) (I	SI setup time (F) [19] 40 SI hold time (G) [19] 40 SO data valid, rising edge of SCLK to SO data valid (I) [19] — SO enable time (H) [19] — SO disable time (K) [19] — CSB lead time (L) [19] 100 CSB lag time (M) [19] 100 CSB lag time (M) [19] 100 U) Time between two consecutive message request transmitted by MCU Time the MCU shall wait after sending first wake-up [21] 0.75 message per MC33772C IC 33772C) Sequential data transfer delay in TPL mode [22][23] 3.8 — Transmit pulse duration — Port delay introduced by each repeater in MC33772C [24] — Slave response after read command [23][25] 4.0 —	SI setup time (F)	SI setup time (F)

Battery cell controller IC

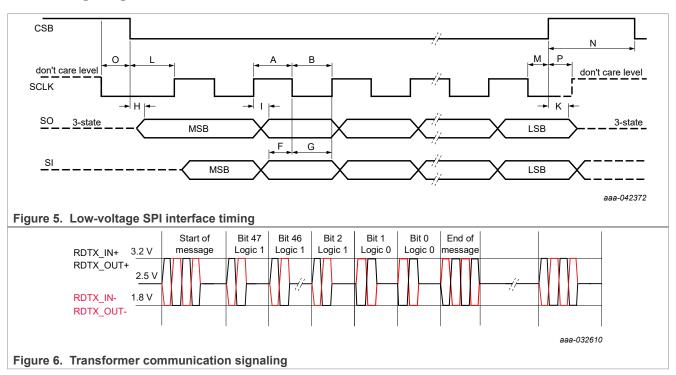
Table 9. Static and dynamic electrical characteristics...continued

Symbol	Parameter	Min	Тур	Max	Unit
t _{EOM}	Message timeout duration [26]	238	250	_	μs
		_			

- [1] The current consumption due to communication is valid with minimum 8 nodes in the daisy chain.
- Use of ADC1-A,B can be performed with a duty cycle of t_{EOC}/period (us). For example, SYS_CFG1[CYCLIC_TIMER] = 010, corresponding to 100000 µs period, and ADC_CFG[ADC1_A_DEF] = ADC_CFG[ADC1_B_DEF] = 11, corresponding to 16 bits and therefore t_{EOC} = 520 µs, given a duty cycle of 0.0052 (or ROM). When an ADC is configured in continuous mode, the duty cycle is equal to 1, resulting in high-current consumption.
- [3] To calculate the current consumption in sleep mode, the following formula has to be used: I_{SLEEP_MODE} = (1 \tau_{NORMAL}). I_{VPWR(SS)} + \tau_{NORMAL}. [I_{VPWR} + I_{VPWR(CBON)} (not zero only if SYS_CFG1[CB_DRVEN] = 1), where \tau_{NORMAL} = (t_{VCOM} + t_{EOC})/period (µs), where \tau_{EOC} depends on the selected number of bits for the ADCs (see ADC_CFG[ADC1_A_DEF, ADC1_B_DEF, ADC2_DEF] fields) and period (µs) depends on SYS_CFG1[CYCLIC_TIMER], as explained in note [1]. Evidently I_{SLEEP_MODE} = I_{VPWR(SS)} only if no conversion is requested in sleep mode (for example, SYS_CFG1[CYCLIC_TIMER] = 000) and if the cell balancing is OFF.
- [4] 5 % to 95 % rise time
- [5] Parameter VPWR_{TERM_ERR} is guaranteed if GPIO[0..1] are set in analog inputs (GPIO_CFG1[GPIO0_CFG] = 0b0x and GPIO_CFG1[GPIO1_CFG] = 0b0x). The VPWR_{TERM_ERR} is degraded to typical ±0.8 % if GPIO0 or GPIO1 is set to digital IO mode (GPIO_CFG1[GPIO0_CFG] = 0b1x or GPIO_CFG1[GPIO1_CFG] = 0b1x).
- [6] ADC1-A/B may clamp when the voltage of the Cellx or ANx is over 4.85 V.
- [7] The cell voltage error includes all internal errors, for example; ADC offset, gain error, INL and DNL are included. Current measurement is not active when measuring the cell voltage. Single shot measurements are affected by noise, which has zero mean and standard deviation given by V_{V_NOISE} and is not included in the cell voltage error. In order to reduce it, SW implemented IIR or FIR low-pass filters may be used; example, a moving average, whose length is N samples, has output standard deviation V_{OUTPUT_NOISE} = V_{V_NOISE} /sqrt(N). Performance can be granted only if ADC1-A,B are configured at 16-bits resolution (ADC_CFG[ADC1_A_DEF] = ADC_CFG[ADC1_B_DEF] = 11) and if -100 mV ≤ CTREF GND ≤ 100 mV.
- [8] Inaccuracies from soldering or aging are not included.
- [9] Inaccuracies from soldering (MSL3 preconditioning) and aging (after 3000 h HTOL at T_A = 125 °C) are included.
- [10] Offset error is considered at PGA inputs, with PGA gain being set to 256. Both PGA inputs are grounded (shorted together with SYS_DIAG[I_MUX]=11). The offset value, guaranteed by design, does not include the noise, which is considered to be averaged. The noise is characterized by V_{I_NOISE} and is also with PGA gain set to 256 and PGA inputs shorted together (with SYS_DIAG[I_MUX]=11).
- [11] Performance can be granted only if the ADC2 is configured at the best resolution, namely, ADC_CFG[ADC2_DEF] = 11.
- [12] Setting the SYS_DIAG[ISENSE_OL_DIAG] bit to logic 1 causes the injection of the current I_{ISENSE_OL} in both ISENSE ± pins, so if the shunt is disconnected, in one or both of the input pins there is an increased voltage due to charging of external capacitors. Comparison to the threshold V_{ISENSE_OL} detects the open fault.
- [13] Diagnostic threshold when the PGA inputs are shorted together, the PGA gain is set at 256 and the ADC2 is configured at 16 bit.
- [14] Cell balance drivers performance can be granted if the cell voltage is greater than 1.1 V.
- [15] For GPIO0 configured as wake-up, transition time must be shorter than 100 µs.
- [16] Out of range band should be considered for the GPIOs external components design to avoid false open pin detection.
- [17] During internal open detection, an internal pull up current of 10 μA typical is generated in the pin.
- [18] See the ADC conversion sequence in Figure 10
- [19] See the timing diagram in Figure 5
- [20] It is the time which MCU shall wait for sending new message request to MC33772C.
- [21] The waiting time for MCU after transmitting the first wake-up message is dependent on the number of MC33772C in daisy chain. If the number of nodes in daisy chain is N, then the total waiting time for MCU after sending first wake-up message is N*t_{WU Wait}
- [22] t_{TPL_TD} is the time between two consecutive response messages at the node which is initiating transmission. This time could vary when measured at other forwarding nodes in daisy chain.
- [23] See the waveforms diagram in Figure 28
- The expected waiting time for MCU, to get the response from MC33772C is dependant on number of MC33772C used in daisy chain. The repeater of each node imposes a delay of t_{port_delay} for both request and response. Example: if 24, MC33772C ICs are used in a daisy chain, the last node (24th MC33772C) receives the request in (24*0.95)μs = 22.8 μs.
- [25] t_{RES} is the time between request received and response transmitted by the slave device, which is addressed in the read command. This time could vary when measured at other forwarding nodes in daisy chain.
- [26] The EOM timeout counter starts/restarts after reception of SOM. This means that the maximum length of allowed message frame is t_{EOM}. If a valid EOM is not received in this time frame, the message frame is discarded and the device is ready for new reception.

Battery cell controller IC

8.5 Timing diagrams



9 Functional description

9.1 Introduction

The MC33772C contains all circuit blocks necessary to perform synchronized battery voltage measurements, battery voltage/current measurement, coulomb counting, cell temperature measurement and integrated cell balancing. These features along with high speed communication make the MC33772C ideal for automotive Lithium-ion battery monitoring. In addition to the battery management functions, the MC33772C is designed to monitor many internal and external functions to validate the integrity of the measurements and the measurement system. The following section describes in detail the features, functions and modes of operation of the device. Table 10 summarizes the IC measurement capability depending on the operating mode. Following terms, phrasings and conventions are used in this document:

- User: this word denotes the battery pack controller, including at least one MCU, where the intelligence of the system is located. The pack controller uses one or more MC33772C to sense the physical quantities of a battery.
- User parameter (or simply parameter): it is a datum memorized in the IC registers that is readable or
 writable by the user and is denoted by an identifier within square brackets preceded by a prefix, for example,
 REGISTER_NAME[FIELD_NAME], where REGISTER_NAME is the symbol for the intended register and
 FIELD_NAME is the symbol for the parameter itself, which is, in general, a portion of the 16-bit register data.
- Channel: it is a signal, which can be measured. There are external channels, for example, cell voltages and temperatures, and internal channels, for example, die temperature, and voltage diagnostic references.
- Conversion: this word denotes an analog to digital conversion performed by an ADC and is often meant as measurement of a given channel.
- Sequence: this term denotes a scan of channels that enter some multiplexers to be routed to the ADCs according to a certain sequence. During the scan, each ADC performs subsequent data conversions,

MC33772C

Battery cell controller IC

where each conversion affects a predetermined channel. Sequences are necessary because the number of channels is much greater than the number of ADCs.

- Cyclic measurement: this means the bank of ADCs perform sequences autonomously, for example, with no intervention requested to the user. The user has to do a single programming of an internal timer by providing it with the period value. Then the timer provides the periodic trigger starting each measurement sequence. For example, the period may be 100 ms, while the sequence duration is order of magnitudes shorter. The main purpose of performing cyclic measurements is to carry out automatic comparisons of some measured channels against predefined tunable thresholds, so some fault bits can be set accordingly. Fault bits are readable by the user by accessing the proper fault registers through the ordinary communication channel; or the fault bits may be used to assert the FAULT pin, for the safety information be propagated to the user through the fault line of daisy chained devices.
- On-demand measurement: this means the bank of ADCs perform a sequence when triggered by a SOC command, where SOC means start of conversion. Typically, the user periodically sends a SOC command followed by the reading of the measured values of the most important channels, namely all cell voltages, temperatures and current.

Table 10. Working mode versus measurements

Operating mode	On-demand measurements	Voltage/temperature cyclic measurements	Current measurement	Coulomb counter	Reference
Normal mode	Available	Available, if SYS_CFG1[CYCLIC_ TIMER] ≠ 0	Available and running continuously if enabled by setting SYS_CFG1[I_MEAS_EN] = 1	Available and running continuously if enabled by setting SYS_CFG1[I_MEAS_EN] = 1 Exception: when the device transitions from sleep to normal mode, it is frozen until it is read and reset by the user	Section 9.3.4
<u>Diagnostic</u> <u>mode</u>	Available	Not available	Available and running continuously if enabled by setting SYS_CFG1[I_MEAS_EN] = 1	Available and running continuously if enabled by setting SYS_CFG1[I_MEAS_EN] = 1	Section 9.3.6
Sleep mode	Not available	Available, if SYS_CFG1[CYCLIC_ TIMER] ≠ 0	Available if enabled by setting SYS_CFG1[I_MEAS_EN] = 1, timing depends on SYS_CFG1[CYCLIC_TIMER] (it must be \neq 0)	Available if enabled by setting SYS_CFG1[I_MEAS_EN] = 1, timing depends on SYS_CFG1[CYCLIC_TIMER] (it must be \neq 0)	Section 9.3.5
other modes	Not available	Not available	Not available	Not available	

9.2 Power supplies and reset

9.2.1 Decoupling of power supplies

The recommended decoupling of power supplies is shown in <u>Figure 7</u> The capacitors should be placed close to the IC pins.

Battery cell controller IC

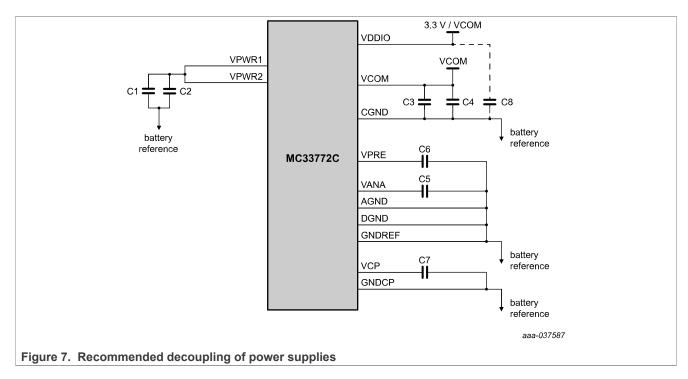


Table 11. Recommended capacitor values for power supply decoupling

ID	Value	Units	Comments
C1	220	nF	
C2	1	nF	
C3	2.2	μF	Ceramic capacitor
C4	220	pF	
C5	47	nF	Ceramic capacitor
C6	470	nF	
C7	10	nF	
C8	100	nF	Only necessary for 3.3 V SPI applications where VDDIO is not connected to VCOM

9.2.2 VPWR overvoltage, low-voltage

The MC33772C incorporates comparators to monitor VPWR pins for overvoltage and low-voltage conditions. In the event the voltage on VPWR pin is above the overvoltage threshold $V_{PWR(OV_Flag)}$ for greater than the $t_{VPWR(Filter)}$ period, the overvoltage fault flag is set in FAULT1_STATUS[VPWR_OV_FLT].

When unmasked by FAULT_MASK1[MASK_12_F], the FAULT1_STATUS[VPWR_OV_FLT] bit sets the FAULT output pin high. An overvoltage condition on the VPWR pin does not cause the MC33772C to perform a shutdown. The pack controller may clear the FAULT1_STATUS[VPWR_OV_FLT] bit when V_{PWR} returns to the normal operating range by writing logic 0 to the FAULT1_STATUS[VPWR_OV_FLT] bit.

When unmasked by FAULT_MASK1[MASK_11_F], a low-voltage condition on VPWR pin causes the FAULT1_STATUS[VPWR_LV_FLT] bit to be set. The FAULT1_STATUS[VPWR_LV_FLT] bit may be cleared when the normal operating range voltage resumes on the VPWR pin and by writing logic 0 to the FAULT1_STATUS[VPWR_LV_FLT] bit.

Battery cell controller IC

9.2.3 VCOM supply

The VCOM supply is a linear regulator used to supply power for communication, GPIOx, SPI interface, external temperature sensor reference, and optional external EEPROM.

The VCOM supply is monitored by the MC33772C for undervoltage. Excessive load on the VCOM pin activates VCOM current limit causing an undervoltage fault condition to occur. During the event, the FAULT2_STATUS[VCOM_UV_FLT] fault bit is set and the regulator enters t_{VCOM(RETRY)} shutdown/retry strategy.

Undervoltage shutdown of the VCOM supply directly affects communication, GPIO outputs and external temperature measurements. In addition to setting the individual fault bits for each ANx/GPIO, multiple faults may be set in the FAULTX STATUS register.

Faults may be cleared by the pack controller when communication resumes. VCOM also has a comparator that monitors for overvoltage. In the event the voltage on VCOM becomes greater than $V_{COM(OV)}$, the FAULT2_STATUS[VCOM_OV_FLT] fault flag is set.

9.2.4 VANA supply

The VANA supply is an internal 2.5 V supply used by the MC33772C for analog control. No circuits other than the decoupling capacitor should be terminated to the VANA pin. The VANA supply is monitored by the MC33772C for undervoltage. External load on the VANA pin activates the VANA current limit causing an undervoltage fault condition to occur. During the event, the FAULT2_STATUS[VANA_UV_FLT] fault bit is set and the regulator enters t_{VANA(retry)} shutdown/retry strategy.

Undervoltage shutdown of the VANA supply directly affects the performance of the analog to digital converters generating fault condition. Additionally, VANA is monitored by the ADC converter for an overvoltage condition each time a conversion sequence is performed. In the event VANA exceeds the $V_{ANA(OV)}$ threshold, the FAULT2 STATUS[VANA OV FLT] is set.

9.2.5 VPRE supply

The VPRE supply is an internal pre-regulator supply that sources power to low-voltage sections of the MC33772C. VPRE is the input supply to the VCOM and VANA regulators. The VPRE pin can only be connected to the decoupling capacitor and, in case the SPI communication mode needs to be selected, to one end of the $10 \text{ k}\Omega$ resistor, whose other end is connected to SPI COM EN.

9.2.6 VCP supply

The VCP is an internal power supply generated by a doubler charge pump that is fed by VPRE. The VCP pin can only be connected to a 10 nF decoupling capacitor. The other end of such capacitor must be connected to its dedicated ground, namely GNDCP.

9.2.7 VDDIO supply

The VDDIO is an external power supply that enters the IC through a pin having the same name. The purpose of it is supplying power to the SPI and I²C interfaces at 3.3 V or 5.0 V, depending on the input voltage. In 5.0 V applications, the VDDIO pin can be shorted to the VCOM pin, eliminating the use of an external supply.

9.2.8 Power on reset (POR)

The MC33772C has two sources of power on reset (POR) in the IC system. An undervoltage condition on the VPWR pin causes the MC33772C to reset. Upon returning from undervoltage, the MC33772C performs a POR.

Battery cell controller IC

The second source of potential POR occurs during transient conditions when the internal digital logic supply voltage drops below the critical threshold where logic states cannot be guaranteed. In this case, the MC33772C performs a power on reset.

Power on reset is indicated by the FAULT1_STATUS[POR] bit. In the event of a POR, all registers in the MC33772C are set to their power on reset state and the FAULT pin becomes active.

9.2.9 Hardware and software reset

An active high on the RESET pin for greater than the t_{RESETFLT} filter time causes the MC33772C to reset. Software resets are performed when the MC33772C receives a message written to the SYS_CFG1[SOFT_RST] bit. Hardware and software resets are indicated by the status of the FAULT1_STATUS[RESET_FLT] bit, and the FAULT pin becomes active. After a HW or SW reset, it is necessary to wait for the time interval t_{VPWR(READY)} before being possible to reprogram the part.

9.3 Modes of operation

From Reset mode, the MC33772C must be initialized with a cluster ID before the device is allowed to enter Normal mode. After initialization, the MC33772C enters Normal mode. In Normal mode the device is in full operation performing the necessary safety functions as well as on-demand conversions. When commanded to Sleep mode, the device will have reduced current consumption. Diagnostic mode provides a method for diagnosing the integrity of many safety functions as well as internal or external faults that may have occurred. If properly configured, if there is no traffic during Normal mode on the bus during t_{COM_LOSS} , the MC33772C will reset.

In the event the device is powered up and not initialized, the MC33772C enters the low-power Idle mode after a t_{IDLE} timeout period. Detecting a wake-up pattern transfers the MC33772C to the initialization state Init where the CID can be programmed. In <u>Figure 8</u>, an integer number enclosed in round brackets close to a transition arc indicates the priority of such a state transition in case the conditions are verified at the same time. The lower the number is, the higher is the priority, so if several conditions are true at the same time, the one with lowest priority number determines the state transition; a boolean condition is enclosed between square brackets. A list of actions after the state transition condition is preceded by the slash symbol. Symbol "t" represents the absolute time, symbol t₀ stays for a variable having the dimension of time.

Battery cell controller IC

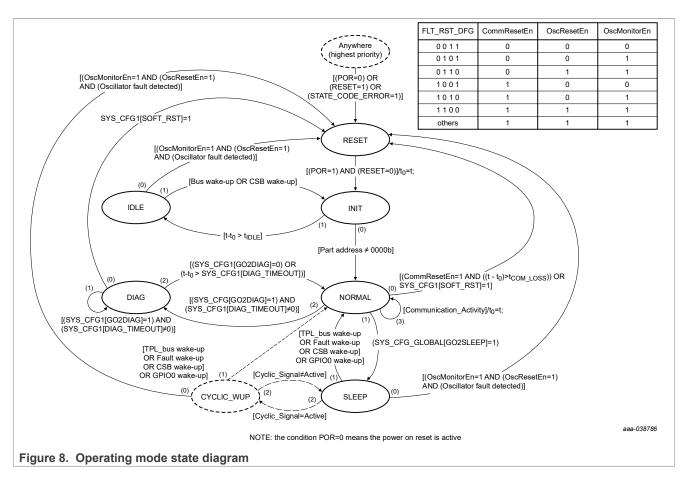


Table 12. Power supply mode operation

	Normal/Init mode	Diagnostic mode	Cyclic Wake-up	Sleep/Idle mode
Supplies active	VCOM = ON,	VCOM = ON,	VCOM = ON (during cycle),	VCOM = 0,
	VANA = ON,	VANA = ON,	VANA = ON (during cycle),	VANA = 0,
	VPRE = ON,	VPRE = ON,	VPRE = ON,	VPRE = ON,
	VCP = ON	VCP = ON	VCP = ON	VCP = ON
Communication	Communication enabled	Communication enabled	Communication enabled (during cycle)	Wake-up function only

9.3.1 Reset mode

The table in <u>Figure 8</u> provides information about the mapping between all possible values of the SYS_CFG2[FLT_RST_CFG] field, which may be written and read by the user, and the corresponding values of the following internal bits, which are not user readable:

- CommResetEN: If it is equal to 1, the IC reset due to a communication timeout in Normal mode is enabled, else it is disabled
- OscResetEN: If it is equal to 1, the IC reset due to the detection of a defective oscillator in Sleep mode is enabled, else it is disabled
- OscMonitorEN: If it is equal to 1, the oscillator monitoring is enabled, else it is disabled

The value "others" readable in the column labeled as SYS_CFG2[FLT_RST_CFG] refers to values that are different from those listed above.

The registers are reset to their default values, except some bits of the FAULT1_STATUS register.

MC337720

Battery cell controller IC

9.3.2 Idle mode

The MC33772C enters Idle mode from Init mode when the communication bus is not active for the t_{IDLF} time period. While the MC33772C is in Idle mode, no messages are recognized, only a valid wake-up sequence lets the device transition from Idle mode to Init mode. When the MC33772C is configured as a SPI interface and enters Idle mode, the device transitions from Idle mode to Init mode if CSB duration is larger than CSB_{WILFLT} maximum value, otherwise the pulse will be considered as a glitch and then filtered.

9.3.3 Init mode

After a Power On Reset (POR) or Reset (Soft RST or pin RESET), the MC33772C enters Init mode. The MC33772C's cluster ID is 0 (unassigned CID). All registers, except the Init register, are read-only. In Init mode, any unassigned MC33772C does not forward any message and responds (if needed) only on the side that received a request. The user has to assign a Cluster ID between 1 and 63, to enter Normal mode. This assignment is mandatory for both SPI and TPL communication. If the assignment of a Cluster ID is not performed within the t_{IDLF} timeout, Idle mode will be entered to reduce current consumption.

9.3.4 Normal mode

In Normal mode, on reception of a valid message, the MC33772C executes the commanded operation. Device configuration registers control the operating characteristics of the MC33772C and are all programmed while the device is in Normal mode. Once programmed, the MC33772C performs safety operations like overvoltage and undervoltage in the background without further instruction from the pack controller¹.

To accomplish the safety operations in Normal mode, the MC33772C performs a cyclic conversion sequence at the programmed timed interval. In the event the MC33772C receives an on-demand conversion request from the pack controller during a cyclic conversion, the device stops the cyclic conversion and immediately starts the on-demand conversion cycle. Halting the cyclic conversion and performing the on-demand conversion allows all MC33772C devices in the system to achieve synchronized measurements. From Normal mode, the MC33772C may be commanded to Sleep mode or Diag mode. If instructed by a proper value of the SYS CFG2[FLT RST CFG] field, the part automatically resets whenever the communication is absent for longer than t_{COM LOSS}.

9.3.5 Sleep mode

Sleep mode provides a method to significantly reduce battery current and the overall quiescent current of the battery management system. In Sleep mode, the overvoltage, undervoltage, overtemperature, undertemperature, and overcurrent circuitry can remain cyclically active², as well as the monitoring of V_{PWR}.

Based on the CYCLIC_TIMER setting, the MC33772C may continue performing cyclic conversions in Sleep mode. This is the meaning of the dotted bubble labeled as CYCLIC WUP in the state diagram shown in Figure 8. The permanence time in the CYCLIC WUP transient state is really short; it is basically the time needed to turn on the VCOM power supply and to acquire 20 channels.

In the event a conversion value is greater than or less than the threshold value and the particular wake-up/fault is unmasked, the MC33772C performs a bus wake-up and can activate the FAULT pin.

To instruct the MC33772C to enter the Sleep mode, the user sets the SYS_CFG_GLOBAL[GO2SLEEP] bit to logic 1. If the communication type is TPL, only a global write command can be used, while in case of pure SPI communication, a local write command is necessary. In case the ADCs are performing acquisition (for a single sample or an average of N samples), the transition is delayed until the ongoing sequence is completed. It means that a single sample will be correctly acquired while an average will be potentially interrupted; in this

¹ The cyclic measurement is disabled by default. Cyclic measurement can be activated by writing to SYS_CFG1[CYCLIC_TIMER].

² The cyclic measurement is disabled by default. Cyclic measurement can be activated by writing to SYS_CFG1[CYCLIC_TIMER].

Battery cell controller IC

latter case MEAS_CELLx registers cannot be updated (DATA_RDY bit stays at 0 until the completion of the next average).

Exit from Sleep mode is possible if one of the following occurs:

- · Upon detection of a bus wake-up sequence, in TPL mode only
- By transitioning the CSB pin from low state to high state (shortly referred to as CSB wake-up)
- Upon detection of at least one out of a certain number of fault conditions (see FAULT1_STATUS, FAULT2_STATUS and FAULT3_STATUS along with their associated wake-up mask registers WAKEUP MASK1, WAKEUP MASK2 and WAKEUP MASK3)³
- Depending on the content of SYS_CFG2[FLT_RST_CFG] field, it is possible to set the OscResetEn variable
 to 1. This causes a reset if the oscillator monitor function detects a clock malfunction, signaled by the
 FAULT2_STATUS[OSC_ERR] = 1
- Wake-up by GPIO0

The CSB wake-up capability implies some system considerations when SPI communication is used. Assuming the CSB line is pulled up to the same power supply used by the MCU, when the MCU commands the MC33772C to go to sleep and then the MCU itself goes to sleep, both devices sleep until the time the MCU wakes up. However, when this happens, the MC33772C wakes up because the CSB line transitions from low state to high state. To avoid this behavior, the MCU has to take care to force the CSB line to the high state during the entire sleep time.

9.3.6 Diagnostic mode

In Diagnostic mode, the system controller has extended control of the MC33772C in order to execute performance integrity checks of the device. It is critical to note that when the MC33772C is in Diagnostic mode, cyclic conversions are halted and OV/UV/OT/UT detection is not performed automatically. To perform OV/UV/OT/UT or any other protection feature that requires a conversion, an on-demand conversion message must be sent by the pack controller.

To prevent the MC33772C from remaining in diagnostic mode without automatic OV/UV/OT/UT detection, a protection DIAG_TIMEOUT timer has been implemented. In the event of the timeout, the MC33772C reverts to Normal mode and sets the bit FAULT3_STATUS[DIAG_TO_FLT] to logic 1.

To enter diagnostic mode, the user must set the SYS_CFG1[GO2DIAG] bit to logic 1. To exit diagnostic mode, the user must clear the SYS_CFG1[GO2DIAG] bit.

Note: If cyclic acquisition is enabled, before transitioning to diagnostic mode, the cyclic acquisition needs to be disabled. Disabling of cyclic acquisition and GO2DIAG should be two separate commands sent by MCU.

9.4 Analog to digital converters ADC1-A, ADC1-B, ADC2

At the heart of the MC33772C are three hybrid ADCs using a 6.0 MHz clock and having two modes of operation, called *phases*:

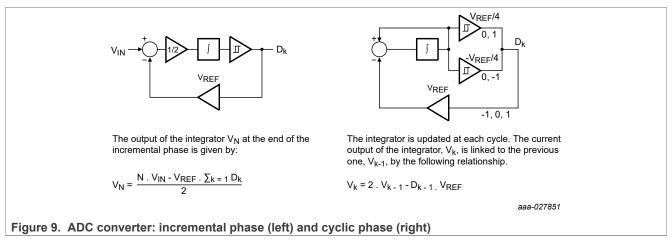
- Incremental phase: it is necessary to compute the most significant bits. During this first phase, the ADC operates as shown in <u>Figure 9</u> (left part). It appears equal to a 1st order ΣΔ, but it has no memory, as the initial state is always 0.
- The second phase, referred to as cyclic phase, is needed to extract the least significant bits. During this
 phase, the converter is blind to the input (but not to the reference) and performs the conversion of the residual
 error.

MC337720

³ The wake-up performed by MC33772C under the detection of internal fault is disabled by default. It can be activated by writing to registers WAKEUP MASK1, WAKEUP MASK2 and WAKEUP MASK3.

Battery cell controller IC

This ADC, which is built around a switched capacitor integrator, is much faster than a $\Sigma\Delta$, an essential feature when the input comes from a multiplexer and the channel switching has to be very fast. There is no decimation downstream the ADC.



The ADC architecture affords the user the flexibility to select the speed vs. accuracy. Conversion resolution setting for ADC1-A, ADC1-B and ADC2 are programmable from 13 to 16 bits (see <u>Section 11.7 "ADC configuration register – ADC_CFG"</u>). ADC1-A and ADC1-B settings must be equal to each other.

9.4.1 High precision voltage reference

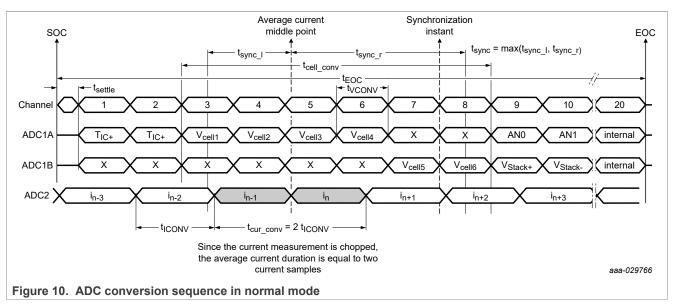
To guarantee the accuracy of all ADC conversion data, the MC33772C integrates a high precision fully compensated voltage reference.

9.4.2 Measurement sequence

The MC33772C performs on-demand differential measurements of external inputs and internal measurements using three ADC converters for measurement, calibration, and diagnostics. Once the device is initialized, on-demand conversions are initiated by writing to the ADC_CFG[SOC] convert register or a GPIO2 input trigger.

The ADC_CFG register contains the conversion parameters for ADC1-A, ADC1-B, and ADC2 converters and the start conversion bit for synchronization. Writing a logic 1 to the SOC bit initiates the conversion sequence. Conversions in progress may be interrupted by reinitiating a new conversion. Measurements for each ADC converters in the MC33772C have a predefined measuring sequence. Voltage conversions coming from ADC1-A and ADC1-B are synchronized with free running current measurements performed by ADC2.

Battery cell controller IC



Immediately after receipt of a conversion request, there is a dead time t_{SETTLE}, after which ADC1-A and ADC1-B converters start their conversion sequence. Voltage conversions of ADC1-A and ADC1-B run asynchronously with the current measurements performed by ADC2 as shown in Figure 10.

At time t_{CELL_CONV} , all voltage and current samples are frozen and then post-elaborated. Offset is measured and canceled, a multiplicative correction with a gain depending on the IC die temperature is performed. The completion of the entire sequence, whose length is equal to 20 time slots, occurs at time t_{EOC} . All results are stored into user registers and their associated data ready bits are set to Logic 1. Channels identified as "internal" are used for calibration purposes and are performed at each conversion sequence. Information on how the data is tagged and stored is provided in <u>Section 10 "Communication"</u>. On-demand conversions are not only used for storing measurement results in user registers, but also for OV/UV/OT/UT comparisons.

The MC33772C features a synchronized voltage and current measurements for each requested conversion. Synchronization point is after the 7th channel, that is, at this time the IC takes a snapshot of the latest two chopped conversions of the current signal, the average of which is calculated to get rid of the current offset.

The meaning of the time t_{SYNC} is the maximum value of two time intervals, t_{SYNC} L and t_{SYNC} R, where:

- t_{SYNC_L} is the time interval between the middle point of the first voltage conversion and the instant corresponding to middle point of the latest valid average current value
- t_{SYNC_R} is the time interval between the previously mentioned instant and the middle point of the eighth converted channel

<u>Table 13</u> shows how the user channels are mapped in the 20 available time slots per ADC. Symbols Vbg_tj_a and Vbg_tj_b correspond, respectively, to contents of MEAS_VBG_DIAG_ADC1A and MEAS_VBG_DIAG_ADC1B registers. They represent the measurements of the same diagnostic band gap.

Table 13. ADC conversion sequence multiplexer inputs

ADC conversion	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20
ADC1-A	IC temp	IC temp	Cell 1	Cell 2	Cell 3	Cell 4			AN0	AN1	AN2	AN3	AN4	AN5	AN6	Vbg_tj_a	internal	internal	internal	internal
ADC1-B							Cell 5	Cell 6	Stack	Stack	internal	VANA	Vbg_tj_b	internal						

In addition to on-demand conversion requests, the MC33772C provides timing control for cyclic measurements, that is, conversions occurring with no need for the pack controller to repeatedly send SOC commands. Cyclic measurements are useful for automatic OV/UV/OT/UT check. The user may select the cycle period by programming register SYS_CFG1[CYCLIC_TIMER]. The effective duration of a cyclic sequence is given by the teoc parameter. A cyclic sequence does not affect the content of the measurement registers (namely, of

Battery cell controller IC

registers MEAS_xxxx), while it has effect on the content of CELL_OV_FLT, CELL_UV_FLT, AN_OT_UT_FLT and FAULTx_STATUS registers.

An undervoltage on VANA might alter the functioning of the ADC. This could result in the detection of nonexistent faults. Therefore, if FAULT2_STATUS[VANA_UV_FLT] is set, the following faults should be ignored:

- FAULT1 STATUS[VPWR OV FLT]
- FAULT1 STATUS[AN UT FLT]
- FAULT1 STATUS[CT OV FLT]
- FAULT2_STATUS[VANA_OV_FLT]
- FAULT2 STATUS[ADC1 A FLT]
- FAULT2_STATUS[ADC1_B_FLT]
- FAULT3 STATUS[VCP UV]

9.4.2.1 Voltage averaging

The MC33772C provides a feature of on-demand, on-chip voltage averaging. Using this feature, cell terminal voltage, Vstack voltage, and VrefA and VrefB voltages can be averaged for a configured number of samples. Averaging makes the measurement data more robust to noise, the averaging feature acts as a digital low pass filter. The on-chip averaging feature of MC33772C reduces the MCU load by performing the averaging on-chip and also reducing the number of communication frames to be exchanged between master and slave.

After initialization of MC33772C, averaging can be triggered by configuring the ADC_CFG register as described in <u>Section 11.7 "ADC configuration register – ADC_CFG"</u>. The number of samples to be averaged is chosen by writing to bit-field ADC_CFG[AVG] and accumulation of samples to be averaged is initiated by setting bit-field ADC_CFG[SOC] to logic 1 or by triggering GPIO2 input. Once the averaging is started the MC33772C accumulates the configured number of samples and divides the accumulated value by the number of configured samples. The final value is updated in MEAS_CELLxx registers.

Ongoing accumulation of samples can only be interrupted by the GO2SLEEP and GO2DIAG commands. However, the averaging can be restarted with a new SOC command. On reception of a new SOC command, the MC33772C discards the ongoing measurement (accumulation) and starts the new measurement. It is to be noted that the feature of voltage averaging is not available for cyclic measurement.

In Normal mode, during ongoing averaging the device can interrupt the voltage averaging and change its mode of operation. However, the GO2SLEEP and GO2DIAG commands have certain priority over averaging. The MC33772C performing averaging is able to transition to Sleep or Diagnostic mode on reception of a valid GO2SLEEP or GO2DIAG command but only after completion of the ongoing sequence of measurement.

9.4.3 Measurement processing

After all channels are converted, they need to be post-processed. Three operations are performed before the final value is available:

- · Offset compensation
- · Gain compensation
- · Temperature compensation

This can be seen in <u>Table 14</u>. The columns labeled as "Gain comp.?" and "By..." show if the input signals are gain compensated (yes/no) and by which gain. For instance, GCF_c1 stays for a gain, which may be calculated by using GCF_room_c1, GCF_hot_c1 and GCF_cold_c1 variables specified in <u>Table 89</u>. In this table, attributes "cold" and "hot" refer to –40 °C and 89 °C respectively, and attribute room refers to 25 °C. A gain mayor may not depend on the temperature (column "Temp. comp.?" may attain the value yes or no). If a gain depends on the IC temperature, there are three scalar gains. For instance, GCF_cold_cx, GCF_room_cx, GCF_hot_cx represent respectively the delta gain compensation values at cold (–40 °C) room (+25 °C) and hot (+89 °C)

MC33772C

Battery cell controller IC

temperature of the die. They are used to calculate, by delta gain compensation, the actual value of gain at any temperature.

ADC2 works with GCF_ix (x = 4, 16, 64, 256), depending on the current gain used by the PGA. See <u>Table 89</u>. The value of a gain is centered on the targeted channel resolution, so it is of the form 1 + DG. Therefore, DG is centered on zero and is represented in two's complement. In the IC, only the DG part of the gain needs to be stored. See <u>Table 15</u>.

Table 14. Gain compensation

Table 14.	1	Compense				I				
Measured channel				Ву	Temp. comp.?	Result stored in	checked by	in the range of		
By ADC1-A										
ICTEMP1	1	Chopper	Yes	GCF_IcTemp	No	MEAS_IC_TEMP				
ICTEMP1	2	Chopper	Yes	GCF_IcTemp	No	MEAS_IC_TEMP				
CT1	3	Yes	Yes	GCF_c1	Yes	MEAS_CELL1	IC	CT1_UV_TH	CT1_OV_TH	
CT2	4	Yes	Yes	GCF_c2	Yes	MEAS_CELL2	IC	CT2_UV_TH	CT2_OV_TH	
CT3	5	Yes	Yes	GCF_c3	Yes	MEAS_CELL3	IC	CT3_UV_TH	CT3_OV_TH	
CT4	6	Yes	Yes	GCF_c4	Yes	MEAS_CELL4	IC	CT4_UV_TH	CT4_OV_TH	
Unused	7									
Unused	8									
AN0	9	Yes	Yes	GCF_ANx_ratio [1]	No ^[1]	MEAS_AN0	IC	AN0_UT_TH	AN0_OT_TH	
AN1	10	Yes	Yes	GCF_ANx_ratio [1]	No ^[1]	MEAS_AN1	IC	AN1_UT_TH	AN1_OT_TH	
AN2	11	Yes	Yes	GCF_ANx_ratio [1]	No ^[1]	MEAS_AN2	IC	AN2_UT_TH	AN2_OT_TH	
AN3	12	Yes	Yes	GCF_ANx_ratio [1]	No ^[1]	MEAS_AN3	IC	AN3_UT_TH	AN3_OT_TH	
AN4	13	Yes	Yes	GCF_ANx_ratio [1]	No ^[1]	MEAS_AN4	IC	AN4_UT_TH	AN4_OT_TH	
AN5	14	Yes	Yes	GCF_ANx_ratio ^[1]	No ^[1]	MEAS_AN5	IC	AN5_UT_TH	AN5_OT_TH	
AN6	15	Yes	Yes	GCF_ANx_ratio ^[1]	No ^[1]	MEAS_AN6	IC	AN6_UT_TH	AN6_OT_TH	
V _{BG_TJ}	16	Yes	Yes	GCF_Vbgtj1	Yes	MEAS_VBG_DIAG_ADC1A	IC	Internal r	eference	
Reserved	17									
Reserved	18									
Reserved	19									
Reserved	20									
By ADC1-B							<u>'</u>			
Unused	1									
Unused	2									
Unused	3									
Unused	4									
Unused	5									
Unused	6									
CT5	7	Yes	Yes	GCF_c5	Yes	MEAS_CELL5	IC	CT5_UV_TH	CT5_OV_TH	
CT6	8	Yes	Yes	GCF_c6	Yes	MEAS_CELL6	IC	CT6_UV_TH	CT6_OV_TH	
Stack	9	Chopper	Yes	GCF_stack	No	MEAS_STACK				
Stack	10	Chopper	Yes	GCF_stack	No	MEAS_STACK				
Reserved	11									
VANA	12	Yes	Yes	GCF_c1	Yes	ADC1_B_RESULT	IC		VANA_OV_TH	
V _{BG_TJ}	13	Yes	Yes	GCF_Vbgtj2	Yes	MEAS_VBG_DIAG_ADC1B	IC	Internal r	eference	
Reserved	14									
Reserved	15									
Reserved	16									
Reserved	17									
By ADC2										
ISENSE	1	Chopper	Yes	GCF_i4-256	Yes	MEAS_I	IC		TH_ISENSE_H	
ISENSE	2	Chopper	Yes	GCF_i4-256	Yes	MEAS_I	IC		TH_ISENSE_H	

Battery cell controller IC

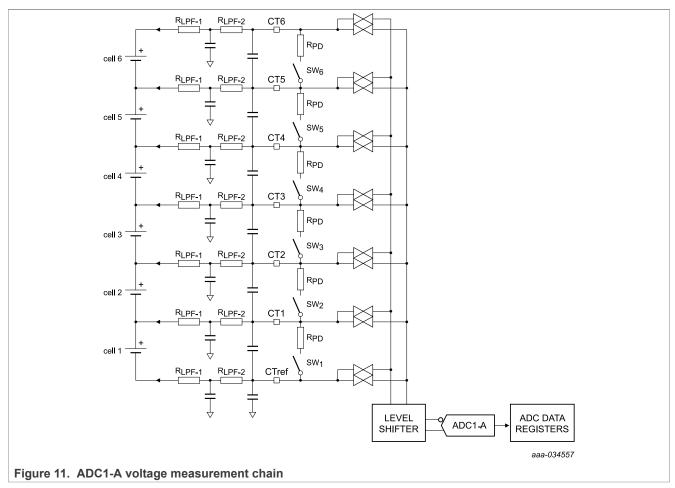
[1] It is assumed that all ANx have been programmed as ratiometric; in case a certain ANx is programmed as an absolute input, the gain GCF_ANx_ratio gets replaced by GFC_c1 and the 'No' value contained in the column labeled 'Temp. comp.?' is replaced by a 'Yes'.

9.5 Cell terminal voltage measurement

Cell terminal voltages are monitored differentially, level shifted and multiplexed to the ADC1-A and ADC1-B converters. Conversion results of the cells are available in MEAS CELLx registers.

Unused cell terminal (CTx) inputs may be terminated as shown in <u>Figure 1</u> or as described in <u>Section 13.2.2</u> "<u>Unused cells</u>". Overvoltage and undervoltage of unused inputs should be disabled through the OV_UV_EN[CTx_OVUV_EN] bits to prevent the input from triggering fault events. Conversions performed on unused inputs result in nearly zero ADC values.

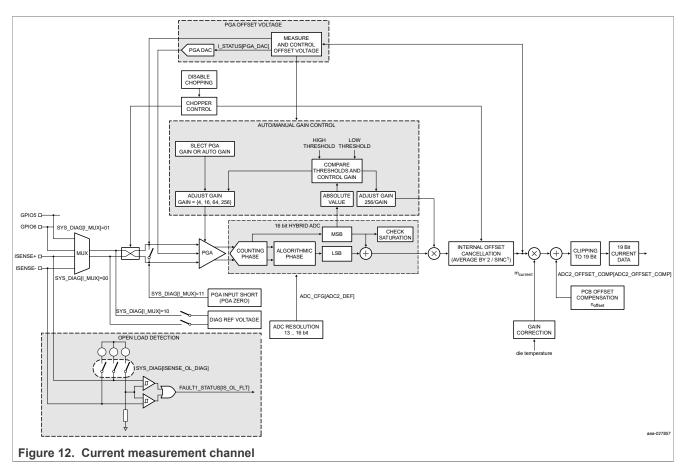
The differential measurement of each cell terminal input is designed to function in conjunction with external antialiasing filter (see <u>Section 13.2 "MC33772C External Components"</u>).



9.6 Current measurement

Current measurement channel features 16-bit ADC with an automatic programmable gain amplifier (PGA) allowing the user to accurately measure current from -1500 A to 1500 A (the actual range is in terms of voltage and is given by min and max of V_{IND}) with a 6.0 mA resolution (in terms of voltage it is V_{2RES}) when using a single $100~\mu\Omega$ shunt resistor. The current channel includes automatic gain selection, redundant measurement path, and internal diagnostics.

Battery cell controller IC



From initialization, the current measurement chain is disabled. The MCU controller must enable the measurement chain by setting the SYS_CFG1[I_MEAS_EN] bit to logic 1, to initiate continuous current conversions. Current measurement conversions for coulomb counting are performed continuously in Normal and Diagnostic modes, while in Sleep mode they occur periodically and the period is given by SYS_CFG1[CYCLIC_TIMER].

Note: The conversion command ADC_CFG[SOC] must be sent at least 27 µs after SYS_CFG1[I_MEAS_EN] is enabled.

The Current Acquisition Channel fulfills accuracy and dynamic range requirement through:

- The Auto-Zero Compensation feature is guaranteeing the PGA dynamic range.
- A chopper function is ensuring a reduced offset introduced by the acquisition Chain.

The automatic auto-zero compensation for the PGA is performed each time the current measurement channel gets enabled. The time to perform the procedure is given by the parameter t_{AZC_SETTLE} .

To minimize the offset introduced by the acquisition chain, the chopper sends alternatively and repetitively, the ISENSE+/– differential inputs and the ISENSE–/+ differential inputs (reverse input pair) to the PGA differential inputs. Downstream the ADC2, a digital post-processor computes the difference between the current sample and the past sample and divided it by 2. Therefore, the offset introduced by the acquisition chain is cancelled.

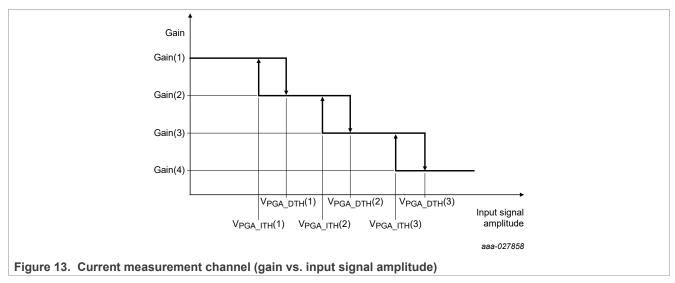
Conversion result of current channel will be stored into MEAS_ISENSE1[MEAS_I_MSB] and MEAS_ISENSE2[MEAS_I_LSB] with a resolution of V_{2RES} , which remains the same regardless of the PGA Gain setting.

Note: A conversion started with an ADC_CFG[AVG] bit-field set to a non-zero value would result in the toggling of MEAS_ISENSE1[DATA_RDY] and MEAS_ISENSE2[DATA_RDY] between 0 and 1 for each voltage

measurement sequence, unless the configured number of sequences are completed. At the end of averaging, the bit MEAS_ISENSEx[DATA_RDY] is stable at the end of last sequence.

The PGA gain of the current acquisition channel (4, 16, 64, 256) can either be set in a manual or an automatic mode. The setting of the PGA gain in manual or automatic mode can be performed by configuring ADC_CFG[PGA_GAIN] register.

The setting of the PGA gain in automatic mode will also be performed by the automatic gain control. Automatic gain control allows the device to obtain the most appropriate gain setting for the amplifier input signal level. In automatic gain control mode, the conversion result is digitally compared with internally programmed thresholds. See Figure 13.



PGA auto-gain is implemented by applying a hysteresis to each threshold. Saturation of the ADC is reported by the flag MEAS_ISENSE2[ADC2_SAT]. A PGA setting change between two chopped measurements is reported by the flag MEAS_ISENSE2[PGA_GCHANGE] to indicate reduced accuracy for the resulting measurement value. An external low-pass filter is required to prevent an over range event within the PGA. Such event may happen if the time derivative of the current signal is so high that it causes the voltage drop across the ISENSE +/- terminals to exceed the maximum allowed slope value of ±4 V/s. The way this limit on the slope has to be understood is the following: if the battery current changes like a large ideal step, the output signal of the input filter must have a slope whose absolute value must not exceed the aforementioned value. So, this limit only applies to large signals, that is, it does not apply, for example, to a sinusoidal current signal having small amplitude but very large frequency, because a small signal normally does not require a change in the gain value. Large signal signifies that the signal magnitude is so high that the PGA gain is required to be switched to a value different from the currently used one.

ADC2, dedicated to the current measurement channel, performs continuous conversions in Normal and Diagnostic modes. Receiving an on-demand conversion request, the most recent current measurement obtained before the last cell voltage gets converted is stored in MEAS_ISENSE1 and MEAS_ISENSE2 registers, so synchronizing the current with all voltages within the t_{SYNC} window.

The current measurement channel includes a sleep mode wake-up feature. In Sleep mode, the PGA gain is constantly equal to 256 and each cyclic current measurement result is compared with the current wake-up threshold TH_ISENSE_OC register. Three out of four current values above the threshold trigger a system wake-up and activate the fault output when the wake-up enable bit is set.

Note: If current sense is active (SYS_CFG1[I_MEAS_EN]=1) during sleep mode, cyclic acquisition should not be set to continuous mode (SYS_CFG1[CYCLIC_TIME]=001).

9.6.1 Gain correction of the current channel

The following is a detailed explanation of the gain correction of the current channel.

- Room temperature delta gains:
 - GCF_ix (for x = 4, 16, 64, 256 representing all possible PGA gains) with resolution 0.09765625 %, spanning the range (-256...+255).0.09765625 %
- Cold temperature delta gains:
 - GCF_cold_ix (for x = 4, 16, 64, 256 representing all possible PGA gains) with resolution 0.09765625 %, spanning the range (-16...+15).0.09765625 %
- Hot temperature delta gains:
 - GCF_hot_ix (for x = 4, 16, 64, 256 representing all possible PGA gains) with resolution 0.09765625 %, spanning the range (-16...+15).0.09765625 %

In contrast to i_gain_x, which is represented by a 9-bit word, GCF_hot_ix and GCF_cold_ix are represented by a reduced number of bits (5) and therefore their range is 16 times smaller than the one at room temperature, because the resolution is the same for all gains. Basically GCF_hot_ix and GCF_cold_ix can only additively correct the i_gain_x respectively in hot and cold conditions. This becomes clear by considering the gain temperature dependency, which is as follows:

If (temperature T is higher than T_room) Then // T is the IC temperature

gain_selected = GCF_hot_ix

Else

gain selected = GCF cold ix

EndIf

DG = GCF_ix + (gain_selected * k(T)) // where k(T) is a stored function, such that: $0 \le k(T) \le 1$, k(T_room) = 0 and k(T_cold) = k(T_hot) = 1

Gain = 1 + DG

Table 15. Gain format

Gain = 1 + DG (DG)	Representation: 2's complement (number of bits)	Min (%)	Max (%)	Resolution (%)
GCF_room_cx (odd cell)	10	-6.2500	6.2378	0.01221
GFC_room_c(x+1)vs(x) (even cell vs odd cell)	4 for x = 1 2 for x ≠ 1	-0.098 for x = 1 -0.024 for x \neq 1	0.085 for $x = 1$ 0.012 for $x \ne 1$	0.01221
GFC_cold_cx (odd cell) (cold temp vs room)	7 for $x = 1$ 6 for $x \ne 1$	-0.781 for x = 1 -0.391 for x \neq 1	0.769 for $x = 1$ 0.378 for $x \neq 1$	0.01221
GFC_cold_c(x+1)vs(x) (even cell vs odd cell)	6 for x = 1 2 for x ≠ 1	-0.391 for x = 1 -0.024 for x \neq 1	0.378 for $x = 1$ 0.012 for $x \ne 1$	0.01221
GFC_hot_cx (odd cell) (hot temp vs room)	7 for $x = 1$ 6 for $x \ne 1$	-0.781 for x = 1 -0.391 for x \neq 1	-0.769 for x = 1 -0.378 for x \neq 1	0.01221
GFC_hot_c(x+1)vs(x) (even cell vs odd cell)	5 for $x = 1$ 3 for $x \neq 1$	-0.195 for x = 1 -0.049 for x \neq 1	0.183 for $x = 1$ 0.037 for $x \ne 1$	0.01221
GFC_Vbgtj1-2 (diagnostic voltage reference) ^[1]	8	-3.1250	3.1006	0.02441
GFC_i4-256 (current)	9	-25.0000	24.9023	0.09766
GFC_stack (stack voltage)	7	-3.1250	3.0762	0.04883

MC337720

Battery cell controller IC

Table 15. Gain format...continued

Gain = 1 + DG (DG)	Representation: 2's complement (number of bits)	Min (%)		Resolution (%)
GCF_ANx_ratio (ANx ratio)	5	-1.5625	1.4648	0.09766
GCF_lcTemp (IC temperature)	4	-3.1250	2.7344	0.39063

^[1] This gain compensation factor is relative to GCF_c1.

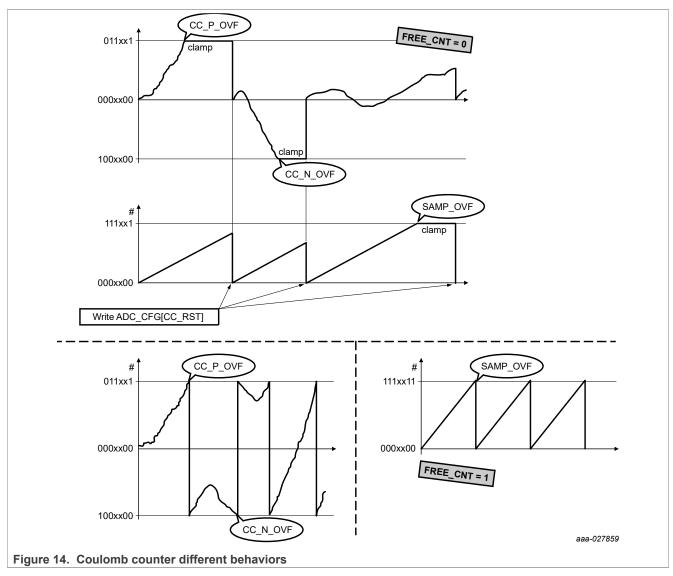
9.7 Coulomb counting

All conversions of ADC2 increment the internal coulomb counter, referred to as COULOMB_CNT, which represents the discrete integral of ADC2 samples, where the time index can only take positive integer values. COULOMB_CNT is copied to registers COULOMB_CNT1, COULOMB_CNT2. In addition to this, the MC33772C provides the number of accumulated samples in register CC_NB_SAMPLES, which represents the elapsed time expressed in integer units. The coulomb counter registers COULOMB_CNT1, COULOMB_CNT2 and CC_NB_SAMPLES are reset by writing the ADC_CFG[CC_RST] reset bit.

The registers CC_NB_SAMPLES/COULOMB_CNT1/COULOMB_CNT2 are updated if a write command has been done on one of these 3 registers (updated at next read) or if a read/write command has been done on another register (updated at next read). If the 3 registers are read in loop without any write or read command on other registers, their values are not updated.

In the event an overflow occurs in either COULOMB_CNT or CC_NB_SAMPLES, the CC_OVR_FLT bit is set and, when unmasked, the FAULT pin is activated. The coulomb count value is impacted by conversions performed during diagnosis of the current measurement chain.

Battery cell controller IC



The COULOMB_CNT is an integer whose associated resolution is V_{2RES} , therefore, COULOMB_CNT· V_{2RES} gives μV . If the shunt resistance R_{SHUNT} is expressed in $\mu \Omega$, then COULOMB_CNT· V_{2RES} / R_{SHUNT} gives A.

The coulomb counting feature allows the pack controller to compute the average current. Value of R_{SHUNT} is only owned by the pack controller. By assuming two snapshots of the above mentioned registers are taken at two consecutive times T_{k-1} and T_k , the ratio $Iav_k = (ACC_k - ACC_{k-1}) / (N_k - N_{k-1})$ provides the average value of the current during the time interval $(T_k - T_{k-1})$, where ACC_k and ACC_{k-1} are the values of the quantity $COULOMB_CNT \cdot V_{2RES} / R_{SHUNT}$ respectively at times T_k and T_{k-1} , and N_k and N_{k-1} are the values of $CC_NB_SAMPLES$ corresponding to the same two instants. To get an electric charge, the pack controller needs to multiply the ratio Iav_k by $(T_k - T_{k-1})$ to get an electric charge.

Reading one of the three user registers (COULOMB_CNT1, COULOMB_CNT2, CC_NB_SAMPLES) triggers the MC33772C to copy the content of the coulomb counter internal registers into these three user registers. The content of the coulomb counter user registers is updated only when an address different from \$2D, \$2E, and \$2F is read, and then one or more of the registers (COULOMB_CNT1, COULOMB_CNT2, CC_NB_SAMPLES) are read again.

It is important to reset the entire coulomb counter status each time the type of input source is changed. In fact, the coulomb counter integrates not only the current signal, but also other possible diagnostic inputs.

If the bit ADC2_OFFSET_COMP[CC_RST_CFG] is set to logic 1, reading any coulomb counter register (from @ \$2D to @ \$2F) also resets the coulomb counter.

The coulomb counter can behave in two different ways: clamping mode (by setting ADC2_OFFSET_COMP[FREE_CNT] = 0) and rollover mode (by setting ADC2_OFFSET_COMP[FREE_CNT] = 1): see Figure 14.

Flags ADC2_OFFSET_COMP[CC_P_OVF] and ADC2_OFFSET_COMP[CC_N_OVF] respectively signal an occurred overflow or an occurred underflow in the coulomb counter accumulator; they can be reset to zero by writing a logic 0 in those bits.

The flag ADC2_OFFSET_COMP[SAMP_OVF] signals an occurred overflow of the number of samples. It can be reset to zero by writing a Logic 0 in it. Any kind of occurring overflow is reflected in the content of the FAULT3_STATUS[CC_OVR_FLT] bit as well.

If ADC2 is enabled (SYS_CFG1[I_MEAS_EN] = 1) AND cyclic measurement is active (SYS_CFG1[CYCLIC_TIMER] ≠ 0), the coulomb counter is calculated also in sleep mode. If so, each time the device is entering into Cyclic Wake-Up mode at the period equal of the cyclic timer configured according to SYS_CFG1[CYCLIC_TIMER], the current will be measured, with PGA gain set to 256, and integrated in the Coulomb Counter. The number of samples accumulated in the Coulomb Counter will also be incremented by 1.

If any fault condition occurs by these operations, depending on the fault and wake-up mask configuration, the device is awakened and the fault line is activated, including the case where the coulomb counter crosses the threshold TH_COULOMB_CNT, which is specific to Sleep mode and produces the setting of both ADC2_OFFSET_COMP[CC_OVT] and FAULT3_STATUS[CC_OVR_FLT] bits.

When the device transitions from Sleep mode to Normal mode, the coulomb counter is frozen until it is read and reset by the user, and the acquisition speed is turned from the configured one (by the cyclic timer SYS CFG1[CYCLIC TIMER]) to continuous.

TYPE A (free running mode with explicit reset):

CONFIGURATION instructions:

- 1. SYS CFG1[IMEAS EN] = 1; // Enable the current measurement
- 2. ADC2_OFFSET_COMP[FREE_CNT] = 1; // Select the free running mode
- 3. ADC2_OFFSET_COMP[CC_RST_CFG] = 0; // Do not reset to zero upon read

RESET instructions:

- 1. write ADC CFG[CC RST] = 1; // Reset to zero:
- COULOMB_CNT = COULOMB_CNT_old = CC_NB_SAMPLES_old = Time = Time_old = 0; // Variables initialization

NORMAL USE instructions:

- 1. Time = get_abs_time(); // Get the absolute time
- 2. Read registers COULOMB_CNT1, COULOMB_CNT2 and CC_NB_SAMPLES;
- 3. COULOMB_CNT = (COULOMB_CNT1, COULOMB_CNT2); // Concatenate MSB and LSB
- 4. I_AVG = (COULOMB_CNT COULOMB_CNT_old)/(CC_NB_SAMPLES -CC_NB_SAMPLES_old); // This is average current
- 5. DELTA_Q = I_AVG * (Time Time_old); // This delta charge may be accumulated in a different variable
- 6. COULOMB_CNT_old = COULOMB_CNT;
- 7. CC_NB_SAMPLES_old = CC_NB_SAMPLES;
- 8. Time old = Time;
- 9. Read any register different from COULOMB CNT1, COULOMB CNT2 and CC NB SAMPLES
- 10. Jump to step 1

TYPE B (free running mode with implicit reset):

MC33772C

All information provided in this document is subject to legal disclaimers.

© 2024 NXP B.V. All rights reserved.

Battery cell controller IC

CONFIGURATION instructions:

- 1. SYS CFG1[IMEAS EN] = 1; // Enable the current measurement
- 2. ADC2 OFFSET COMP[FREE CNT] = 1; // Select the free running mode
- 3. ADC2_OFFSET_COMP[CC_RST_CFG] = 1; // Reset to zero upon read

RESET instructions:

- 1. ADC_CFG[CC_RST] = 1; // Reset to zero
- 2. Time = Time old = 0; // Variables initialization

NORMAL USE instructions:

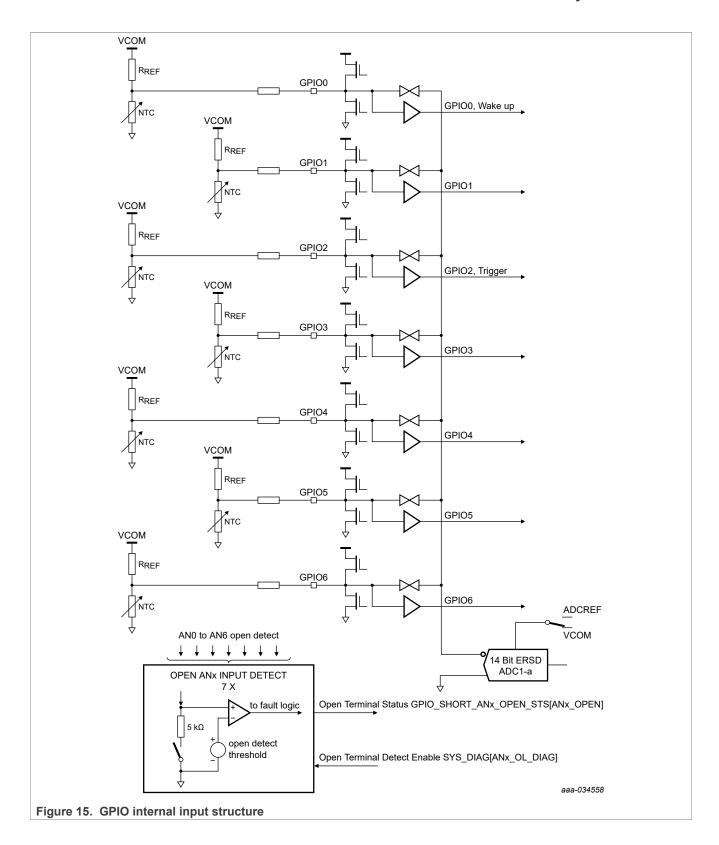
- 1. Time = get abs time(); // Get the absolute time
- 2. Read registers COULOMB CNT1, COULOMB CNT2 and CC NB SAMPLES;
- 3. COULOMB_CNT = (COULOMB_CNT1, COULOMB_CNT2); // Concatenate MSB and LSB
- 4. I_AVG = COULOMB_CNT/CC_NB_SAMPLES; // This is average current
- 5. DELTA Q = I AVG *(Time-Time old); // This delta charge may be accumulated in a different variable
- 6. Time old = Time;
- 7. Read any register different from COULOMB_CNT1, COULOMB_CNT2 and CC_NB_SAMPLES
- 8. Jump to step 1

9.8 GPIOx port control and diagnostics

For user flexibility, the MC33772C has seven GPIO to support voltage measurements referenced to GND - typically coming from NTC based circuits used to extract temperature information, e.g. that of cells - or to drive external circuits. All GPIOs may be individually configured as digital inputs or output ports, wake-up inputs, convert trigger inputs, ratiometric analog inputs with reference to VCOM, or analog inputs with absolute measurements, as shown in Table 16. With the exception of the GPIO0, no external voltage must be applied on GPIOx pins when the device is off or in Sleep mode.

Table 16. GPIO port configurations

	GPIO				ANx		
GPIO port	Standard GPIO	Wup and daisy chain	Convert trigger	Absolute	Ratiometric	(diagnostic mode only)	
0	x	х	_	x	х	_	
1	x	_	_	x	х	_	
2	x	_	x	х	х	_	
3	x	_	_	x	х	_	
4	х	_	_	х	х	_	
5	x	_	_	x	х	x	
6	x	_	_	х	х	x	



9.8.1 GPIOx used as digital I/O

Setting the GPIO_CFG1[GPIOx_CFG] bits to 10 or 11 configures the specific port as an input or output. Pins configured as outputs are driven high or low by writing to the GPIO_CFG2 register. Status of the ports, regardless of the digital configuration, is provided in the GPIO_STS register, which is a feedback of the actually commanded output.

Ports configured as GPIO outputs are diagnosed by the MC33772C. An output state GPIO_STS[GPIOx_ST], which is opposite of the commanded state GPIO_CFG2[GPIOx_DR], is considered to be shorted. Each short fault bit GPIO_SHORT_ANx_OPEN_STS[GPIOx_SH] associated with each GPIOx is OR wired to the FAULT2_STATUS[GPIO_SHORT_FLT] bit. Each GPIO_SHORT_ANx_OPEN_STS[GPIOx_SH] bit when unmasked activates the FAULT pin.

9.8.2 GPIO0 used as wake-up input or fault pin activation input

Setting the GPIO_CFG1[GPIO0_CFG] bits to 10 is used to configure a GPIO0 port as an input. To program GPIO0 as wake-up input, the user must set the GPIO_CFG2[GPIO0_WU] bit to logic 1. In this case, the device performs a wake-up on the rising or falling edge.

By setting the GPIO_CFG2[GPIO0_FLT_ACT] to logic 1, the GPIO0 port may be used to activate the FAULT pin in Normal, Sleep, and Diagnostic modes of operation. This feature allows the user to daisy chain the FAULT pin in high-voltage battery pack applications.

9.8.3 FAULT pin daisy chain operation

The FAULT pin may be programmed to provide the battery management system with a diagnostic feedback. Two behaviors are possible. One is based on logic levels: low level indicates normal condition, high level reveals a faulty condition. The other possibility is based on the heartbeat signal, a periodic signal generated by the IC to indicate normal operation, which provides a higher integrity level. The signal getting stuck to a constant level reveals a faulty condition.

Both modes can be activated in Normal mode, Sleep mode, and Diagnostic mode. The fault pin, carrying the diagnostic signal, is daisy chained to the next lower MC33772C GPIO0 port. Each MC33772C device is programmed to pass the heartbeat through to the neighboring device in the system. In this configuration, any fault that the MC33772C can automatically detect may activate the FAULT line.

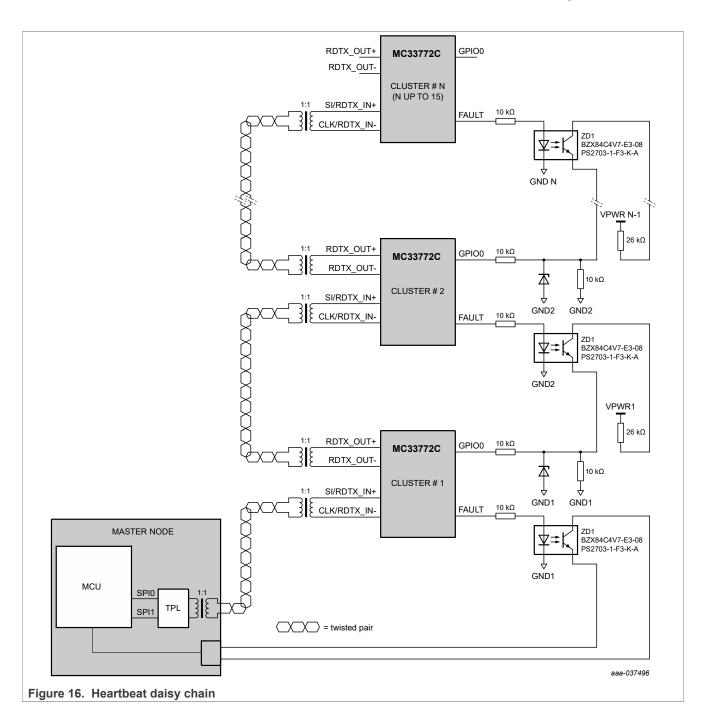
To configure the MC33772C for daisy chain fault output:

- 1. Set GPIO0 as an input GPIO0_CFG = 10.
- 2. Disable wake-up on GPIO0 with GPIO0 WU = 0.
- 3. Set GPIO0 to propagate signal to FAULT pin with GPIO CFG2[GPIO0 FLT ACT] = 1.

To use the MC33772C heartbeat feature, the user must write a 1 in the SYS_CFG1[FAULT_WAVE] bit. The signaling square wave has constant on time, whereas the desired off time may be selected by writing a proper value in the SYS_CFG1[WAVE_DC_BITx] configuration field.

The usage of the fault pin is essential if the IC uses SPI communication and must provide some monitoring functionality in Sleep mode. In such use case the fault line is the only means to alert the system controller about an occurred fault, while in TPL mode, even if the IC is sleeping, it has the chance to send a wake-up signal through the bus. The fault line usage is optional in Normal and Diagnostic modes, as well as in Sleep mode and TPL configuration.

Battery cell controller IC



9.8.4 GPIO2 used as ADC trigger

The MC33772C provides a convenient method to trigger an ADC conversion from an external digital source. To use GPIO2 as an ADC trigger, configure the port as a digital input through the setting GPIO_CFG1[GPIO2_CFG] = 10 and enable the trigger through the setting GPIO_CFG2[GPIO2_SOC] = 1. With the port configured, positive edge events on GPIO_CFG2[GPIO2_SOC] triggers a start of conversion sequence.

With a GPIO2 trigger, the converter operates as programmed in the ADC_CFG[SOC] bit. The GPIO2 convert trigger feature is not available in Sleep mode.

9.8.5 GPIOx used as analog

Setting the GPIO_CFG1[GPIOx_CFG] bits to 00 or 01 configures the specific port as an analog ratiometric input (for conversion with ADC1-A using VCOM as reference voltage) or single ended input (for absolute measurement, which means using ADC1-A with its internal voltage reference in place of VCOM). GPIOs configured as analog inputs are usually used for temperature measurement. The MC33772C may be programmed to detect overtemperature and undertemperature.

To detect overtemperature and undertemperature, the generated digital value is compared to an individually programmed threshold in the TH_ANx_OT and TH_ANx_UT registers. ADC1-A results on any temperature measurement input that exceed the threshold activate the FAULT1_STATUS[AN_OT_FLT,AN_UT_FLT] bit. The conversion results for the analog inputs are available in MEAS_ANx register for the pack controller to read. GPIOs configured as single ended analog inputs can also be used to monitor voltage through external voltage divider.

9.8.6 GPIO5, GPIO6 used as ISENSE

To use GPIO5 and GPIO6 as inputs to the current sense PGA, the MC33772C must be in Diagnostic mode. As a secondary method of measuring current for functional verification, the user may connect input ports 5 and 6 as inputs to the positive and negative inputs of the PGA by setting the SYS_DIAG[I_MUX] bits to 01. This way, GPIO5 plays the role of ISENSE+ and GPIO6 plays the role of ISENSE-.

Customers using GPIO5 and GPIO6 as a secondary current measurement in diagnostic mode must command GPIO5 and GPIO6 to digital inputs by setting GPIO_CFG1[GPIO5_CFG] = 10 and GPIO_CFG1[GPIO6_CFG] = 10.

9.9 Cell balance control

The MC33772C features fully protected integrated cell balancing drivers with fault diagnostics. The cell balancing feature is active in Normal, Sleep and Diagnostic modes. The MC33772C contains registers to control and monitor cell balance drivers and cell balance fault status.

The SYS_CFG1 register contains the CB_DRVEN bit. The CB_DRVEN bit must be enabled for any of the drivers to be activated. All drivers are disabled when CB_DRVEN bit is logic 0. For cell balance drivers to be active, both the SYS_CFG1[CB_DRVEN] and the CBx_CFG[CB_EN] bits must be set to logic 1.

The individual cell balance timer is set through the CBx_CFG[CB_TIMER]. Timing parameters can be found in the register map of this specification. Each time the cell balance CBx_CFG[CB_TIMER] bit is written by the MCU controller, the MC33772C initiates the cell balance timer. It is important to explicitly mention, each time the CB_DRVEN bit is set to logic 0, then cell balancing timers get reset to 0 (the CBx_CFG[CB_TIMER] bits are unchanged) and all cell balancing MOSFETs are turned off. Before the CB_DRVEN bit is set again to logic 1, all CBx_CFG registers need to be configured again. Otherwise, a cell balancing sequence will be started with the previous settings.

The SYS_CFG1 register contains the CB_MANUAL_PAUSE bit, which, if set to logic 1, instructs the MC33772C to disable the cell balance switches. When the CB_MANUAL_PAUSE bit is set again to logic 0, the cell balance switches are restored according to the programming. However, the cell balance timers are not frozen during a manual pause. The contents of CBx_CFG[CB_TIMER] and ADC2_OFFSET_COMP[ALLCBOFF_ON_SHORT] bits must not be changed while balancing.

9.10 Internal IC temperature

Internal temperature measurement is completed automatically during each ADC conversion sequence. The MEAS_IC_TEMP register containing the IC temperature measurement may be read at any time by the pack controller. Resolution of MEAS_IC_TEMP is 32 mK/LSB.

MC33772C

Battery cell controller IC

9.11 Internal temperature fault

In addition to the digital temperature measurement register, the MC33772C is equipped with a silicon overtemperature Thermal ShutDown (TSD). In the event the silicon thermal shutdown is activated in Normal mode, the MC33772C halts all monitoring operations and enters a low-power state with the FAULT pin activated. When the die temperature returns to normal, the MC33772C resumes operation in Init mode.

In the event of an internal TSD:

- 1. Conversion sequence is aborted and the MC33772C stops converting
- 2. The FAULT2_STATUS[IC_TSD_FLT] bit is set to logic 1, implying a FAULT pin activation.
- 3. VCOM, VANA and VPRE are in shut down, communication gets blocked
- 4. All cell balance switches are disabled, all IC information except the FAULT2_STATUS[IC_TSD_FLT] bit is cleared and CB_DRVEN is cleared

Overtemperature TSD events are also detected while the MC33772C is in Sleep mode during cyclic measurements. TSD events detected during the Sleep mode cyclic measurement force the MC33772C to set the IC_TSD_FLT bit and activate the FAULT pin while remaining in Sleep mode.

When the die temperature returns to a normal level, as the IC returns in Init mode, the user shall provide the device with an address and proper parameters again.

9.12 Storage of parameters in an optional EEPROM

NXP provides parts with optimal calibration values, stored in a Read Only Memory called *fuses cell array*. It is typically neither necessary nor advised to change the standard values. Nevertheless, sometimes this might be required. An example is adjusting the gain calibration of the current channel to take into account the behavior of the external shunt resistor, due to the temperature coefficient and individual resistance deviation from the nominal value.

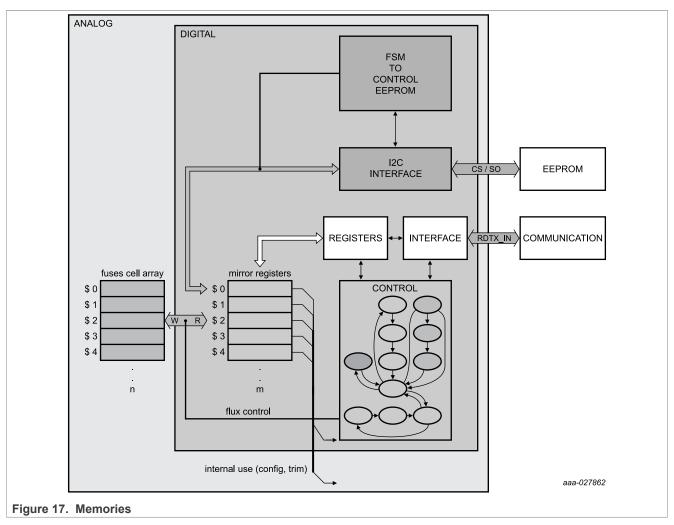
New calibration values may be determined in Normal mode and then stored:

- either in an external EEPROM (keeping content in case of power-down or reset event)
- or in the internal R/W memory, which is referred to as *mirror memory*. In this case, they are active until next power-down or reset event

Each time the part experiences a power-up or reset event, an initialization process (transparent to the user) takes place like hereafter:

- the mirror memory is first uploaded with the value of the fuses cell array
- if an EEPROM is recognized, this mirror memory gets automatically reloaded with the content of the EEPROM (overwriting the previous values). Else, the mirror memory is not modified
- the content of the mirror memory is released and propagated to the applicative part of the chip, protected by an ECC (Error Correction Code)

Battery cell controller IC



Because the EEPROM content is expected to overwrite the mirror memory, the space of EEPROM-addresses and the space of mirror-addresses correlate to each other. Mirror data are organized in 16-bit words, while the data of the EEPROM have been thought as bytes. As at EEPROM-address \$00 there is the key value, the first calibration byte of the EEPROM must have EEPROM-address \$01 and corresponds to the most significant byte of the mirror word having mirror-address \$00. The second calibration byte of the EEPROM must have EEPROM-address \$02 and corresponds to the least significant byte of the mirror word still having mirror-address \$00, and so on.

9.12.1 Error Correction Code (ECC)

The calibration values are protected with some ECC bits, which are programmed in the *fuses cell array*. Like the calibration values, these ECC bits are loaded the same way in the mirror memory during the initialization process, to be used as a protection of the calibration data.

In case of a single error, the problem is automatically corrected, and the user is warned by the bit FUSE_MIRROR_CNTL[SEC_ERR_FLT]. In case of a double error, the problem can only be detected, and the fault flag FAULT2_STATUS[DED_ERR_FLT] is set.

If the user customizes its own calibration data, some new ECC bits must be evaluated. There are two ways for the user to evaluate by its own the new ECC bits.

Battery cell controller IC

- There is a special calculation sheet the customer has to request from NXP. This sheet contains the correct values for DED_ENCODE2 and DED_ENCODE1 information, that is, ECC words used in the MC33772C to detect a single error in the data and to correct it
- 2. Writing the SYS_CFG2[HAMM_ENCOD] bit to logic 1, in which case the DED Hamming decoders generate the redundancy bits in DED_ENCODE1 and DED_ENCODE2 registers. See <u>Table 84</u> and <u>Table 85</u>. However, in the normal usage, the SYS_CFG2[HAMM_ENCOD] bit has to be set at logic 0. For safety reasons, it is recommended the value of such bit is periodically checked to be at logic 0. If the bit is not at logic 0, then it must be written at logic 0 again

Once evaluated, these new ECC bits must be stored in the appropriate location:

- In the mirror memory if the customization is done there
- In the EEPROM, if the new calibration is stored there (will be downloaded at next power-up)
- In both cases, at address \$0E and \$0F (or EEPROM equivalent) of the fuse bank. See Table 89

9.12.2 Mirror memory

As described previously, the mirror memory can be accessed, partially in Read/Write mode, totally in Read-Only mode. This, by using the FUSE_MIRROR_DATA and FUSE_MIRROR_CNTL general registers (see <u>Table 86</u> and <u>Table 87</u>).

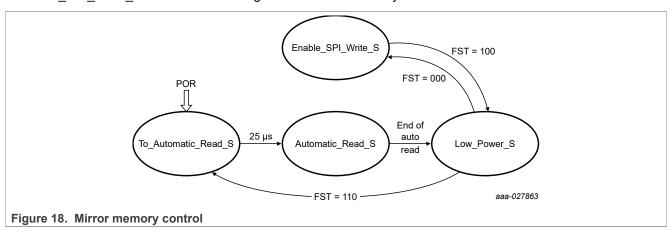
The former contains the value of the data to be written into the mirror memory or to be read from it (FMR_DATA). The latter contains the address to access (FMR_ADDR) and some control fields (FSTM and FST).

Note: FUSE_MIRROR_CNTL[FM_ADDR] enables to access addresses from \$00 to \$0F in Read/Write mode and addresses from \$10 to \$12 in Read-Only mode. See <u>Table</u> 89.

To manage the mirror memory, the FSM of Figure 18 must be used.

Meaning of the states:

- To_Automatic_Read_S: transient state for slightly delaying the automatic read, after POR
- Automatic_Read_S: in this state the entire bank of fuses is automatically transferred from fuses cell array to the mirror memory
- Low_Power_S: low power state; it must be the initial and final state of a sequence of write operations. This is the state where the mechanism idles after an automatic read
- Enable SPI Write S: state allows writing into the mirror memory



The read sequence may be useful, for example when the user wants to read the traceability information (serial number) contained in some specific words of the mirror memory. See <u>Table 89</u>.

MC33772C

Battery cell controller IC

Table 17. Sequence of read operations

Type of command	FSTM	FST	FMR_ADDR	FUSE_MIRROR_DATA				
FUSE_MIRROR_CNTL[FMR_ADDR] set	0	000	00000	X				
FUSE_MIRROR_DATA	Х	Х	Х	data read at addr \$0				
FUSE_MIRROR_CNTL[FMR_ADDR] set	0	000	00001	X				
FUSE_MIRROR_DATA	Х	Х	Х	data read at addr \$1				
FUSE_MIRROR_CNTL[FMR_ADDR] set	0	000	00010	X				
FUSE_MIRROR_DATA read	Х	Х	X	data read at addr \$2				

Table 18. Sequence of write operations

Type of command	FSTM	FST	FMR_ADDR	FUSE_MIRROR_DATA
FUSE_MIRROR_CNTL to enable writing	1	000	00000	X
FUSE_MIRROR_CNTL[FMR_ADDR] at \$0	1	000	00000	X
FUSE_MIRROR_DATA	Х	Х	Х	Data to be written at addr \$0
FUSE_MIRROR_CNTL[FMR_ADDR] at \$1	1	000	00001	X
FUSE_MIRROR_DATA	Х	Х	X	Data to be written at addr \$1
FUSE_MIRROR_CNTL[FMR_ADDR] at \$2	1	000	00010	Х
FUSE_MIRROR_DATA	Х	Х	Х	Data to be written at addr \$2
FUSE_MIRROR_CNTL to low power	1	100	X	X

9.12.3 Optional EEPROM

Through the I2C interface, it is possible to link the MC33772C to an EEPROM, typically to store a customized configuration of calibration (user's final test and assembly). However, nothing prevents to use it as a generic information storage. But in all cases, the first portion of the EEPROM has to be reserved to the copy of all gains, even if this is identical to the content of the fuse cell array.

If connected, the EEPROM is automatically recognized, provided the address \$00 of the EEPROM contains the proper one-byte key value, namely \$CB hex.

Like for the mirror memory, the EEPROM is accessible following an indirect addressing, through the EEPROM_CTRL register. To program the EEPROM, the address and the data must be provided respectively in EEPROM_CTRL[EEPROM_ADD] and EEPROM_CTRL[DATA_TO_WRITE] fields, with the EEPROM_CTRL[RW] bit set to logic 0. The user must simply send the write command with the EEPROM address and data to be written, and set the write bit to logic 0. The MC33772C automatically writes the data to the given EEPROM address. To read data from the EEPROM, the user has to first write to the EEPROM_CTRL register, providing the address in EEPROM_CTRL[EEPROM_ADD] field, with the EEPROM_CTRL[RW] bit set to logic 1, then read in the same register to get the data in EEPROM_CTRL[READ_DATA] field.

10 Communication

The MC33772C is designed to support Serial Peripheral Interface (SPI) or Transformer Physical Layer (TPL) communication.

SPI communication uses the standard CSB to select the MC33772C and clocks data in and out using SCLK, SI, and SO. Using SPI to communicate to the MC33772C provides system isolation when used in conjunction with galvanic isolators. Serial communication is enabled using the SPI_COM_EN pin. To select SPI communication, the SPI_COM_EN pin must be terminated to the VCOM supply. Terminating the SPI_COM_EN pin to CGND pin

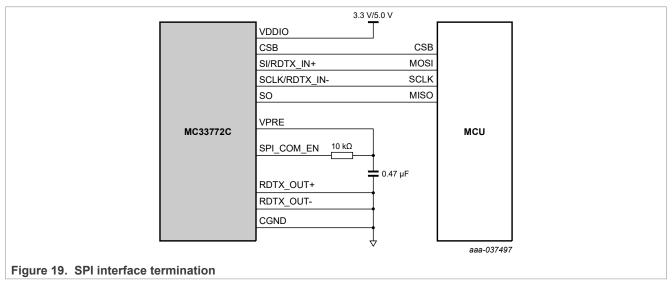
Battery cell controller IC

selects TPL communication. Systems using only SPI communication to the MC33772C may leave RDTX_OUT+ and RDTX_OUT- unterminated or may short them to ground.

During initialization, each MC33772C device is assigned a specific address by the MCU by writing a non-zero value to INIT[CID] bit field. Only the MC33772C with the correct address acts upon and responds to the request from MCU. After initialization, the MCU may communicate globally to all slave devices by using a global command. No response is generated when a global command is received by each slave device in the chain.

Note: The MC33772C supports only one communication method at a time and is determined by the state of SPI_COM_EN pin. Changing the state of the SPI_COM_EN pin after POR and VCOM is in regulation is considered a communication fault, and sets the COM_LOSS_FLT bit. The MC33772C remains in same configuration determined at POR.

10.1 SPI communication



Note: Supply input VDDIO accepts 3.3 V or 5.0 V to manage SPI and I2C interfaces.

The MC33772C SPI interface is a standard SPI interface with a chip select (CSB), clock (SCLK), master in slave out (MISO), and master out slave in (MOSI). The SI/SO shifting of the data follows a first-in-first-out method, with both input and output words transferring the most significant bit (MSB) first. All SPI communication to the MC33772C is controlled by the microcontroller.

One 48-bit message frame for previously requested data is retrieved through serial out for each current serial in message sent by the MCU. For message integrity and communication robustness, each SPI transmit message consists of nine bit fields with a total of 48 bits message frame. The nine transmit fields are defined as following:

- 1. Register data (16 bits)
- 2. Request/Response (1 bit), always at 1 in the response
- 3. Register address (7 bits)
- 4. Reserved (2 bits)
- 5. Cluster ID (6 bits)
- 6. Message counter (4 bits)
- 7. Reserved (2 bits)
- 8. Command (2 bits)
- 9. Cyclic redundancy check (8 bits)

MC33772C

Battery cell controller IC

Messages having less or more than 48 bits, incorrect CRC, or incorrect SCLK phase are disregarded. Communication faults set the COM_ERR_FLT fault bit in the FAULT1_STATUS register and increments the COM_STATUS[COM_ERR_COUNT] register.

Note: It is required that the SCLK input is low before the falling edge of CSB (SCLK phase).

Table 19. SPI command format

Register data	Request/ Response		Reserved	Device address (Cluster ID)	Message counter	Reserved	Command	CRC
Bit[47:32]	Bit[31]	Bit[30:24]	Bit[23:22]	Bit[21:16]	Bit[15:12]	Bit[11:10]	Bit[9:8]	Bit[7:0]

Information is transferred to and from the MC33772C through the read and write commands. After a power-up (POR) or RESET (pin) or SYS_CFG1[SOFT_RST], the MC33772C device only responds to the cluster ID of 00 0000b. The user must change the cluster ID of the device by writing a new cluster ID into register INIT[CID]. Subsequent read/write command must use the new cluster ID to communicate to the device. Whatever the type of transmitted message, the master has to write a logic 0 in the Request/Response bit. Any message transmitted by the user with Request/Response bit set to 1 or with wrong CID is treated as Invalid request by MC33772C.

Notes:

- In SPI communication, global write commands are not allowed and the MC33772C responds with all bit field set to zero except message counter and correct CRC, in the subsequent message frame
- In SPI communication, the MC33772C responds with all bit filed set to zero except message counter and correct CRC to an invalid request from MCU
- In SPI communication, the MC33772C responds with all bit filed set to zero except message counter and the correct CRC to the very first MC33772C / MCU message frame

The response message sent by MC33772C to MCU is similar to the receive message and includes the 4-bit message counter. The Message counter is a local counter to MC33772C. It is increased by one for each new response transmitted by MC33772C, this applies also to auto read generated by MC33772C for write and NOP commands. It is recommended that the MCU compares the message counter value of two consecutive responses transmitted by MC33772C, if the values are same then MCU shall treat the messages as error.

- 1. Register data (16 bits)
- 2. Request/Response (1 bit)
- 3. Register address (7 bits)
- 4. Reserved (2 bits)
- 5. Cluster ID (6 bits)
- 6. Message counter (4 bits)
- 7. Reserved (2 bits)
- 8. Command (2 bits)
- 9. Cyclic redundancy check (8 bit)

Table 20. SPI response format

Register data	Request/ Response		Reserved	Device address (Cluster ID)	Message counter	Reserved	Command	CRC
Bit[47:32]	Bit[31]	Bit[30:24]	Bit[23:22]	Bit[21:16]	Bit[15:12]	Bit[11:10]	Bit[9:8]	Bit[7:0]

To initiate communication, the MCU transitions CSB from high to low. The data from the MCU is sent with the most significant bit first. The SI data is latched by the device on the falling edge of SCLK. Data on SO is changed on the rising edge of SCLK and read by MCU on the falling edge of SCLK. The SO response message is dependent on the previous command.

MC33772C

Falling edge of CSB initiates the following:

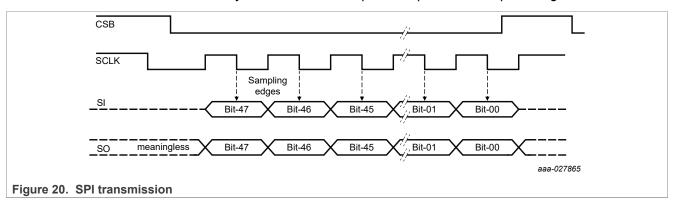
- 1. Enables the SI Input
- 2. Enables the SO output driver

Rising edge of CSB initiates the following operation:

- 1. Disables the SO driver (high-impedance)
- 2. Activates the received 48-bit command word allowing the MC33772C to act upon the new command

Notes:

- The MC33772C responds to a NO_OPERATION command with a NO_OPERATION response (with increased message counter value) in the subsequent response
- After initialization, when writing to a register, the MC33772C responds with an auto read of the register which was written in the subsequent write request
- The MC33772C does not execute any command if the Request/Response bit is equal to logic 1



10.2 TPL communication

High speed differential isolated communication is achieved through the use of transformer or capacitive isolation. Terminating the SPI_COM_EN pin to the CGND pin selects transformer communication. For transformer communication (TPL), an MC33664 IC is required between the MC33772C IC and the MCU, as shown in Figure 48

For TPL communication, it is recommended that the device is terminated as shown in <u>Figure 48</u>. Component values are given in <u>Section 13.2 "MC33772C External Components"</u>.

The MC33772C IC is equipped with a bi-directional transceivers for upstream and downstream communication. The bi-directional transceiver is implemented to support up to 63 nodes in one daisy chain (CID = 00 0000b is reserved for network initialization). The message received by the receiver on one port of MC33772C is retransmitted by the transmitter of the opposite port of MC33772C. This ensures that the message is not attenuated as it propagates through the daisy chain. Each node in the daisy chain adds a delay of tport_delay for forwarding messages in the daisy chain.

In TPL communication, the CSB pin may be used as a wake-up input. During Sleep mode, an edge transition of the CSB initiates the wake-up function. Alternatively, the CSB pin may be shorted to ground or software masked to prevent undesired wake-up events.

Communication between the pack controller and the MC33772C is half duplex communication with transformer isolation. Transformer physical layer in the pack controller creates a pulse phase modulated signal transmitted to the bus through the transformer. The MC33772C physical layer is equipped with a segment-based transmitter, which is used as a terminating resistor (internally) during the receive mode. The default value of terminating resistance is set to 120 Ω for impedance matching and network stability. In TPL communication, the MC33772C IC is always electrically connected to its neighbouring MC33772C ICs in a daisy chain. However, by

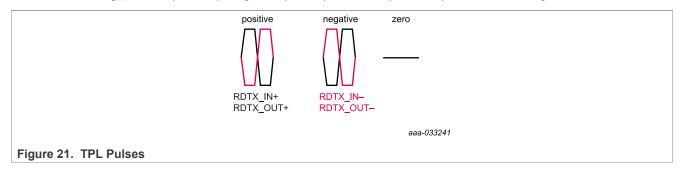
MC337720

Battery cell controller IC

using INIT[BUS_FW] the neighboring MC33772C can be disconnected digitally. This can be configured using INIT register.

10.2.1 TPL Encoding

The transformer physical layer (TPL) uses pulse encoded symbols for communication. The three signal pulses used for encoding positive (P,black), negative (N, red) and zero (M, black) are shown in <u>Figure 21</u>.



Start Of Message (SOM) and End Of Message (EOM) symbols are generated by the transformer driver and always occur at the start and end of the communication message. The SOM symbol and EOM symbol each contain two complete signal pulses. The SOM symbol produces a double pulse with a logic 1 phase. EOM produces a double pulse with logic 0 phase. Data pulses are single period pulse waves that indicate logic 1 or 0, based on the phase. The four symbols shown in <u>Table 21</u> are used.

Table 21. TPL encoding

Symbols	Pulse modulation	Description
Start Of Message (SOM)	Start of message Two pulse positive square waves	Positive phase, double pulse (and plus pause)
End Of Message (EOM)	Figure 22. SOM End of message aaa-032624	Negative phase, double pulse
	Figure 23. EOM	

Battery cell controller IC

Table 21. TPL encoding ...continued

Symbols	Pulse modulation	Description
Logic 1	Bit n Logic 1	Positive phase, single pulse (and plus pause)
Logic 0	Bit n Logic 0	Negative phase, single pulse (and plus pause)
	Figure 25. Logic 0	

10.2.2 Command message bit order

Same as in Section 10.1 "SPI communication".

10.2.3 Response message bit order

Same as in Section 10.1 "SPI communication".

10.2.4 Transformer communication format

Command and response frames are exchanged primarily between a single master and any single slave. One exception is the use of a global command, which can be transmitted from one master to multiple slaves, but includes no slave response. The purpose of the command and response transactions are to read and write to registers within the slave register map.

The command and response communication structure provides all context information required for unambiguous single-exchange transactions for extended memory applications requiring safety critical and efficient memory access.

The message structures have predefined fixed bit length frames and defined timing between transfers. To transfer data efficiently from the slave, multiple response packets may be requested by the read command. The MC33772C defines a set of fields that constitute the command and response message structure.

Transformer message format is identical to the SPI format. Command message frames consist of nine fields containing exactly 48 bits. The response structure is similar to the SPI format.

After initialization, information is transferred to and from the MC33772C through the read and write commands. On Power Up or POR, the first MC33772C device in the chain responds to address 00 0000b^{4 5}. The user must program the first device with a new address by writing to the INIT[CID] register. Programming the device

⁴ A slave device at POR with INIT[CID] = 00 0000b responds only at the port it received the request.

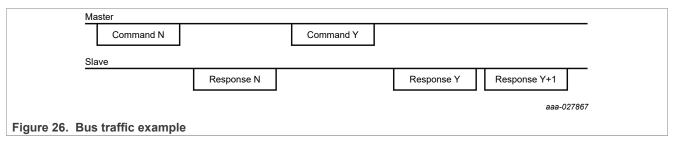
⁵ A slave device with CID = 00 0000b does not forward messages.

Battery cell controller IC

with a new address allows the pack controller to communicate and initialize the next device in the daisy chain. Subsequent read/write commands to the next device must use the new address to communicate.

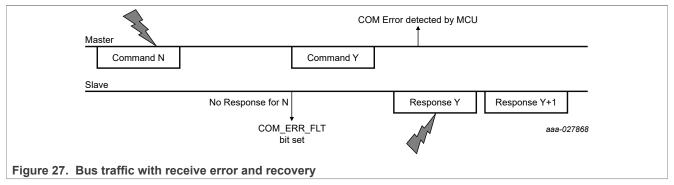
All write commands sent by the master must consist of a single frame. The slave device does not generate any response to a write command from master but only acts on it. Similarly, the slave device does not generate any response nor performs any operation after receiving a valid NOP message from the master.

Read commands sent by the master may generate a single response or multiple responses depending on the parameters set in the read request. The packet size and memory start location are identified in the read command sent by the master.



No response is generated by a slave MC33772C when a corrupted message is received. Confirmation that a global write command is received by the slave must be done by reading the register in which it was written.

In cases where a bus error occurs, due to induced noise or a bus fault, the slave detects bad data transfers. The MC33772C slave reacts to communication faults by setting the FAULT1_STATUS[COM_ERR_FLT] and incrementing the COM_STATUS[COM_ERR_COUNT] register.

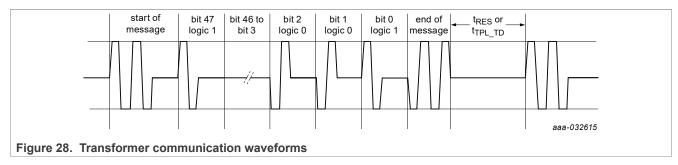


All valid read commands sent to an individual slave provide a response. In the event a slave does not respond to a read request message, the master must assume the message was corrupted or lost. To recover from the event, the master must retransmit the message. Corrupted messages received by the master are detected through an incorrect CRC code. To recover, the master must request the data again.

10.2.5 Transformer communication timing

Command and response message frames are to be sent and received at 2.0 Mbit/s bit rate. The response to a first read request command is provided within t_{RES} of the end of the frame. However, two consecutive message responses transmitted by MC33772C IC for burst read request are separated by t_{TPL_TD} time as shown in Figure 28.

Battery cell controller IC



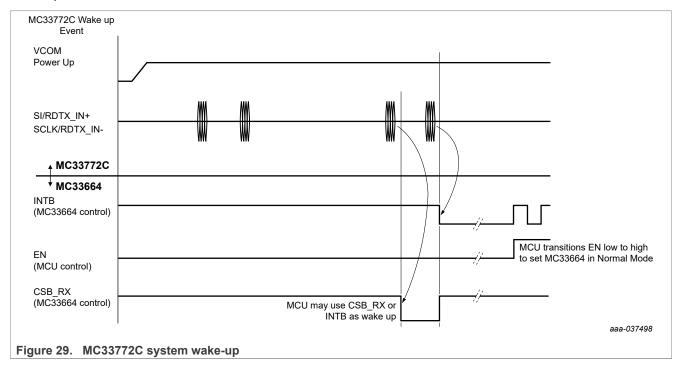
Each sent and received message starts with Start Of Message (SOM) bit followed by a 48-bit message and ends with an End Of Message (EOM) bit.

10.2.6 Transformer communication wake-up

In TPL communication, the system wake-up can be triggered by either the MC33772C IC (wake-up due to internal event) or the pack controller (MCU). In both cases, a dedicated wake-up pulse sequence is used. The wake-up pulse sequence consists of two transmit messages of any length. The messages are separated by a delay time ($t_{WAKE\ DELAY}$). Each message contains a SOM and EOM symbol.

10.2.6.1 MC33772C System wake-up

By default, the internal event wake-up capability of the MC33772C is disabled. When enabled and in the event the MC33772C detects a wake-up condition, the device initiates a wake-up pulse sequence on the bus to alert the pack controller. The MC33772C IC initiating the wake-up, due to an internal event, sends the wake-up sequence upstream and downstream in the daisy chain to ensure the wake-up message propagates along the entire chain to the pack controller. Each neighbouring MC33772C IC in daisy chain forwards the received wake-up sequence opposite to the direction where it received the wake-up sequence. In this process, all MC33772C devices in the daisy chain, along with the pack controller, are awoken. After the pack controller gets awoken; it is recommended the pack controller interrogate each MC33772C in the system to determine the source of the wake-up.

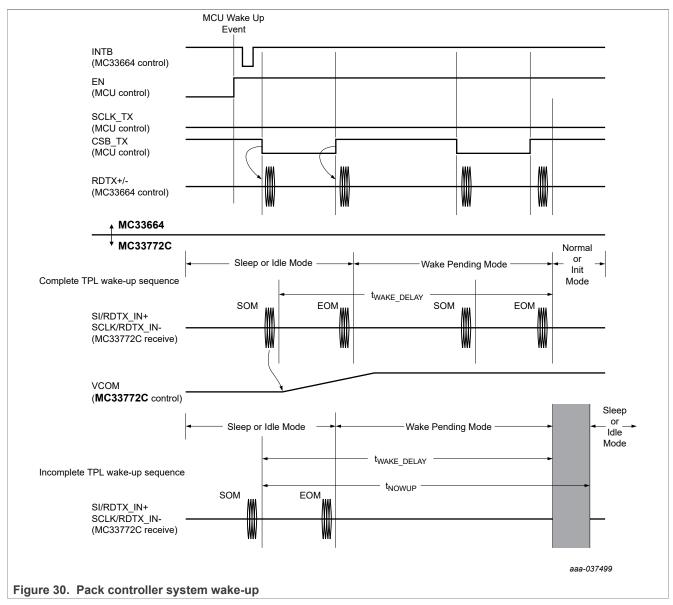


MC33772C

Note: The system wake-up performed by MC33772C IC in case of any internal event is disabled by default. This wake-up can be activated by writing to register WAKEUP_MASK1, WAKEUP_MASK2 and WAKEUP_MASK3.

10.2.6.2 Pack controller system wake-up

The pack controller can also perform system wake-up by sending a wake-up sequence to the first MC33772C IC. The pack controller can use the CSB_TX pin of the MC33664 to generate SOM and EOM with correct timing.



If the device is in Sleep mode, each successive slave device awoken by the wake-up message on the bus, generates a new wake-up message for its neighbor. The message is to be transmitted in one direction only on the bus. The direction of transmission of the wake-up message on the bus is always at the opposite port of the received wake-up message. In the unlikely event of a collision, the message at the lower port (RDTX_IN) is given a higher priority than the message at the higher port (RDTX_OUT).

Note:

- Any write message of any length can be used to generate both wake-up pulses and obtain a valid device wake-up
- The second wake-up message should be sent after a minimum time of tWAKE_DELAY(min) from the first SOM reception
- The device falls back to Sleep or Idle mode when an SOM followed by EOM is not received in tWAKE_DELAY(max)
- If the wake-up sequence is incomplete, then a new wake-up attempt can only be done after a tNOWUP delay (see <u>Figure 30</u>)
- The pack controller must wait for t_{WU_Wait} ms per node to communicate with the MC33772C ICs after sending the first wake-up message. For example, given that the MC33772C IC is enumerated and bus forwarding is enabled, with 10 nodes in a daisy chain the pack controller must wait 7.5 ms before communicating to MC33772C IC. The waiting time allows all the MC33772C ICs in the system to transition to Normal mode
- The pack controller must use only one master node to perform wake-up of devices

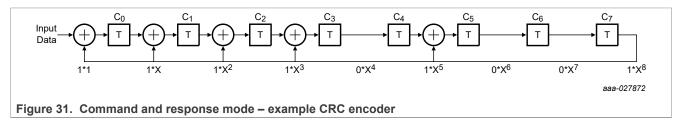
10.3 CRC generation

The master and slaves calculate a CRC on the entire message using the processes detailed in this section.

The command and response CRC is fixed at 8 bits in length. The CRC is calculated using the polynomial $x^8 + x^5 + x^3 + x^2 + x + 1$ (identified by 97h – Koopman notation). To get the CRC engine into the correct state, a 11h must be clocked in before the message. This procedure corresponds to a seed value of 42h.

An example CRC encoding HW implementation is shown in Figure 31.

Note: 97h in Koopman notation corresponds to 2Fh in the MSB-first code notification.



The effect of the CRC encoding procedure is shown in the following table. The seed value is appended into the most significant bits of the shift register.

Table 22. Data preparation for CRC encoding

Seed			Register address	Reserved		Message counter	Reserved	Cmd
1111_1111	Bits [47:32]	Bit [31]	Bits [30:24]	Bits[23:22]	Bits[21:16]	Bits[15:12]	Bits[11:10]	Bits[9:8]

Seed	padded with the message to encode	padded
		with 8 zeros

- 1. Using a serial CRC calculation method, the transmitter rotates the seed and data into the least significant bits of the shift register
- 2. During the serial CRC calculation, the seed and the data bits are XOR compared with the polynomial data bits. When the MSB is logic 1, the comparison result is loaded in the register, otherwise the data bits are simply shifted. It must be noted the 48-bit message to be processed must have the bits corresponding to the CRC byte all equal to zero (00000000)
- 3. Once the CRC is calculated, it replaces the CRC byte initially set to all zeros and is transmitted

Following is the procedure for the CRC decoding:

MC33772C

Battery cell controller IC

- 1. The seed value is loaded into the most significant bits of the receive register
- 2. Using a serial CRC calculation method, the receiver rotates the received message and CRC into the least significant bits of the shift register in the order received (MSB first)
- 3. When the calculation on the last bit of the CRC is rotated into the shift register, the shift register contains the CRC check result:
 - · If the shift register contains all zeros, the CRC is correct
 - If the shift register contains a value other than zero, the CRC is incorrect

CRC calculation examples:

Table 23. Command CRC calculation examples

Data 16 bit (Hex)	Request/Response bit and memory address, 8 bit (Hex)	Reserved (2 bits) and Cluster Id (6 bit), 8 bit (Hex)	Message counter, 4 bit (Hex)	Reserved (2 bits) and Command (2 bits), 4 bit (Hex)	CRC 8 bit (Hex)	Frame 48 bit (Hex)
0x0101	0x08	0x01	0x3	0x0	0x3C	0x01010801303C
0x0A0A	0x01	0x0A	0x9	0x1	0x84	0x0A0A010A9184
0x01C4	0x0F	0x02	0x1	0x2	0x26	0x01C40F021226
0x7257	0x01	0x05	0x7	0x3	0xC7	0x7257010573C7

Table 24. Response CRC calculation examples

Data 16 bit (Hex)	Request/Response bit and memory address, 8 bit (Hex)	Reserved (2 bits) and Cluster Id (6 bit), 8 bit (Hex)	Message counter 4 bit (Hex)	Reserved (2 bits) and Command (2 bits), 4 bit (Hex)	CRC 8 bit (Hex)	Frame 48 bit (Hex)
0x1101	0x89	0x01	0x3	0x0	0x26	0x110189013026
0x2002	0x89	0x05	0x9	0x0	0x7A	0x20028905907A
0x5103	0x89	0x0A	0x1	0x5	0x07	0x5103890A1507
0xFF04	0x89	0x06	0x7	0x2	0xA6	0xFF04890672A6

10.4 Commands

10.4.1 Read command and response

Read command is intended to be used for SPI and transformer interface. The read command is a local command used for retrieving data from the MC33772C device. The data field contains the number of data registers to be returned. Requesting data from registers greater than address \$7F forces the device to loop the register counter back to register \$00.

Battery cell controller IC

Table 25. Read command table

Table 25. Nead Command table												
Command name	Register data		Request/ Response	Register address	Reserved	Device address (Cluster ID)	_	Reserved	Command	CRC		
	Bit[47:32]		Bit[31]	Bit[30:24]	Bit[23:22]	Bit[21:16]	Bit[15:12]	Bit[11:10]	Bit[9:8]	Bit[7:0]		
Read command	XXXX XXXX X	NRT- 01 to 7F	0b	Register address	xxb	CID	xxxxb	xxb	01b	CRC		

Table 26. Read response table

Command name	Register data	Request/ Response	Register address	Reserved	Device address (Cluster ID)	Message counter	Reserved	Command	CRC
	Bit[47:32]	Bit[31]	Bit[30:24]	Bit[23:22]	Bit[21:16]	Bit[15:12]	Bit[11:10]	Bit[9:8]	Bit[7:0]
Read MsgCntr Response	Register Data	1b	Register address	00b	CID	MsgCntr	00b	01b	CRC

Table 27. Legend for read command, read response tables

Read com	mand	Read resp	onse
Bit[7:0]	= 8-bit CRC	Bit[7:0]	= 8-bit CRC
Bit[9:8]	= Command (01b)	Bit[9:8]	= Command field (01b)
Bit[11:10]	= Reserved (xxb)	Bit[11:10]	= Reserved (00b)
Bit[15:12]	= Message counter	Bit[15:12]	= Message counter
Bit[21:16]	= Device address (Cluster ID)	Bit[21:16]	= Device address (Cluster ID)
Bit[23:22]	= Reserved = X, don't care	Bit[23:22]	= Reserved (00b)
Bit[30:24]	= Register address	Bit[30:24]	= Register address
Bit[31]	= Request/Response = 0b (Request)	Bit[31]	= Request/Response = 1b (Response)
Bit[39:32]	= NRT, number of registers to transfer back. Max is \$7F, loop back on address \$00	Bit[47:32]	= Data at memory address
Bit[47:40]	= X, don't care		

Notes:

- The read command is a local command
- Requesting a read of a reserved register provides a \$0000 data response
- · Registers are read-only on devices that have not been initialized
- Requesting a number of NRT equal to 00 is the same as requesting 01
- The MsgCntr is a local counter of MC33772C IC. It is only increased by the node responding to MCU request. The node increases the value of MsgCntr by 1 with each new response transmitted by MC33772C. On saturation of this counter it restarts from 0000b
- The initial value of message counter is 0000b and first response transmitted by MC33772C has the message counter value set to 0000b

MC337720

62 / 128

Battery cell controller IC

10.4.2 Local write command

Unlike the read command, for which MC33772C responds with data, the write command does not generate any response. When the slave receives a valid local write command, the message is acted upon but no response is generated. Writing to read only registers does not allow the register content to be updated.

Table 28. Write command table

Command name	Register data	Request/ Response	Register address	Reserved	Device address (Cluster ID)	Message counter	Reserved	Command	CRC
	Bit[47:32]	Bit[31]	Bit[30:24]	Bit[23:22]	Bit[21:16]	Bit[15:12]	Bit[11:10]	Bit[9:8]	Bit[7:0]
Write command	Register Data	0b	Register address	xxb	CID	xxxxb	xxb	10b	CRC

Table 29. Legend for write command and write response tables

Write command	
Bit[7:0]	= 8-bit CRC
Bit[9:8]	= Command (10b)
Bit[11:10]	= Reserved (xxb)
Bit[15:12]	= Message counter (xxxxb)
Bit[21:16]	= Device address (Cluster ID)
Bit[23:22]	= Reserved (xxb)
Bit[30:24]	= Register address
Bit[31]	= Request/Response = 0b
Bit[47:32]	= Register Data

Note: Writing to reserved registers performs no operation and loads no data in the reserved register.

10.4.3 Global write command

The global write command allows the transformer user to communicate to all devices on the bus at the same time. The global write command is useful to program all devices at the same time with values for fault threshold or to synchronize conversions for all devices on the bus. When a slave receives a valid global write command, the message is acted upon, but no response is generated.

Table 30. Global write command table

Command name	Register data	Request/ Response	Register address	Reserved	Device address (Cluster ID)	Message counter	Reserved	Command	CRC
	Bit[47:32]	Bit[31]	Bit[30:24]	Bit[23:22]	Bit[21:16]	Bit[15:12]	Bit[11:10]	Bit[9:8]	Bit[7:0]
Global Write command	Register Data	0b	Register address	xxb	XX XXXXb (global)	MsgCntr	xxb	11b	CRC

Battery cell controller IC

Table 31. Legend for global write command table

Write command	
Bit[7:0]	= 8-bit CRC
Bit[9:8]	= Command field (11b)
Bit[11:10]	= Reserved (xxb)
Bit[15:12]	= Message counter = xxxxb (global)
Bit[21:16]	= Device address (Cluster ID) = xx xxxxb (global)
Bit[23:22]	= Reserved = xxb, Don't care
Bit[30:24]	= Register address
Bit[31]	= Request/Response = 0b
Bit[47:32]	= Register Data

10.4.4 No operation command

The No Operation (NOP) command allows the user to reset the communication time-out timer of the MC33772C. If the pack controller has no new request for MC33772C IC but does not want the MC33772C to reset (and lose its CID address), it can send a NOP command to the MC33772C IC. The NOP command does not trigger any response or operation from the MC33772C. Thus, the NOP command can be used by the pack controller like a ping to prevent the IC from resetting itself.

Table 32. No operation command table

Command name	Register data	Request/ Response	Register address	Reserved	Device address (Cluster ID)	Message counter	Reserved	Command	CRC
	Bit[47:32]	Bit[31]	Bit[30:24]	Bit[23:22]	Bit[21:16]	Bit[15:12]	Bit[11:10]	Bit[9:8]	Bit[7:0]
No operation (NOP) command	Register Data	0b	Register address	xxb	CID	xxxxb	xxb	00b	CRC

Table 33. Legend for no operation command and no operation response tables

Write command	
Bit[7:0]	= 8-bit CRC
Bit[9:8]	= Command field (00b)
Bit[11:10]	= Reserved (xxb)
Bit[15:12]	= Message counter
Bit[21:16]	= Device address (Cluster ID) = CID
Bit[23:22]	= Reserved = xxb, Don't care
Bit[30:24]	= Register address
Bit[31]	= Request/Response = 0b
Bit[47:32]	= Register Data

Battery cell controller IC

10.4.5 Command and response summary

Table 34. Command summary table

Table 34. Command Summary table												
Command name	Register data	Request/ Response	Register address	Reserved	Device address (Cluster ID)	Message counter	Reserved	Command	CRC			
	Bit[47:32]	Bit[31]	Bit[30:24]	Bit[23:22]	Bit[21:16]	Bit[15:12]	Bit[11:10]	Bit[9:8]	Bit[7:0]			
NOP command	xxxxb	0b	xxx xxxxb	xxb	CID	XXXXb	XXb	00b	CRC			
Read command	Number of registers	0b	Register address	xxb	CID	XXXXb	XXb	01b	CRC			
Write command	Register Data	0b	Register address	xxb	CID	XXXXb	XXb	10b	CRC			
Global write command	Register Data	0b	Register address	xxb	XX XXXXb	XXXXb	XXb	11b	CRC			

If a device has its cluster ID (CID) equal to 00 0000b, then only its INIT register can be written by the pack controller. All the MC33772C devices have their First message from MCU controller writing to cluster ID 00 0000b. To perform a read/write operation of any register (other than INIT) of MC33772C IC, the MCU must first assign a unique address to each MC33772C device by writing to its INIT register with a suitable CID value. The process of assigning a unique CID address to each slave device by the pack controller is called *initialization*.

After initialization, each time the device receives a frame having the Request/Response bit equal to logic 1, this frame is not recognized, even though the address contained in the CID field is equal to the programmed one. In this condition, the device neither acts upon nor answers the command. This is a normal behavior, whose purpose is to avoid the device acting upon or responding to a frame generated by another slave device of the network.

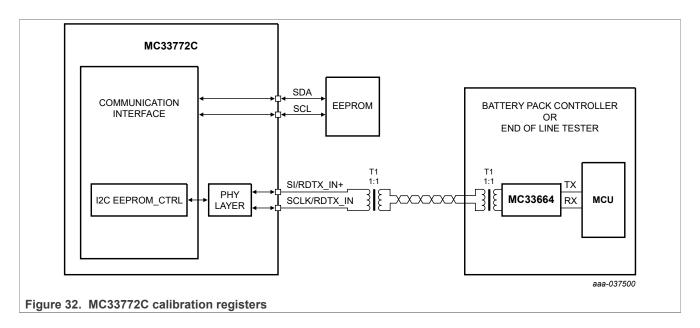
Table 35. Response summary table

Command name	Register data	Request/ Response	Register address	Reserved	Device address (Cluster ID)	Message counter	Reserved	Command	CRC
	Bit[47:32]	Bit[31]	Bit[30:24]	Bit[23:22]	Bit[21:16]	Bit[15:12]	Bit[11:10]	Bit[9:8]	Bit[7:0]
Read response	Register Data	1b	Register address	00b	CID	MsgCntr	XXb	01b	CRC

10.5 I²C communication interface

As an optional feature, the MC33772C has an integrated I²C communication link to an external local EEPROM, which may be used to store calibration parameters defined by the user. If the EEPROM is not used, then the SCL and SDA pins must be left open. When this occurs, the FAULT1_STATUS[I2C_ERR_FLT] bit is automatically updated to logic 1. The automatic update happens even if an error bit is masked. If no EEPROM is mounted, the pack controller has to ignore the content of FAULT1_STATUS[I2C_ERR_FLT].

Battery cell controller IC



11 Registers

11.1 Register map

Important: Trying to access registers marked as reserved produces responses having all zeros in the data field.

Unless otherwise stated, in all register descriptions, POR means one of the following:

- · Power on reset
- Hardware reset
- Software reset
- Reset event based on SYS_CFG2[FLT_RST_CFG] register configuration

Table 36. Register table

Registe	r	Response	Reference	Description	Notes
A[6:0]	Symbol				
\$00	Reserved	Table 26		Reserved	Not readable or writeable
\$01	INIT	Table 26	Section 11.2	Device initialization	Global write is forbidden for CID
\$02	SYS_CFG_ GLOBAL	Table 26	Section 11.3	Global system configuration	Only accessible through a global access in transformer mode. In SPI mode it can be written by a standard write command.
\$03	SYS_CFG1	Table 26	Section 11.4	System configuration	
\$04	SYS_CFG2	Table 26	Section 11.5	System configuration	
\$05	SYS_DIAG	Table 26	Section 11.6	System diagnostic	Writable in DIAG mode only, automatically

MC33772C

All information provided in this document is subject to legal disclaimers.

© 2024 NXP B.V. All rights reserved.

Table 36. Register table...continued

Registe	r	Response	Reference	Description	Notes
A[6:0]	Symbol				
					cleared when exiting DIAG mode
\$06	ADC_CFG	Table 26	Section 11.7	ADC configuration	
\$07	ADC2_OFFSET_ COMP	Table 26	Section 11.8	ADC2 offset compensation	
\$08	OV_UV_EN	Table 26	Section 11.9	CT measurement selection	
\$09	CELL_OV_FLT	Table 26	Section 11.10	CT overvoltage fault	
\$0A	CELL_UV_FLT	Table 26	Section 11.11	CT undervoltage fault	
\$0B	TPL_CFG	Table 26	Section 11.12	TPL configuration for up and down Transmitter	
\$0C	CB1_CFG	Table 26	Section 11.13	CB configuration for cell 1	
\$0D	CB2_CFG	Table 26	Section 11.13	CB configuration for cell 2	
\$0E	CB3_CFG	Table 26	Section 11.13	CB configuration for cell 3	
\$0F	CB4_CFG	Table 26	Section 11.13	CB configuration for cell 4	
\$10	CB5_CFG	Table 26	Section 11.13	CB configuration for cell 5	
\$11	CB6_CFG	Table 26	Section 11.13	CB configuration for cell 6	
\$12	Reserved	Table 26	Section 11.47	NXP reserved	
\$13	Reserved	Table 26	Section 11.47	NXP reserved	
\$14	Reserved	Table 26	Section 11.47	NXP reserved	
\$15	Reserved	Table 26	Section 11.47	NXP reserved	
\$16	Reserved	Table 26	Section 11.47	NXP reserved	
\$17	Reserved	Table 26	Section 11.47	NXP reserved	
\$18	Reserved	Table 26	Section 11.47	NXP reserved	
\$19	Reserved	Table 26	Section 11.47	NXP reserved	
\$1A	CB_OPEN_FLT	Table 26	Section 11.14	Open CB fault	
\$1B	CB_SHORT_FLT	Table 26	Section 11.15	Short CB fault	
\$1C	CB_DRV_STS	Table 26	Section 11.16	CB driver status	
\$1D	GPIO_CFG1	Table 26	<u>Section 11.17</u>	GPIO configuration	
\$1E	GPIO_CFG2	Table 26	Section 11.18	GPIO configuration	
\$1F	GPIO_STS	Table 26	Section 11.19	GPIO diagnostic	
\$20	AN_OT_UT_FLT	Table 26	Section 11.20	AN over and undertemperature	
\$21	GPIO_SHORT_ ANx_OPEN_STS	Table 26	Section 11.21	Short GPIO / Open AN diagnostic	
\$22	I_STATUS	Table 26	Section 11.22	PGA DAC value	
\$23	COM_STATUS	Table 26	Section 11.23	Number of COM error counted	
\$24	FAULT1_STATUS	Table 26	Section 11.24	Fault status	
\$25	FAULT2_STATUS	Table 26	Section 11.25	Fault status	

Table 36. Register table...continued

Registe	r	Response	Reference	Description	Notes
A[6:0]	Symbol				
\$26	FAULT3_STATUS	Table 26	Section 11.26	Fault status	
\$27	FAULT_MASK1	Table 26	Section 11.27	FAULT pin mask	
\$28	FAULT_MASK2	Table 26	Section 11.28	FAULT pin mask	
\$29	FAULT_MASK3	Table 26	Section 11.29	FAULT pin mask	
\$2A	WAKEUP_MASK1	Table 26	Section 11.30	Wake-up events mask	
\$2B	WAKEUP_MASK2	Table 26	Section 11.31	Wake-up events mask	
\$2C	WAKEUP_MASK3	Table 26	Section 11.32	Wake-up events mask	
\$2D	CC_NB_SAMPLES	Table 26	Section 11.33	Number of samples in coulomb counter	
\$2E	COULOMB_CNT1	Table 26	Section 11.34	Coulomb counting accumulator	
\$2F	COULOMB_CNT2	Table 26	Section 11.34	Coulomb counting accumulator	
\$30	MEAS_ISENSE1	Table 26	Section 11.35	ISENSE measurement	
\$31	MEAS_ISENSE2	Table 26	Section 11.35	ISENSE measurement	
\$32	MEAS_STACK	Table 26	Section 11.36	Stack voltage measurement	
\$33	Reserved	Table 26	Section 11.47	NXP reserved	
\$34	Reserved	Table 26	Section 11.47	NXP reserved	
\$35	Reserved	Table 26	Section 11.47	NXP reserved	
\$36	Reserved	Table 26	Section 11.47	NXP reserved	
\$37	Reserved	Table 26	Section 11.47	NXP reserved	
\$38	Reserved	Table 26	Section 11.47	NXP reserved	
\$39	Reserved	Table 26	Section 11.47	NXP reserved	
\$3A	Reserved	Table 26	Section 11.47	NXP reserved	
\$3B	MEAS_CELL6	Table 26	Section 11.36	Cell 6 voltage measurement	
\$3C	MEAS_CELL5	Table 26	Section 11.36	Cell 5 voltage measurement	
\$3D	MEAS_CELL4	Table 26	Section 11.36	Cell 4 voltage measurement	
\$3E	MEAS_CELL3	Table 26	Section 11.36	Cell 3 voltage measurement	
\$3F	MEAS_CELL2	Table 26	Section 11.36	Cell 2 voltage measurement	
\$40	MEAS_CELL1	Table 26	Section 11.36	Cell 1 voltage measurement	
\$41	MEAS_AN6	Table 26	Section 11.36	AN6 voltage measurement	
\$42	MEAS_AN5	Table 26	Section 11.36	AN5 voltage measurement	
\$43	MEAS_AN4	Table 26	Section 11.36	AN4 voltage measurement	
\$44	MEAS_AN3	Table 26	Section 11.36	AN3 voltage measurement	
\$45	MEAS_AN2	Table 26	Section 11.36	AN2 voltage measurement	
\$46	MEAS_AN1	Table 26	Section 11.36	AN1 voltage measurement	
\$47	MEAS_AN0	Table 26	Section 11.36	AN0 voltage measurement	
\$48	MEAS_IC_TEMP	Table 26	Section 11.36	IC temperature measurement	

Table 36. Register table...continued

Registe	r	Response	Reference	Description	Notes
A[6:0]	Symbol				
\$49	MEAS_VBG_ DIAG_ADC1A	Table 26	Section 11.36	ADC1-A voltage reference measurement	
\$4A	MEAS_VBG_ DIAG_ADC1B	Table 26	Section 11.36	ADC1-B voltage reference measurement	
\$4B	TH_ALL_CT	Table 26	Section 11.37	CTx over and undervoltage threshold	
\$4C	Reserved	Table 26	Section 11.47	NXP reserved	
\$4D	Reserved	Table 26	Section 11.47	NXP reserved	
\$4E	Reserved	Table 26	Section 11.47	NXP reserved	
\$4F	Reserved	Table 26	Section 11.47	NXP reserved	
\$50	Reserved	Table 26	Section 11.47	NXP reserved	
\$51	Reserved	Table 26	Section 11.47	NXP reserved	
\$52	Reserved	Table 26	Section 11.47	NXP reserved	
\$53	Reserved	Table 26	Section 11.47	NXP reserved	
\$54	TH_CT6	Table 26	Section 11.38	CT6 over and undervoltage threshold	
\$55	TH_CT5	Table 26	Section 11.38	CT5 over and undervoltage threshold	
\$56	TH_CT4	Table 26	Section 11.38	CT4 over and undervoltage threshold	
\$57	TH_CT3	Table 26	Section 11.38	CT3 over and undervoltage threshold	
\$58	TH_CT2	Table 26	Section 11.38	CT2 over and undervoltage threshold	
\$59	TH_CT1	Table 26	Section 11.38	CT1 over and undervoltage threshold	
\$5A	TH_AN6_OT	Table 26	Section 11.39	AN6 overtemperature threshold	
\$5B	TH_AN5_OT	Table 26	Section 11.39	AN5 overtemperature threshold	
\$5C	TH_AN4_OT	Table 26	Section 11.39	AN4 overtemperature threshold	
\$5D	TH_AN3_OT	Table 26	Section 11.39	AN3 overtemperature threshold	
\$5E	TH_AN2_OT	Table 26	Section 11.39	AN2 overtemperature threshold	
\$5F	TH_AN1_OT	Table 26	Section 11.39	AN1 overtemperature threshold	
\$60	TH_AN0_OT	Table 26	Section 11.39	AN0 overtemperature threshold	
\$61	TH_AN6_UT	Table 26	Section 11.39	AN6 undertemperature threshold	
\$62	TH_AN5_UT	Table 26	Section 11.39	AN5 undertemperature threshold	
\$63	TH_AN4_UT	Table 26	Section 11.39	AN4 undertemperature threshold	
\$64	TH_AN3_UT	Table 26	Section 11.39	AN3 undertemperature threshold	
\$65	TH_AN2_UT	Table 26	Section 11.39	AN2 undertemperature threshold	

Table 36. Register table...continued

Registe	r	Response	Reference	Description	Notes
A[6:0]	Symbol				
\$66	TH_AN1_UT	Table 26	Section 11.39	AN1 undertemperature threshold	
\$67	TH_AN0_UT	Table 26	Section 11.39	AN0 undertemperature threshold	
\$68	TH_ISENSE_OC	Table 26	Section 11.40	ISENSE overcurrent threshold	
\$69	TH_COULOMB_ CNT_MSB	Table 26	Section 11.41	Coulomb counter threshold (MSB)	
\$6A	TH_COULOMB_ CNT_LSB	Table 26	Section 11.41	Coulomb counter threshold (LSB)	
\$6B	SILICON_REV	Table 26	Section 11.42	Silicon revision	
\$6C	EEPROM_CNTL	Table 26	Section 11.43	EEPROM transfer control	
\$6D	DED_ENCODE1	Table 26	Section 11.44	ECC signature 1	
\$6E	DED_ENCODE2	Table 26	Section 11.45	ECC signature 2	
\$6F	FUSE_MIRROR_ DATA	Table 26	Section 11.46	Fuse mirror data	
\$70	FUSE_MIRROR_ CNTL	Table 26	Section 11.46	Fuse mirror address	
\$71	Reserved	Table 26	Section 11.47	NXP reserved	
	Reserved	Table 26	Section 11.47	NXP reserved	
\$7F	Reserved	Table 26	Section 11.47	NXP reserved	

Table 37. Mirror memory

Register		Description	Notes
A[4:0]	Name		
\$00	FUSE_MIRROR_BANK0	Fuse bank 0	
\$01	FUSE_MIRROR_BANK1	Fuse bank 1	
\$02	FUSE_MIRROR_BANK2	Fuse bank 2	
\$03	FUSE_MIRROR_BANK3	Fuse bank 3	
\$04	FUSE_MIRROR_BANK4	Fuse bank 4	
\$05	FUSE_MIRROR_BANK5	Fuse bank 5	
\$06	FUSE_MIRROR_BANK6	Fuse bank 6	
\$07	FUSE_MIRROR_BANK7	Fuse bank 7	
\$08	FUSE_MIRROR_BANK8	Fuse bank 8	
\$09	FUSE_MIRROR_BANK9	Fuse bank 9	
\$0A	FUSE_MIRROR_BANK10	Fuse bank 10	
\$0B	FUSE_MIRROR_BANK11	Fuse bank 11	
\$0C	FUSE_MIRROR_BANK12	Fuse bank 12	
\$0D	FUSE_MIRROR_BANK13	Fuse bank 13	

Battery cell controller IC

Table 37. Mirror memory...continued

Register		Description	Notes
A[4:0]	Name		
\$0E	FUSE_MIRROR_BANK14	Fuse bank 14	DED_ENCODE2
\$0F	FUSE_MIRROR_BANK15	Fuse bank 15	DED_ENCODE1
\$10	FUSE_MIRROR_BANK16	Fuse bank 16	Traceability
\$11	FUSE_MIRROR_BANK17	Fuse bank 17	Traceability
\$12	FUSE_MIRROR_BANK18	Fuse bank 18	Traceability

11.2 Initialization register – INIT

Following power-up or soft POR, the MC33772C is in a reset state. In the Init mode, the user may read the registers of the MC33772C using the cluster id 00 0000b. The MC33772C must be enumerated before it acts upon to write commands.

To initialize the device, a write command has to be sent with the value of 00 0000b in the cluster Identifier field of the frame, Section 10.4.2 "Local write command", with the new cluster ID, that is the new address to be assigned to the node, must be written to the CID field of the INIT register. Only a device with current cluster ID of 00 0000b may be programmed to a new address. By programming the device with a new CID the device is considered enumerated. After a device has been initialized, it only acts on subsequent global write (transformer mode) or local write and responds to read commands matching the device cluster ID. Once a device has been enumerated, the CID bits in the register INIT cannot be reprogrammed unless the device receives a hard or soft reset.

The bit fields INIT[TPLx_TX_TERM] are used for preventing pins (RDTX_IN/OUT±) from floating when the MC33772Cs are connected in single ended daisy chain (without loop-back). It is to be noted that this applies only to last node in the daisy chain. Depending on which pin (RDTX_IN± or RDTX_OUT±) of last node is floating, INIT[TPLx_TX_TERM] should be set to 1. The MC33772C IC used in daisy chain communication with loop-back shall have the bit fields INIT[TPLx_TX_TERM] set to zero while for single ended daisy chain communication (without loop-back) the floating TPL port shall be set to 1.

When the bus forwarding bit INIT[BUSFW] is 0 (default):

The IC forwards all messages to its neighboring node. The IC also responds to read messages in both directions to balance current consumption for all nodes of the daisy chain.

When INIT[BUSFW] is 1:

- · Normal mode: The IC does not forward any message
- Sleep mode: The IC only forwards the wake-up messages to enable all nodes in daisy chain to be activated
- The IC responds only in one direction (the direction in which it received the request). However, in case of internal fault in Sleep mode the IC sends wake-up messages in both directions on the daisy chain.

Battery cell controller IC

Table 38. INIT

Tubic c	O. IIVI	·															
INIT																	
\$01	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0	
Write									TPL1_	TPL2_							
Read	0	0	0	0	0	0	0	BUS_FW	TX_ TERM	TX_ TERM			(CID			
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	
		Description	on	Bus forwa	Bus forwarding, from one port to the opposite port and single side response to a READ request												
BUS FW		0		Forwardii	ng to neigh	boring node	e and respo	nse on both	n sides (onl	y if CID ≠ \$	(00)						
BUS_FW		1		Stop forw	arding and	response o	on single si	de (side at v	which the re	equest was	received)						
		Reset co	ndition	POR													
		Description	on	TPL trans	TPL transmitter termination for lower port (RDTX_IN)												
TDI 1 TV	- FPL1 TX TERM -	0		Disabled	Disabled												
IFLI_IA	_I EKIVI	1		Enabled	Enabled												
		Reset co	ndition	POR													
		Description	on	TPL trans	mitter term	ination for	upper port	(RDTX_OU	T)								
TPL2 TX	TEDM	0		Disabled													
IPLZ_IA	_I EKIVI	1		Enabled													
		Reset co	ndition	POR													
		Description	on	Cluster Id	lentifier. Ca	n be overio	lden by any	combination	n different	from "all ze	eros". Not	accessible	with global	write			
CID		00000	0	Default													
CID		xxxxx	ĸ	CID													
		Reset co	ndition	POR													

11.3 System configuration global register SYS_CFG_GLOBAL

In TPL mode, only a global command can be used to write to register \$02, while a local write is disregarded. In contrast, if using the SPI mode, only a local write to register \$02 can be executed.

Table 39. SYS_CFG_GLOBAL

SYS_CF	SYS_CFG_GLOBAL															
\$02	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write																GO2 SLEEP
Read	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
		Description	escription Go to sleep command													
CO201 E	-n	0		Disabled												
GUZSLEI	GO2SLEEP		pulse)	Device go	Device goes to Sleep mode after all conversions in progress are completed											
			ndition	POR												

11.4 System configuration register 1 - SYS_CFG1

The SYS_CFG1 register contains control bits and register settings that allow the user to adapt the MC33772C to specific applications and system requirements. Of these control bits, it is important to note the SYS_CFG1[SOFT_RST] bit is used to reset register contents of the device.

Table 40. SYS_CFG1

SYS_CFG1	SYS_CFG1															
\$03	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write	CYCLIC_TIMER		DIAG TIMEOUT			I_ MEAS	DO NOT CHANGE	CB_ DRVEN	GO2DIAG		SOFT_ RST	FAULT_ WAVE	WAVE_ DC_BITx		х	
Read									DIAG_ST	PAUSE	0				x	
Reset	0	0	0	1	0	0	0	0	0	0	0	0	0	0	0	1

Table 40. SYS_CFG1...continued

Table 40. SYS_C	FG1continu	ed .
	Description	Timer to trigger cyclic measurements in Normal mode or Sleep mode
	0 0 0	Cyclic measure is disabled, whatever the mode
	0 0 1	Continuous measurements
	0 1 0	0.1 s
OVOLIO TIMED	0 1 1	0.2 s
CYCLIC_TIMER	100	1.0 s
	1 0 1	2.0 s
	1 1 0	4.0 s
	111	8.0 s
	Reset condition	POR
	Description	Diag mode timeout. Length of time the device is allowed to be in Diag mode before being forced to Normal mode
	0 0 0	No timer, not allowed to enter Diag mode
	0 0 1	0.05 s
	0 1 0	0.1 s
	0 1 1	0.2 s
DIAG_TIMEOUT	100	1.0 s
	101	2.0 s
	110	4.0 s
	111	8.0 s
	Reset condition	POR
	Description	Enable for current measurement chain
	0	Disabled
I_MEAS_EN		
	1	Current measurement chain is enabled
	Reset condition	POR
	Description	General enable or disable for all cell balance drivers
CB_DRVEN	0	Disabled
	1	Enabled, each cell balance driver can be individually switched on and off by CBx_CFG register
	Reset condition	POR
	Description	Commands the device to Diag mode. Rewriting the GO2DIAG bit restarts the DIAG_TIMEOUT
GO2DIAG	0	Exit Diag mode
	1	Enter Diag mode (starts timer)
	Reset condition	POR
	Description	Cell balancing manual pause
CB_MANUAL_PAUSE	0	Disabled. CB switches can be normally commanded on/off by the dedicated logic functions
05	1	CB switches are forced off, CB counters are not frozen
	Reset condition	POR
	Description	Identifies when the device is in Diag mode
DIAG_ST	0	System is not in Diag mode
DIAO_01	1	System is in Diag mode
	Reset condition	POR
	Description	Software reset
COET DET	0	Disabled
SOFT_RST	1 (active pulse)	Active software reset
	Reset condition	POR (bit is not reset if reset was due to software reset)
	Description	FAULT pin waveform control bit
FALUE MANGE	0	FAULT pin has high or low level behavior. FAULT pin high, fault is present. FAULT pin low indicates no fault present
FAULT_WAVE	1	FAULT pin has heartbeat wave when no fault is present. Pulse high time is fixed at 500 μs
	Reset condition	POR
	Description	Controls the off time of the heartbeat pulse
	0 0	500 μs
WAVE_DC_BITx	0 1	1.0 ms
	10	10 ms
i		1

Battery cell controller IC

Table 40. SYS_CFG1...continued

11	100 ms
Reset condition	POR

11.5 System configuration register 2 – SYS_CFG2

Table 41. SYS_CFG2

SYS_CFG2	_																
\$04	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0	
Write	x	х	х							[4]	TIME	OUT	x	w0c ^[2]	NUMB	HAMM	
Read	х	х	х	PRE	/IOUS_S	L ΓΑΤΕ		FLT_RS	ST_CFG	[1]		MM	×	VPRE_UV	ODD_	ENCO	
Reset	0	0	0	0	0	0	1	1	0	0	1	1	0	1	0	0	
	1	Description		Informati	on about t	he previo	us state	of the	device				I	l	<u> </u>	1	
		0 0 0		The devi	ce is comi	ng from li	nit state	(reset v	/alue)								
		0 0 1		The device is coming from Idle state													
PREVIOUS_	CTATE	0 1 0		The device is coming from Normal state													
PREVIOUS_	_STATE	0 1 1		The device is coming from Diag state													
		111		The device is coming from Sleep state													
		110		The device is coming from Cyclic_WUP state													
		Reset condit	ion	POR													
		Description		Fault reset configuration ^[3]													
		0 0 1 1		Disabled COM timeout (1024 ms) reset and OSC fault monitoring and reset													
		0 1 0 1		Enabled OSC fault monitoring													
		0110		Enabled OSC fault monitoring and reset													
FLT_RST_C	FG	1001		Enabled COM timeout (1024 ms) reset													
		1010		Enabled COM timeout (1024 ms) reset and OSC fault monitoring Enable COM timeout (1024 ms) reset and OSC fault monitoring and reset (reset value)													
		1100		Enable C	OM timed	ut (1024	ms) res	et and C	OSC fau	It monito	ring and r	eset (reset	t value)				
		others		Invalid, le	eads to en	abled CC	M time	out (102	24 ms) re	eset and	OSC fault	monitorin	g and reset	(1100)			
		Reset condit	ion	POR													
		Description		No communication timeout - flag in FAULT1_STATUS[COM_LOSS] if no communication during													
		0 0		32 ms													
TIMEOUT_C	NMO	0 1		64 ms													
TIMEOUT_C	OUNIN	10		128 ms													
		11		256 ms (reset value)													
		Reset condit	ion	POR													
		Description		V _{PRE} und	lervoltage	detection	ı										
VPRE_UV		0		No unde	rvoltage d	etected (r	eset va	lue)									
VI IXE_0V		1		Undervol	tage dete	cted on V	PRE										
		Reset condit	ion	POR / CI	ear on wr	te 0											
		Description		Odd num	ber of cel	ls in the c	luster (ı	useful fo	or open-	load diag	ınosis)						
NUMB ODE)	0		Even cor	nfiguration	(reset va	ılue)										
NOMB_ODE	,	1		Odd cont	figuration												
		Reset condit	ion	POR													
		Description		Hamming	g encoder	s											
HAMM_ENC	COD	0		Decode -	the DED	Hamming	g decod	ers fulfil	I their jo	b (reset	value)						
, aviivi_LINC	,00	1		Encode -	the DED	Hamming	g decod	ers gene	erate the	e redund	ancy bits						
		Reset condit	ion	POR													

The GO2RESET option should not be disabled after a communication time out.

w0c: write 0 to clear
For more information, refer to Figure 8

11.6 System diagnostics register - SYS_DIAG

Table 42. SYS DIAG

	42. SYS	5_DIAC	,															
SYS_DIA		I	I	I	I	I	T	I	I	I	T	I	I	I	I	1		
\$05	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0		
Write	FAULT_				1UX	ISENSE_ OL_	ANx_ OL_	ANx_ TEMP_	DA_DIAG	POL	CT_ LEAK_	CT_	CT_OL_	CT_OL_	CB_OL_	CB_OL		
Read	DIAG	0	0			DIAG	DIAG	DIAG		ARIII	DIAG	ov_ūv	ODD	EVEN	ODD	EVEN		
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0		
		Description	on	FAULT pi	n driver cor	nmand												
AULT_D	IAG	0		No FAUL	Γ pin drive,	FAULT pin	is under co	ommand of	the pack co	ontroller								
		1		FAULT pi	n is forced	to high leve	el											
		Reset co	ndition	POR														
		Description	on	Allows user to select between various inputs to PGA to be converted by ADC2														
		0 0		(ISENSE+, ISENSE-) (GPIO5, GPIO6)														
I_MUX		0 1		(GPIO5,	GPIO6)													
_wox		1 0		Calibrate	Calibrated internal reference (VREF_DIAG)													
		11		PGA zero	(PGA diffe	rential inpu	ıts terminat	ed to grour	nd)									
		Reset co	ndition	POR														
		Description	on	ISENSE open load diagnostic control bit. Enables or disables internal pull-up resistors on the ISENSE input pins														
CENCE	OL DIAC	0		Disabled														
ISENSE_	OL_DIAG	1		Enabled Enabled														
		Reset co	ndition	POR														
		Description	on	ANx open load diagnostic control bit. Used to activate the pull-down on GPIO input pins														
	DIA C	0		Diagnostic disabled														
ANx_OL_	DIAG	1		Diagnosti	Diagnostic enabled													
		Reset co	ndition	POR														
		Description	on	Control b	Control bit to activate the OT/UT diagnostic on GPIOx configured as ANx ratiometric or single ended ADC input													
		0		Diagnosti	Diagnostic inactive													
ANx_TEN	/IP_DIAG	1		Diagnosti	Diagnostic active													
		Reset cor	ndition	POR														
		Description	on	Cell volta	ge channel	functional	verification	. Diagnostic	mode fund	tion only								
		0		Cell voltage channel functional verification. Diagnostic mode function only No check														
DA_DIAG	3	1				pating Zene	r conversion	on, ground	Zener meas	surement a	dded, com	parison)						
		Reset co	ndition	POR								,						
		Description			t used in te	rminal leak	age detect	ion. Contro	ls the polari	tv between	n the level s	hifter and t	he ADC1-A	and ADC1	-B converte	ers		
		0		Noninver			<u> </u>			,								
POLARIT	Υ	1		Inverted														
		Reset cor	ndition	POR														
		Description		Control b	t used in te		age detect	ion. Comm	ands the M	JX to route	e the CTx/C	Bx pin to A	DC1-A,B c	onverters.	This bit mus	st be		
CT_LEA	CDIAG	0			peration, C		Ked to conv	erter										
0	5	1		Δ betwee	n CT and C	B pins are	routed to the	he analog f	ront end, to	be conver	ted							
		Reset cor	ndition	POR	_													
		Description	on	OV and U	IV diagnost	ic is enable	ed. This bit	must be se	t to logic 0 v	when perfo	orming CT o	pen load d	iagnostic					
		0			IV diagnost							·						
CT_OV_I	JV	1			IV diagnost													
		Reset co	ndition	POR														
		Description		-	t used to co	ontrol the o	dd number	ed cell term	ninal open d	etect swite	hes							
		0		Control bit used to control the odd numbered cell terminal open detect switches Odd switches are open														
CT_OL_0	DDD	1		-			ne set only	when CT (OL EVFN i	s logic (1)								
		Reset cor	ndition	Odd switches are closed (may be set only when CT_OL_EVEN is logic 0) POR														
		Description			t used to o	ontrol the o	ven numbo	red cell tor	minal open	detect cui	tches							
	EVEN	Description	211	Control D	. 4304 10 0	J. 10 01 01 0 0	· on munibe	nou och ich	mai open	actool SWI	10100							

Table 42. SYS_DIAG...continued

	1	Even switches are closed (may be set only when CT_OL_ODD is logic 0)
	Reset condition	POR
	Description	Control bit used to control the cell balance open load ODD detection switches
CB OL ODD	0	ODD cell balance open load detection switches are open
CB_OL_ODD	1	ODD cell balance open load detection switches are closed
	Reset Condition	POR
	Description	Control bit used to control the cell balance open load EVEN detection switches
CB OL EVEN	0	EVEN cell balance open load detection switches are open
OB_OL_EVEN	1	EVEN cell balance open load detection switches are closed
	Reset condition	POR

11.7 ADC configuration register - ADC_CFG

The ADC_CFG is used to set the conversion parameters of the three ADC converters and command the MC33772C to perform on-demand conversions in both normal and diagnostic modes.

Table 43. ADC_CFG

ADC_CF	G																	
\$06	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0		
Write					soc		PGA_GAII	N .	CC_RST	х	4004	A DEE	400	. D. DEE	400	0. DEE		
Read		P	WG		EOC_N	F	PGA_GAIN	_S	0	х	ADC1	_A_DEF	ADC	I_B_DEF	ADC	2_DEF		
Reset	0	0	0	0	0	1	0	0	0	0	0	1	0	1	1	1		
		Descripti	on	With each	conversion	n request,	the number	of sample	s to be aver	aged can	be configu	red	'		'			
		0000		No averag	ging, the re	sult is take	n as is (cor	npatibility n	node)									
		0 0 0 1		Averaging	Averaging of 2 consecutive samples Averaging of 4 consecutive samples													
		0 0 1 0		Averaging	of 4 conse	cutive sar	nples											
		0 0 1 1		Averaging	Averaging of 8 consecutive samples													
		0 1 0 0		Averaging of 16 consecutive samples														
AVG		0 1 0 1		Averaging	Averaging of 32 consecutive samples													
		0 1 1 0		Averaging	Averaging of 64 consecutive samples													
		0 1 1 1		Averaging	Averaging of 128 consecutive samples													
		1000		Averaging	Averaging of 256 consecutive samples													
		All other Configure	ations	No averaging, the result is taken as is (compatibility mode)														
		Reset co	ndition	POR														
		Descripti	on	Control bi	Control bit to command the MC33772C to initiate a conversion sequence													
soc		0		Disabled. Writing SOC to 0 has no effect on an ongoing conversion sequence														
300		1 (active	pulse)	Enabled. Initiate a conversion sequence														
		Reset co	ndition	POR														
		Descripti	on	End of co	nversion fla	ıg												
EOC_N		0		Device ha	s complete	d the com	manded co	nversion										
L00_IV		1		Device is	performing	the comm	anded con	version										
		Reset co	ndition	POR														
		Descripti	on	Define the	e gain of the	e ADC2 pr	ogrammabl	e gain amp	lifier									
		000		4														
		0 0 1		16														
PGA_GA	IN	0 1 0		64														
		0 1 1		256														
		1 x x		Automatio	gain selec	tion (interr	ally adjuste	ed)										
		Reset co	ndition	POR	<u> </u>			<u> </u>				<u> </u>						

Battery cell controller IC

Table 43. ADC_CFG...continued

Table 43. AL	JC_CFGcontine	
	Description (bit 10)	Automatic gain mode status (information available only if SYS_CFG1[I_MEAS_EN] = 1)
	0	Fixed gain
	1	Automatic gain control
	Reset condition	POR
PGA_GAIN_S	Description (bit[9:8])	Report the current gain of the ADC2 programmable gain amplifier (automatically settled or not). (information available only if SYS_CFG1[I_MEAS_EN] = 1)
	0 0	4
	0 1	16
	1 0	64
	1 1	256
	Reset condition	POR
	Description	Control bit used to reset the value of the coulomb counter to 0
CC_RST	0	No action
CC_K31	1 (active pulse)	Reset coulomb counter registers COULOMB_CNT1 and COULOMB_CNT2 and the CC_NB_SAMPLES registers
	Reset condition	POR
	Description	ADC1_A measurement resolution
	0 0	13 bit
ADC1_A_DEF	0 1	14 bit
ADC1_A_DEF	1 0	15 bit
	1 1	16 bit
	Reset condition	POR
	Description	ADC1_B measurement resolution
	0 0	13 bit
ADC1 B DEF	0 1	14 bit
ADC1_B_DEF	10	15 bit
	11	16 bit
	Reset condition	POR
	Description	ADC2 measurement resolution
	0 0	13 bit
ADC2 DEE	0 1	14 bit
ADC2_DEF	1 0	15 bit
	1 1	16 bit
	Reset condition	POR
	_	

11.8 Current measurement chain offset compensation - ADC2_OFFSET_COMP

This register contains an 8-bit signed data (two's complement). The content of the offset compensation register is added directly to the data at the end of the channel measurement, independent on the PGA gain. Even though the current channel is fully offset compensated, the PCB HW introduces an extra offset that can be compensated by means of this data. This register provides several bits that are able to influence the behavior of the coulomb counter.

Table 44. ADC2_OFFSET_COMP

ADC2_OF	FSET_CO	MP														
\$07	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write	cc_	FREE	w0c ^[1]	w0c ^[1]	w0c ^[1]	w0c ^[1]	x A	LLCBOFF								•
Read	RST_ CFG	'I_														
Reset	0	1	0	0	0	0	0	0	0	0	0	0	0	0	0	0
		Descriptio	n	Configuration of the action linked to the read of coulomb count results												
00 007	050	0		No linked action												
CC_RST_CFG 1			Reading a	Reading any CC register (from @ \$2D to @ \$2F) also resets the coulomb counters												
		Reset con	dition	POR												

Battery cell controller IC

Table 44. ADC2_OFFSET_COMP...continued

	Description	Configuration of the free running coulomb counters
EDEE ONT	0	No free-running, coulomb counters clamp on min/max values
FREE_CNT	1	Free-running mode. No clamp but rollover
	Reset condition	POR
	Description	Overflow indicator on the COULOMB_CNT1,2[COULOMB_CNT]
CC P OVF	0	No overflow
CC_F_OVF	1	COULOMB_CNT1,2[COULOMB_CNT] went in overflow
	Reset condition	POR / Clear on write 0
	Description	Underflow indicator on the COULOMB_CNT1,2[COULOMB_CNT]
CC N OVF	0	No underflow
CC_N_OVF	1	COULOMB_CNT1,2[COULOMB_CNT] went in underflow
	Reset condition	POR / Clear on write 0
	Description	Overflow indicator on the CC_NB_SAMPLES
SAMP OVF	0	No underflow
SAIVIF_OVF	1	CC_NB_SAMPLES went in overflow
	Reset condition	POR / Clear on write 0
	Description	Overthreshold indicator on the COULOMB_CNT1,2[COULOMB_CNT]
CC OVT	0	No over threshold
CC_0V1	1	COULOMB_CNT1,2[COULOMB_CNT] went in over threshold (TH_COULOMB_CNT)
	Reset condition	POR / Clear on write 0
	Description	All CB's turn off in case of at least one short
ALLCBOFF ON	0	Only shorted CB's are turned off
SHORT	1	If at least one CB is shorted, all CB's are then turned off (CB_DRVEN is reset)
	Reset condition	POR
ADC2_OFFSET_	Description	Offset value, signed (two's complement) with V _{2RES} resolution. It can be used to compensate for a PCB offset
COMP	Reset condition	POR

^[1] w0c: write 0 to clear

11.9 Cell select register - OV_UV_EN

The user has the option to select a common overvoltage and undervoltage threshold, or individual thresholds for each cell. To use a common threshold for all cell terminal inputs, the user must program register TH_ALL_CT and enable the common threshold bit. An individual threshold may be programmed for each cell terminal through register TH_CTx. Either threshold selection requires the CTx_OVUV_EN bit be set for the MC33772C to monitor the cell terminal input for over and undervoltage.

Table 45. OV UV EN

OV_UV_I	EN																
\$08	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0	
Write		соммон									CT6_	CT5_	CT4_	CT3_	CT2_	CT1_	
Read	OV_TH			0	0	0	0	0	0	0	OVUV_ EN	OVUV_ EN	OVUV_ EN	OVUV_ EN	OVUV_ EN	OVUV_ EN	
Reset	0	0	0	0	0	0	0	0	0	0	1	1	1	1	1	1	
	Description			All CTx measurement use the common overvoltage threshold register for comparison													
COMMO	N OV TH	0		Use individual threshold register													
COMMO	N_OV_IH	1		Use com	Use common threshold register												
		Reset con	dition	POR													
		Descriptio	n	All CTx n	neasureme	nt use the	common ur	ndervoltage	threshold	register for	comparison						
COMMO	N 11\/ TLI	0		Use indiv	idual thres	hold registe	er										
COMMO	N_UV_TH	1		Use com	mon thresh	old registe	r										
		Reset condition POR															
		Reset condition POR															

Battery cell controller IC

Table 45. OV_UV_EN...continued

	Description	Enable or disable ADC data to be compared with thresholds for OV/UV. If disabled no OV/UV fault is set
CTx OVUV EN	0	OV/UV disabled
CIX_OVOV_EN	1	OV/UV is enabled
	Reset condition	POR

11.10 Cell terminal overvoltage fault register – CELL_OV_FLT

The CELL_OV_FLT register contains the overvoltage fault status of each cell. The CELL_OV_FLT register is updated with each cyclic conversion and each on-demand conversion from the system controller. In Normal mode, the CTx_OV_FLT bit may be cleared by writing logic 0 when overvoltage is no longer present at the cell terminal inputs.

Table 46. CELL_OV_FLT

CELL_O\	/_FLT															
\$09	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write											w0c ^[1]					
Read	0	0	0	0	0	0	0	0	0	0	CT6_ OV_FLT	CT5_ OV_FLT	CT4_ OV_FLT	CT3_ OV_FLT	CT2_ OV_FLT	CT1_ OV_FLT
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
		Description	on			er contains d conversio		of the overv	oltage faul	t for each c	ell terminal	. Register is	s updated v	vith each in	ternal and	system
CTx_OV_	FLT	0		No cell ter	minal over	voltage										
	1			Cell termi	nal overvol	tage detect	ed on termi	nal x								
		Reset cor	ndition	POR / Cle	ar on write	0										

^[1] w0c: write 0 to clear

11.11 Cell terminal undervoltage fault register – CELL_UV_FLT

The CELL_UV_FLT register contains the undervoltage fault status of each cell. The CELL_UV_FLT register is updated with each cyclic conversion and each on-demand conversion from the system controller. In Normal mode, the CTx_UV_FLT bit may be cleared by writing logic 0 when undervoltage is no longer present at the cell terminal inputs.

Table 47. CELL_UV_FLT

/_FLT															
bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
										w0c ^[1]	w0c ^[1]	w0c ^[1]	w0c ^[1]	w0c ^[1]	w0c ^[1]
0	0	0	0	0	0	0	0	0	0	CT6_UV _FLT	CT5_ UV_FLT	CT4_ UV_FLT	CT3_ UV_FLT	CT2_ UV_FLT	CT1_ UV_FLT
0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Description	on					of the over	oltage faul	t for each c	ell terminal	Register is	updated v	vith each in	ternal and	system
FLT	0		No cell te	rminal unde	ervoltage										
	1	Cell terminal undervoltage detected on terminal x													
	Reset cor	ndition	POR / Cle	ear on write	0										
	bit 15 0 0	bit 15 bit 14	Description Description	Description Description	Description Description Description CTx_UV_FLT registed controller requested Description Cell terminal undervised C	Description Description Description O O O O O O O O O	Description CTx_UV_FLT register contains the status of controller requested conversion cycle Cell terminal undervoltage Cell terminal undervoltage detected on terminal undervoltage Cell terminal undervoltage	Description CTx_UV_FLT register contains the status of the over controller requested conversion cycle Cell terminal undervoltage Cell terminal undervolta	Description CTx_UV_FLT register contains the status of the overvoltage faul controller requested conversion cycle Cell terminal undervoltage detected on terminal x	Description CTx_UV_FLT register contains the status of the overvoltage fault for each of controller requested conversion cycle Cell terminal undervoltage detected on terminal x	Description Description CTx_UV_FLT register contains the status of the overvoltage fault for each cell terminal undervoltage Description Cell terminal undervoltage Cell terminal	Description CTx_UV_FLT register contains the status of the overvoltage fault for each cell terminal. Register is cell terminal undervoltage Cell terminal undervoltage detected on terminal x Description Cell terminal undervoltage Description Cell terminal undervoltage Description Cell terminal undervoltage detected on terminal Description Cell terminal undervoltage Description Cell terminal undervoltage Description Description Description Description Description Cell terminal undervoltage Description D	Description CTx_UV_FLT register contains the status of the overvoltage fault for each cell terminal. Register is updated v Cell terminal undervoltage Cel	Description Description CTx_UV_FLT register contains the status of the overvoltage fault for each cell terminal. Register is updated with each in controller requested conversion cycle Cell terminal undervoltage detected on terminal x	Description Description CTx_UV_FLT register contains the status of the overvoltage fault for each cell terminal. Register is updated with each internal and controller requested conversion cycle Cell terminal undervoltage detected on terminal x

^[1] w0c: write 0 to clear

11.12 TPL register - TPL CFG

TPL_CFG register configures up and down transmitter. It allows the pack controller to configure transmitter drive strength based on capacitive or transformer isolation and selection of differential load termination.

MC33772C

Battery cell controller IC

Table 48. TPL_CFG

TPL_CFG	;															
\$0B	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write								DO NOT	CHANGE							
Read								DO NOT	CHANGE							
Reset	0	1	1	0	0	0	1	0	0	1	1	0	0	0	1	0

Note: The default value TPL_CFG register is set considering a transmission line of 120 Ω .

11.13 Cell balance configuration register - CBx_CFG

The cell balance configuration register holds the operating parameters of the cell balance output drivers.

Table 49. CBx CFG

iable	49. CE	DX_CFC	,													
CBx_CF	G															
\$0C to \$19	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write							CBx_EN		_	1		OD TIME				
Read	0	0	0	0	0	0	CBx_STS					CBx_TIME	=K			
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
		Descripti	on	Cell bala	nce enable	:			'			'				
CDv EN		0		Cell bala	nce driver	disabled										
CBx_EN		1		Cell bala	nce is ena	oled or re-l	aunched if overv	vritten (res	tarts the tin	ner count f	rom zero a	and enables	s the driver)		
		Reset co	ndition	POR												
		Descripti	on	Cell bala	nce driver	status										
ODV OT		0		Cell bala	nce driver	is off										
CBx_STS	5	1		Cell bala	nce driver	is on										
		Reset co	ndition	POR												
		Descripti	on	Cell bala	nce timer i	n minutes										
		0000000	00	0.5 minu	tes											
		0000000	01	1 minute												
CBx_TIM	IER	0000000	10	2 minute	s											
		1111111	11	511 minu	tes											
		Reset co	ndition	POR												

11.14 Cell balance open load fault detection register - CB_OPEN_FLT

Table 50. CB_OPEN_FLT

			<u></u>													
CB_OPE	N_FLT															
\$1A	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write											w0c ^[1]					
Read	0	0	0	0	0	0	0	0	0	0	CB6_ OPEN_ FLT	CB5_ OPEN_ FLT	CB4_ OPEN_ FLT	CB3_ OPEN_ FLT	CB2_ OPEN_ FLT	CB1_ OPEN_ FLT
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
		Descript	on	Cell bala	ncing open	load detec	tion – (info	Logic OR	of CBx_OF	PEN_FLT is	provided in	the FAULT	2_STATUS	[CB_OPE	N_FLT]	
CDv ODI	-N	0		No open	load cell ba	alance fault	detected									
CBx_OPI	EN_FLI	0 No open load cell balance fault detected 1 Off state open load detected														
		Reset co	ndition	POR / CI	ear on write	e 0										

[1] w0c: write 0 to clear

Battery cell controller IC

11.15 Cell balance shorted load fault detection register - CB_SHORT_FLT

The cell balance short detection register holds the cell balance shorted load status.

Table 51. CB_SHORT_FLT

CB_SHO	RT_FLT															
\$1B	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write											w0c ^[1]					
Read	0	0	0	0	0	0	0	0	0	0	CB6_ SHORT_ FLT	CB5_ SHORT_ FLT	CB4_ SHORT_ FLT	CB3_ SHORT_ FLT	CB2_ SHORT_ FLT	CB1_ SHORT_ FLT
Reset	0	0	0	0											0	0
		Description	n	Cell balan	cing shorte	d load faul	t detection -	– (info) CB:	x_SHORT_	FLT Ored i	s provided	in the FAUL	T2[CB_SH	IORT_FLT]		
CBx SHC	OF ELT	0		No shorte	d load fault	detected										
CBX_SHC	JKI_FLI	1		Shorted lo	ad fault de	tected										
		Reset cor	ndition	POR / Cle	ar on write	0										

^[1] w0c: write 0 to clear

11.16 Cell balance driver on/off status register - CB_DRV_STS

Table 52. CB_DRV_STS

CB_DRV	_STS															
\$1C	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write																
Read	0	0	0	0	0 0 0 0 0 CB6_STS CB5_STS CB4_STS CB3_STS CB2_STS CB1_STS											
Reset	0	0	0	0	0 0 0 0 0 0 0 0 0 0 0											
	•	Description	on	Contains	the state of	the cell ba	lance drive	r								
CDv CTC		0		Driver CB	x is off											
CBx_STS 1 Driver CBx is on																
		Reset cor	ndition	POR												

11.17 GPIO configuration register 1 – GPIO_CFG1

The GPIO_CFG1 register programs the individual GPIO port as a ratiometric, single ended, input or output port.

Table 53. GPIO_CFG1

GPIO_CF	-G1															
\$1D	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write			GPIC	6 CFG	GPIO	5 CFG	GPIO	4 CFG	GPIO	3 CFG	GPIO	2 CFG	GPIO	1 CFG	GPIC	0 CFG
Read	0	0	GFIC	00_CFG	GFIO:	5_CFG	GFIO	4_CFG	GFIO	3_CFG	GFIO	2_0FG	GFIO	I_CFG	GFIC	10_CFG
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
		Descript	ion	Register	controls the	configura	tion of the C	SPIO port		'			'		'	
		0 0		GPIOx c	onfigured as	analog in	put for ratio	metric mea	asurement							
CDIO _V C	`FC	0 1		GPIOx c	onfigured as	analog in	put for abso	lute meas	urement							
GPIOX_C	GPIOx_CFG	1 0		GPIOx c	onfigured as	digital inp	out									
	_			GPIOx c	onfigured as	digital ou	tput									
		Reset co	ondition	POR												

11.18 GPIO configuration register 2 - GPIO_CFG2

Table 54. GPIO CFG2

iable () , Oi	10_01	J_													
GPIO_CF	G2															
\$1E	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write							GPIO2_	GPIO0_	GPIO0_ FLT	GPIO6_	GPIO5_	GPIO4_	GPIO3_	GPIO2_	GPIO1_	GPIO0_
Read	0	0	0	0	0	0	soc	WU	ACT	DR	DR	DR	DR	DR	DR	DR
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
		Description	on	GPIO2 us	sed as ADC	1_A/ADC1	_B start-of-	conversion	. Requires	GPIO2_CF	G = 10		•			•
GPIO2 S	00	0		GPIO2 po	ort ADC trig	ger is disal	bled									
GF102_3	00	1		GPIO2 po	ort ADC trig	ger is enab	oled. A risin	g edge on (GPIO2 trigg	ers an AD0	C1-A and A	DC1-B con	version – o	nly when in	n normal m	ode
		Reset co	ndition	POR												
		Description	on	GPIO0 w	ake-up cap	ability. Valid	d only when	GPIO0_C	FG = 10							
GPIO0 W	/1.1	0		No wake-	up capabili	ty										
GF100_W	70	1		Wake-up	on any edg	je, transitio	ning the sys	stem from s	leep to nor	mal						
		Reset co	ndition	POR												
		Description	on	GPIO0 ac	tivate fault	output pin.	Valid only	when GPIC	0_CFG = 1	0						
GPIO0 F	IT ACT	0		Does not	activate FA	ULT pin wl	nen GPIO0	is configure	ed as an inp	out and is lo	ogic 1					
GF100_I	LI_ACI	1		Activates	the FAULT	pin when (GPIO is con	figured as	an input an	d is logic 1						
		Reset co	ndition	POR												
		Description	on	GPIOx pi	n drive. Ign	ored excep	t when GPI	Ox_CFG =	11							
GPIOx D	D	0		Drive GP	Ox to low I	evel										
GFIOX_D	IX	1		Drive GP	Ox to high	level										
		Reset co	ndition	POR												

11.19 GPIO status register - GPIO_STS

Table 55. GPIO_STS

	<u></u>	<u></u>													
s															
bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
	w0c ^[1]	w0c ^[1]	w0c ^[1]	w0c ^[1]	w0c ^[1]	w0c ^[1]	w0c ^[1]								
0	GPIO6_H	GPIO5_H	GPIO4_H	GPIO3_H	GPIO2_H	GPIO1_H	GPIO0_H	0	GPIO6_ ST	GPIO5_ ST	GPIO4_ ST	GPIO3_ ST	GPIO2_ ST	GPIO1_ ST	GPIO0_ ST
Reset 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0								0	0						
	Description	n	The GPIO	x_H bits de	etects and I	atches the	low to high	transition	occurring o	n the GPIO	x input	•			
	0		No high st	ate detecte	ed										
	1		A high sta	te has bee	n detected										
	Reset con	dition	POR / Cle	ar on write	0										
	Description	n	Real time	GPIOx stat	tus										
GPIOx_ST 0	0		Report GF	PIOx at low	level										
	1		Report GF	PIOx at high	n level										
	Reset con	dition	POR												
	bit 15 0 0	S bit 15 bit 14 w0c ^[1] 0 GPIO6_H 0 0 Description 0 1 Reset cor 0 1	bit 15 bit 14 bit 13 w0c ^[1] w0c ^[1] 0 GPIO6_H GPIO5_H 0 0 0 Description 0 1 Reset condition Description 0	S S S S S S S S S S	Description Real time GPIOx at low Description Report GPIOx at low Description Description Description Report GPIOx at low Description Description	S Dit 15 Dit 14 Dit 13 Dit 12 Dit 11 Dit 10	S Dit 15 Dit 14 Dit 13 Dit 12 Dit 11 Dit 10 Dit 9	S S S S S S S S S S	District District	Dit 15	S S S S S S S S S S	Dit 15	Dit 15	Dit 15	Dit 15

^[1] w0c: write 0 to clear

11.20 Overtemperature/undertemperature fault register - AN_OT_UT_FLT

Table 56. AN_OT_UT_FLT

AN_OT_U	JT_FLT															
\$20	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write		w0c ^[1]		w0c ^[1]												
Read	0	AN6_OT	AN5_OT	AN4_OT	AN3_OT	AN2_OT	AN1_OT	AN0_OT	0	AN6_UT	AN5_UT	AN4_UT	AN3_UT	AN2_UT	AN1_UT	AN0_UT
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0

MC337720

All information provided in this document is subject to legal disclaimers.

© 2024 NXP B.V. All rights reserved.

Table 56. AN_OT_UT_FLT...continued

	Description	Overtemperature detection for ANx – ANx_OT ored is provided in FAULT1_STATUS[AN_OT_FLT]
ANx OT	0	No overtemperature fault detected
AIVOT	1	Overtemperature fault detected on ANx
	Reset condition	POR / Clear on write 0 (ANx_OT is set again on next cyclic conversion or on-demand conversion if overtemperature persists)
	Description	Undertemperature detection for ANx – ANx_UT ored is provided in FAULT1_STATUS[AN_UT_FLT]
ANx UT	0	No undertemperature fault detected
AIN_UI	1	Undertemperature fault detected on ANx
	Reset condition	POR / Clear on write 0 (ANx_UT is set again on next cyclic conversion or on-demand conversion if undertemperature persists)

^[1] w0c: write 0 to clear

11.21 GPIO open short register - GPIO_SHORT_ANx_OPEN_STS

Table 57. GPIO_SHORT_ANx_OPEN_STS

		x_OPEN_S														
\$21	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write		w0c ^[1]		w0c ^[1]												
Read	0	GPIO6_ SH	GPIO5_ SH	GPIO4_ SH	GPIO3_ SH	GPIO2_ SH	GPIO1_ SH	GPIO0_ SH	0	AN6_ OPEN	AN5_ OPEN	AN4_ OPEN	AN3_ OPEN	AN2_ OPEN	AN1_ OPEN	AN0_ OPEN
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	-		n	GPIOx sh	ort detectio	n GPIOx_S	SH ored is p	provided in	FAULT2_S	TATUS[GP	IO_SHOR	T_FLT]				
CDIO _V C	-	0		No short o	letected											
GPIOX_S	п	1		Short dete	ected, pad	sense is dif	ferent from	pad comm	and							
		Reset cor	ndition	POR / Cle	ar on write	0										_
		Description	n	Analog in	outs open le	oad detecti	on. ANx_O	PEN ored i	s provided	in FAULT2	_STATUS[A	AN_OPEN_	FLT]			_
ANI: ODI		0		No open I	oad detecte	ed										
ANX_OPE	Nx_OPEN -	1		Open load	detected of	on Anx										
		Reset cor	ndition	POR / Cle	ar on write	0 (ANx_O	PEN is set	again with	open load o	detect switch	h closed a	nd open loa	d persists)			

^[1] w0c: write 0 to clear

11.22 Current measurement status register – I_STATUS

Table 58. I_STATUS

I_STATUS																
\$22	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write		<u>'</u>	<u>'</u>	<u> </u>		<u>'</u>	<u>'</u>									
Read	PGA_DAC															
Reset	0 0 0 0 0 0 0 0 0 0 0 0 0 0															
	•	Descripti	on	DAC code	e											
DCA DA		00000	000	DAC code	e is initially	all zeros										
PGA_DAC	11111	111	DAC code	e to be prov	ided to the	e PGA (for o	offset cance	ellation), ca	lculated thr	ough an au	itozero pha	se				
1		Reset co	ndition	POR												

11.23 Communication status register - COM_STATUS

Table 59. COM_STATUS

COM_STA	COM_STATUS															
\$23	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write	w0c ^[1]															
Read				COM_ERF	R_COUNT				0	0	0	0	0	0	0	0
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	
COM_ER COUNT																

MC33772C

All information provided in this document is subject to legal disclaimers.

© 2024 NXP B.V. All rights reserved.

Table 59. COM_STATUS...continued

0000000	0 communication errors have been detected
	255 communication errors have been detected. Overflow of counter sets FAULT1_STATUS[COMM_ERR_OVR_FLT]. Count remains at 255 until cleared by controller
Reset condition	POR / Clear on write 0

^[1] w0c: write 0 to clear

11.24 Fault status register 1 - FAULT1_STATUS

Table 6	0. FAI	JLT1 S	TATUS	;												
FAULT1_S				<u> </u>												
\$24	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write	w0c ^[1]	w0c ^[1]	w0c ^[1]	w0c ^[1]	w0c ^[1]	w0c ^[1]	w0c ^[1]	w0c ^[1]	w0c ^[1]	w0c ^[1]	w0c ^[1]	w0c ^[1]				
Read	POR	RESET_ FLT	COM_ ERR_ OVR_ FLT	VPWR_ OV_FLT	VPWR_ LV_FLT	COM_ LOSS_ FLT	COM_ ERR_ FLT	CSB_ WUP_ FLT	GPIO0_ WUP_ FLT	I2C_ ERR_ FLT	IS_OL_ FLT	IS_OC_ FLT	AN_ OT_FLT	AN_ UT_FLT	CT_ OV_FLT	CT_ UV_FL
Reset	1	0**	0*	0*	0*	0**	0*	0	0	0	0	0	0	0	0	0
		oltage condi ay be flipped							of bits ma	rked by a *	may be flip	ped.	'			
		Description	n	Power-On	-Reset indi	cation (PO	R)									
POR		0		No POR												
PUR		1		Device ha	s PORed											
		Reset con	dition	POR / Cle	ar on write	0										
		Description	n	RESET In	dication (no	n-maskab	le)									
		0		No reset												
RESET_FL	_T	1			s been reso		the RESET	pin or by a	write comr	nand settir	g the SYS_	_CFG1[SO	FT_RST] o	r by a comr	nunication	loss or ar
		Reset con	dition	POR / Cle	ar on write	0										
		Description	n	Overflow i	ndicator on	the COM_	STATUS[C	OM_ERR_	COUNT]							
COM ERR	ROVR	0		No error												
FLT _		1		COM_STA	ATUS[COM	_ERR_CO	UNT] went	in overflow								
		Reset con	dition	POR / Cle	ar on write	0										
		Description	n	VPWR ov	ervoltage n	otification ^{[2}	·]									
		0		No overvo	Itage (VPV	/R < VPWF	R(OV_FLAG	G)) detecte	d							
VPWR_OV	/_FLI	1		Overvolta	ge detected	I (VPWR >	VPWR(OV	/_FLAG), ti	ming filtered	d)						
		Reset con	dition	POR / Cle	ar on write	0										
		Description	n	VPWR lov	v-voltage n	otification										

No low-voltage (VPWR > VPWR(LV_FLAG)) detected

An error has been detected during a communication

POR / Clear on write 0

POR / Clear on write 0

POR / Clear on write 0

No wake-up

CBS wake-up notification

CSB wake-up detected

POR / Clear on write 0

GPIO0 wake-up notification

Communication loss detected

Communication error detected

Low-voltage detected (VPWR < VPWR(LV_FLAG), timing filtered)

Ν	1C3	37	720	1

VPWR_LV_FLT

COM_LOSS_FLT

COM_ERR_FLT

CSB_WUP_FLT

GPIO0_WUP_FLT

Reset condition

Reset condition

Reset condition

Reset condition

Description

Description

Description

Description

In Normal mode, each slave device must receive a local message within the programmed period or COM_LOSS_FLT flag is set

Battery cell controller IC

Table 60. FAULT1_STATUS...continued

	0	No wake-up
	1	GPIO0 wake-up detected
	Reset condition	POR / Clear on write 0
	Description	I ² C communication error during the transfer from EEPROM to the IC
I2C ERR FLT	0	No Error
IZO_ERR_FLI	1	Error detected
	Reset condition	POR / Clear on write 0
	Description	ISENSE pins open load detected
IS OL FLT	0	No open load detected
IS_OL_FLI	1	Open load detected in one or both ISENSE pins
	Reset Condition	POR / Clear on write 0
	Description	ISENSE overcurrent detected (Sleep mode only)
IS OC FLT	0	No overcurrent detected
IS_UC_FLI	1	Overcurrent detected from ISENSE inputs
	Reset condition	POR / Clear on write 0
	Description	Analog input overtemperature detection
AN OT FLT	0	No overtemperature detected
AN_OI_FLI	1	Overtemperature detected in one or more of the ANx analog inputs
	Reset condition	POR / Clear on write 0 all AN_OT_UT[ANx_OT] bits
	Description	Analog inputs undertemperature detection ^[2]
AN UT FLT	0	No undertemperature detected
AN_UI_FLI	1	Undertemperature detected in one or more of the ANx analog inputs
	Reset condition	POR / Clear on write 0 all AN_OT_UT[ANx_UT] bits
	Description	Cell terminal overvoltage detection ^[2]
CT OV FLT	0	No overvoltage detected
CI_OV_FLI	1	Overvoltage detected in one or more of the 6 cell terminals
	Reset condition	POR / Clear on write 0 all CELL_OV[CTx_OV] bits
	Description	Cell terminal undervoltage detection
CT UV ELT	0	No undervoltage detected
CT_UV_FLT	1	Undervoltage detection in one or more of the 6 cell terminals
	Reset condition	POR / Clear on write 0 all CELL_UV[CTx_UV] bits

^[1] w0c: write 0 to clear
[2] Ignore if FAULT2_STATUS[VANA_UV_FLT] is set

11.25 Fault status register 2 - FAULT2_STATUS

Table 61. FAULT2_STATUS

FAULT2_	STATUS															
\$25	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write	w0c ^[1]	w0c ^[1]	w0c ^[1]	w0c ^[1]					w0c ^[1]	w0c ^[1]	w0c ^[1]					
Read	VCOM_ OV_FLT	VCOM_ UV_FLT	VANA_ OV_FLT	VANA_ UV_FLT	ADC1_ B_FLT	ADC1_ A_FLT	GND_ LOSS_ FLT	IC_ TSD_ FLT	IDLE_ MODE_ FLT	AN_ OPEN_ FLT	GPIO_ SHORT_ FLT	CB_ SHORT_ FLT	CB_ OPEN_ FLT	OSC_ ERR_ FLT	DED_ ERR_ FLT	FUSE_ ERR_ FLT
Reset	0*	0*	0*	0*	0	0	0*	0	0	0	0	0	0	0*	0*	0**
	g on the vo	-		-					e of bits ma	rked by a	* may be fli	pped.			1	
Values ma	arked ** ma															
		Descriptio	n		ervoltage n		•									
VCOM_O	V_FLT	1			oltage detec		on VCOM	cupply								
		Reset cor	dition		ear on write		OII VCOIVI	supply								
		Description		-	dervoltage		1									
		0	,11		oltage dete											
VCOM_U	V_FLT	1			age has be		d on VCOM	1 eunnly								
		Reset Co	ndition		ear on write		u 011 V 001V	гзирргу								
		Description			ervoltage no											_
		0		1	oltage detec											
VANA_O\	/_FLT	1			ge has bee		on the VAN	NA supply								
		Reset cor	ndition		ar on write											
		Description		-	dervoltage i											
		0			oltage det											
VANA_U\	/_FLT	1			age has be		d on the VA	NA supply	,							
		Reset cor	ndition		ear on write											
		Description	n	ADC1_B	fault notifica	ation ^[2]										
		0		No fault d												
ADC1_B_	_FLT	1		ADC1_B	fault (over o	or undervol	tage has be	en detecte	ed on MEAS	S_VBG_DI	AG_ADC1E	3)				
		Reset cor	ndition	POR / Cle	ar on write	0										
		Description	n	ADC1_A	fault notifica	ation ^[2]										
		0		No fault d	etected											
ADC1_A_	_FLT	1		ADC1_A	fault (over o	r undervol	tage has be	en detecte	ed on MEAS	S_VBG_DI	AG_ADC1A	A)				
		Reset cor	ndition	POR / Cle	ar on write	0										
		Description	n	Loss of gr	ound has b	een detect	ed on DGN	ID or AGNI	D or CGND							
OND LO	00 517	0		No error	-											
GND_LO	55_FLI	1		Loss of gr	ound detec	ted										
		Reset cor	ndition	POR / Cle	ar on write	0										
		Description	n	IC therma	I limitation	notification										
IC TED I	CI T	0		No therma	al limitation	detected										
IC_TSD_I	FLI	1		Thermal I	mitation de	tected										
		Reset cor	ndition	POR / Cle	ar on write	0										
		Description	n	Idle mode	notification	ı										
IDLE_MC	NDE ELT	0		No notific	ation											
IDLL_IVIC	/DL_1 L1	1		The syste	m has trans	sitioned thr	ough idle m	node								
		Reset cor	ndition	POR / Cle	ar on write	0										
		Description	n	Analog in	outs open l	oad detecti	on									
AN_OPEI	N FIT	0		No open I	oad detecte	ed										
, OF EI		1		Open load	d detected i	n one or m	ore of the A	Anx analog	inputs							
		Reset cor	ndition	POR / Cle	ar on write	0 all GPIO	_SHORT_/	AN_OPEN	_FLT[ANx_	OPEN] bits	3					

Battery cell controller IC

Table 61. FAULT2_STATUS...continued

	Description	GPIO short detection
GPIO SHORT FLT	0	No short detected
GFIO_SHORT_FLT	1	Short detected in one or more of the seven GPIOs
	Reset condition	POR / Clear on write 0 all GPIO_SHORT_AN_OPEN_FLT (GPIOx_SH) bits
	Description	Cell balance short-circuit detection
CB SHORT FLT	0	No short-circuit detected
CB_SHORT_FLT	1	On state short-circuit detected in one or more of the 6 cell balancing switches
	Reset condition	POR / Clear on write 0 all CB_SHORT_FLT[CBx_SHORT] bits
	Description	Cell balancing open load detection
CB OPEN FLT	0	No cell balance open load detected
CB_OPEN_FLI	1	Off state open load detected in one or more of the 6 cell balancing switches
	Reset condition	POR / Clear on write 0 all CB_OPEN_FLT[CBx_OPEN] bits
	Description	Low-power oscillator error
OSC ERR FLT	0	No error
OSC_ERR_FLI	1	The low-power oscillator frequency is out of range
	Reset condition	POR / Clear on write 0
	Description	ECC error, double error detection
DED ERR FLT	0	No error
DED_ERR_FLI	1	A double error has been detected in the fuses
	Reset condition	POR / Clear on write 0
	Description	Error in the loading of fuses
FUSE ERR FLT	0	No error
I COL_LIXIC_I LI	1	The lock bit was not set after loading, meaning transfer of the fuse values is aborted

w0c: write 0 to clear Ignore if FAULT2_STATUS[VANA_UV_FLT] is set

11.26 Fault status register 3 - FAULT3_STATUS

Table 62. FAULT3 STATUS

		<u> </u>														
FAULT3_	STATUS															
\$26	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write		w0c ^[1]	w0c ^[1]								w0c ^[1]					
Read	CC_ OVR_ FLT	DIAG_ TO_FLT	VCP_UV	0	0	0	0	0	0	0	EOT_CB6	EOT_CB5	EOT_CB4	EOT_CB3	EOT_CB2	EOT_CB
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
CC_OVR	_FLT	Description	n	Overflow	ndicator or	the COUI	LOMB_CN1	1,2[COUL	OMB_CNT] or CC_NE	S_SAMPLES	3				
0 No error																
		1		COULOM	B_CNT1,2	[COULOM	B_CNT] or	CC_NB_S	AMPLES w	ent in overf	flow					
		Reset cor	ndition	POR / Cle	ar On Writ	e 0 CC_P_	OVF,CC_N	_OVF, SAI	MP_OVF a	nd CC_OV	Т					
DIAG_TO	_FLT	Description	n	Timeout c	f diagnosti	state										
		0		No timeou	ıt											
		1		The syste	m has exite	ed itself fro	m diagnost	ic state afte	er timeout							
		Reset cor	ndition	POR / Cle	ar on write	0										
		Description	n	VCP unde	rvoltage de	etection ^[2]										
\(\(\text{O}\) \(\text{I}\)\(\text{I}\)		0		No under	oltage det	ected										
VCP_UV		1		Undervolt	age detect	ed on VCP	supply									
		Reset cor	ndition	POR / Cle	ar on write	0										
EOT_CBx	(Description	n	End of tim	e cell bala	ncing notifi	ication – ind	licates whe	n a cell bal	ance timer	has expired	and driver	has been	shutoff		
		0		Cell balar	ce timer ha	as not time	d out									
		1		Cell balar	ce timer ha	as timed ou	ut									
		Reset cor	ndition	POR / Cle	ar on write	0										

^[1] w0c: write 0 to clear

11.27 Fault mask register 1 - FAULT_MASK1

The FAULT_MASK1 register allows the user to selectively mask fault bits associated to the FAULT1_STATUS register. Masking a certain fault bit has the effect of preventing this bit from activating the FAULT output pin.

Table 63. FAULT_MASK1

FAULT_N	IASK1															
\$27	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write				MASK_	MASK_	MASK_	MASK_	MASK_	MASK_	MASK_	MASK_	MASK_	MASK_	MASK_	MASK_	MASK_
Read	0	0	0	12_F	11_F	10_F	9_F	8_F	7_F	6_F	5_F	4_F	3_F	2_F	1_F	0_F
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
		Description	n	Prevent th	e correspo	nding flags	in FAULT1	_STATUS	to activate t	he FAULT	pin					
MASK x	_	0		The flag in	position x	activates th	ne FAULT p	oin								
IVIAGR_X_	.г	1		No activat	ion											
		Reset con	dition	POR												

11.28 Fault mask register 2 – FAULT_MASK2

The FAULT_MASK2 register allows the user to selectively mask fault bits associated to the FAULT2_STATUS register. Masking a certain fault bit has the effect of preventing this bit from activating the FAULT output pin.

^[1] woc. write o to clear [2] Ignore if FAULT2_STATUS[VANA_UV_FLT] is set

Battery cell controller IC

Table 64. FAULT_MASK2

FAULT_N	IASK2															
\$28	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write	MASK_	MASK_	MASK_	MASK_	MASK_	MASK_	MASK_			MASK_	MASK_	MASK_	MASK_	MASK_	MASK_	MASK_
Read	15_F	14_F	13_F	12_F	11_F	10_F	9_F	0	0	6_F	5_F	4_F	3_F	2_F	1_F	0_F
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
		Descriptio	n	Prevent th	e correspo	nding flags	in FAULT2	_STATUS	to activate	the FAULT	pin					
MASK	_	0		The flag in	position x	activates th	ne FAULT p	oin								
IVIAGR_X_	MASK_x_F	1		No activat	ion											
		Reset con	dition	POR												

11.29 Fault mask register 3 – FAULT_MASK3

The FAULT_MASK3 register allows the user to selectively mask fault bits associated to the FAULT3_STATUS register. Masking a certain fault bit has the effect of preventing this bit from activating the FAULT output pin.

Table 65. FAULT MASK3

FAULT_N	IASK3															
\$29	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write	MASK_	MASK_	MASK_								MASK_	MASK_	MASK_	MASK_	MASK_	MASK_
Read	15_F	14_F	13_F	0	0	0	0	0	0	0	5_F	4_F	3_F	2_F	1_F	0_F
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
		Descriptio	n	Prevent th	ne correspo	nding flags	in FAULT3	_STATUS	to activate	the FAULT	pin				•	
MASK x	_	0		The flag in	n position (x) activates	the FAULT	pin								
IVIAGR_X_	<u>.</u> F	1		No activa	tion											
		Reset con	dition	POR												

11.30 Wake-up mask register 1 - WAKEUP_MASK1

The WAKEUP_MASK1 register disables wake-up events related to several FAULT1_STATUS fault bits. If a certain bit contained in the latter register is not masked by the corresponding bit of the former register, the IC transitions from Sleep mode to Normal mode.

Table 66. WAKEUP_MASK1

WAKEL	JP_MASI	K1														
\$2A	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write				MASK_	MASK_				MASK_			MASK_	MASK_	MASK_	MASK_	MASK_
Read	0	0	0	12_F	11_F	0	0	0	7_F	0	0	4_F	3_F	2_F	1_F	0_F
Reset	0	0	0	1	1	0	0	0	1	0	0	1	1	1	1	1
		Descrip	tion	Prevent the c	orresponding	flags in F.	AULT1_S	STATUS to w	ake-up the o	levice						
MASK_	v E	0		The flag in po	sition (x) wak	es the de	vice up, v	when active								
IVIAGR_	х_г	1		No wake-up i	s possible by	this sourc	е									
		Reset c	ondition	POR												

Battery cell controller IC

11.31 Wake-up mask register 2 – WAKEUP_MASK2

The WAKEUP_MASK2 register disables wake-up events related to several FAULT2_STATUS fault bits. If a certain bit contained in the latter register is not masked by the corresponding bit of the former register, the IC transitions from Sleep mode to Normal mode.

Table 67. WAKEUP MASK2

WAKEUP	_MASK2															
\$2B	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write	MASK_	MASK_	MASK_	MASK_	MASK_	MASK_	MASK_	MASK_			MASK_	MASK_		MASK_	MASK_	
Read								8_F	0	0	5_F	4_F	0	2_F	1_F	0
Reset 1 1 1 1 1 1 1 0							0	0	1	1	0	1	1	0		
	Description		n	Prevent th	e correspo	nding flags	in FAULT2	_STATUS	to wake-up	the device						
MACK	_	0		The flag ir	position (x	() wakes th	e device, w	hen active								
WASK_X_	<u>.</u> F	1		No wake-ı	up is possib	ole by this s	ource									
	MASK_x_F	Reset con	dition	POR												

11.32 Wake-up mask register 3 – WAKEUP_MASK3

The WAKEUP_MASK3 register disables wake-up events related to several FAULT3_STATUS fault bits. If a certain bit contained in the latter register is not masked by the corresponding bit of the former register, the IC transitions from Sleep mode to Normal mode.

Table 68. WAKEUP MASK3

WAKEL	IP_MASK3															
\$2C	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write	MASK 15 F		MASK 13 F								MASK 5 F	MASK 4 F	MASK 3 F	MASK 2 F	MACK 1 F	MASK 0 F
Read	WIASK_15_F	0	WASK_IS_F	0	0	0	0	0	0	0	WIASK_5_F	IVIASK_4_F	WASK_3_F	WASK_Z_F	IVIASK_I_F	WASK_U_F
Reset	1 0 1		1	0	0	0	0	0	0	0	1	1	1	1	1	1
		Descrip	tion	Prevent	the corre	espondin	g flags	in FAU	LT3_S	TATUS	to wake-up th	e device				
MACK		0		The flag	in positi	on (x) wa	akes the	e devic	e, whe	n active	;					
MASK_	X_F	1		No wak	e-up is p	ossible b	y this s	ource								
		Reset c	ondition	POR												

11.33 Coulomb count number of samples register - CC_NB_SAMPLES

The CC_NB_SAMPLES register contains the 16-bit value, which represents the number of samples accumulated in the coulomb counter at the moment of copying its value to the COULOMB_CNT registers.

Table 69. CC_NB_SAMPLES

CC_NB_S	SAMPLES															
\$2D	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write																
Read	CC_NB_SAMPLES															
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
CC NB 9	CAMPLES	Description	n	Number o	f samples a	accumulate	d for the co	ulomb cou	nt value							
CC_NB_S	NB_SAMPLES Reset condition			POR / AD	C_CFG[CC	_RST]										

11.34 Coulomb count register - COULOMB CNT

The COULOMB_CNT register contains the current 32-bit value of the accumulated current samples. Data representation is signed two's complement, with V_{2RES} resolution. Division of Δ COULOMB_CNT by Δ CC NB SAMPLES provides the average current, where the operator Δ denotes the variation over two

MC33772C

Battery cell controller IC

different readings of a state. Subsequent multiplication by the corresponding elapsed time Δt provides the charge flowed out/in of the battery.

Table 70. COULOMB_CNT1

COULON	IB_CNT1															
\$2E	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write																
Read		COULOMB_CNT_MSB														
Reset 0 0 0 0 0 0 0 0 0					0	0	0	0	0	0	0	0	0			
COULOM	IB_CNT_	Descriptio	n	Coulomb	counting ac	cumulator										
MSB		Reset con	ndition	POR / AD	C_CFG[CC	_RST]										

Table 71. COULOMB CNT2

COUL	ОМВ_С	CNT2														
\$2F	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write																
Read	COULOMB_CNT_LSB															
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
COUL	OMB	Descri	ption	Coulor	nb cour	nting ac	cumula	itor								
CNT_L	_	Reset conditi	on	POR /	ADC_C	FG[CC	_RST]									

11.35 Current measurement registers – MEAS_ISENSE1 and MEAS_ISENSE2

The MEAS_ISENSEx registers contain the signed two's complement value of the battery current measured on demand.

Table 72. MEAS ISENSE1

ENSE1															
bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
		<u>'</u>	<u>'</u>		<u>'</u>	<u>'</u>			<u>'</u>	<u>'</u>	•	·			·
DATA_ RDY							N	1EAS_I _M	ISB						
0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Description	on							is updated.	The DATA	_RDY bit is	cleared wh	nen a requ	est to conv	ert is
Υ	0		A new se	quence of	conversion	s is currentl	y running								
	1		A data is	available ir	n MEAS_IS	ENSE1									
MEAS_I_MSB	Reset cor	ndition	POR												
	Description	n	ISENSE \	value, com	pensated ir	n gain and t	emp, signe	d							
	Reset cor	ndition	POR												
	bit 15 DATA_RDY 0	DATA RDY	DATA_RDY	DATA_RDY	DATA_RDY	DATA_ RDY	DATA_ RDY	DATA_ RDY Description Description A data is available in MEAS_ISENSE1 Reset condition Description Description Reset condition Description Description A data is available in MEAS_ISENSE1 Reset condition Description Description Reset condition Description Description Reset condition Description Reset condition Description Description	ENSE1 bit 15 bit 14 bit 13 bit 12 bit 11 bit 10 bit 9 bit 8 bit 7	ENSE1 bit 15 bit 14 bit 13 bit 12 bit 11 bit 10 bit 9 bit 8 bit 7 bit 6 DATA_RDY	ENSE1 DATA_RDY	DATA_ RDY	ENSE1 bit 15 bit 14 bit 13 bit 12 bit 11 bit 10 bit 9 bit 8 bit 7 bit 6 bit 5 bit 4 bit 3 DATA_RDY MEAS_I_MSB 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0	ENSE1 bit 15 bit 14 bit 13 bit 12 bit 11 bit 10 bit 9 bit 8 bit 7 bit 6 bit 5 bit 4 bit 3 bit 2	ENSE1 bit 15 bit 14 bit 13 bit 12 bit 11 bit 10 bit 9 bit 8 bit 7 bit 6 bit 5 bit 4 bit 3 bit 2 bit 1

Battery cell controller IC

Table 73. MEAS_ISENSE2

MEAS_IS	ENSE2															
\$31	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write								·	w0c ^[1]	w0c ^[1]						
Read	DATA_ RDY	0	0	0	0	0	PGA_	_GAIN	ADC2_ SAT	PGA_ GCHANGE	0	0		MEA	S_I_LSB	
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	•	Description	on				sion is comp C or GPIO2			s updated.	The DATA_	RDY bit is	cleared w	hen a requ	est to conve	ert is
DATA_RD	Υ	0		A new see	quence of o	conversions	s is currentl	y running								
		1		Data is av	ailable in N	MEAS_ISE	NSE2									
		Reset cor	ndition	POR												
		Description	on	Report the	e current ga	ain of the A	ammable ga	ain amplifie	r (automati	cally settle	d or not)					
		0 0		4												
PGA GAI	INI	0 1		16												
rga_gai	IIN	1 0		64												
		1 1		256												
		Reset cor	ndition	POR												
		Description	on	ADC2 sat	uration info	rmation										
ADC2 SA	\T	0		No satura	tion reporte	ed										
ADC2_3/	NI.	1		ADC2 has	s saturated	during the	ISENSE or	n-demand c	onversion							
		Reset cor	ndition	POR / Cle	ear on write	0										
		Description	on	PGA gain	change inf	formation d	luring ISEN	SE on-dem	and conve	rsion						
PGA GCI	HANGE	0		No gain c	hange duri	ng ISENSE	on-deman	d measure	ment; resul	t is accurate	Э					
1 GA_GG	IIANOL	1		The PGA	gain has cl	hanged be	tween the to	wo chopped	d measurer	nents						
		Reset cor	ndition	POR / Cle	ear on write	0										
MEAS I	LSR	Description	on	ISENSE V	alue, comp	ensated ir	n gain and te	emp, signed	d							
IVILAG_I _	_LOD	Reset cor	ndition	POR												

^[1] w0c: write 0 to clear

11.36 Measurement registers - MEAS_xxxx

The MEAS_xxxx registers contain the measured values as a result of on-demand conversions. Note that the cyclic conversions leave no trace in these registers, as they are only used to update the OV/UV/OT/UT flags and other status information.

Table 74. MEAS_xxxx

MEAS_xx	xxx															
\$32 and \$3B to \$4A	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write						•		1	•					•		
Read	DATA_ RDY								MEAS_xxx	κx						
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
		Descript	ion				sion is com C or GPIO2			is updated	The DATA	_RDY bit is	cleared wh	nen a reque	est to conve	ert is
DATA RE	ΟY	0		A new se	equence of	conversion	ns is current	ly running								
_		1		A data is	available ii	n MEAS_x	xxx									
		Reset co	ndition	POR												
MEAG		Descript	ion	Value is	unsigned, r	esolution is	s V _{CT_ANx_R}	ES indepen	dently on th	ne selected	I resolution	of ADC_CI	-G			
WEAS_XX	EAS_xxxx	Reset co	ndition	POR												

Battery cell controller IC

11.37 Overvoltage undervoltage threshold register - TH_ALL_CT

Resolution for OV threshold and UV threshold are, respectively, V_{CTOV(TH)} and V_{CTUV(TH)}.

Table 75. TH_ALL_CT

TH_ALL_																
\$4B	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write				ALL CT	OV TH	'		'				ALL CT	UV TH			'
Read				ALL_C1	_0v_111							ALL_C1	_0v_111			
Reset	1	1	0	1	0	1	1	1	1	0	0	0	0	0	0	0
		Description	on	Overvolta	ge thresho	ld setting fo	or all cell ter	rminals. Er	nabled throu	ıgh register	OV_UV_E	N				•
ALL_CT_	OV_TH	11010111	1	Default ov	vervoltage t	hreshold s	et to 4.2 V									
		Reset cor	ndition	POR												
		Description	n	Undervolt	age thresh	old setting	for all cell te	erminals. E	nabled thro	ough registe	er OV_UV_	EN				
ALL_CT_	UV_TH	10000000)	Default ur	ndervoltage	threshold	set to 2.5 V	′								
		Reset cor	ndition	POR												

11.38 Overvoltage undervoltage threshold register - TH_CTx

Table 76. TH_CTx

TH_CTx		_														
\$4C to \$59	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write				CTv (OV TH							CTv I	JV TH			
Read				01%_0	JV_111							017_0	5v_111			
Reset	1	1 1 0 1 0 1 1 1 1 0 0 0 0 0 0 0														
	Description Overvoltage threshold setting for individual cell terminals. OV_UV EN] bit must be logic 1 to use TH_CTx register as threshold										IMON_OV_	TH] bit mu	st be logic	0 and OV_	UV_EN[CT	x_OVUV_
CTx_OV_	_TH	11010111	1	Default ov	ervoltage t	threshold s	et to 4.2 V									
		Reset cor	ndition	POR												
		Description	on				for individua to use TH_0				MMON_UV	_TH] bit m	ust be logic	0 and OV	_UV_EN[C	Tx_
CTx_UV_	_TH	10000000)	Default ur	ndervoltage	threshold	set to 2.5 V	,								
		Reset cor	ndition	POR												

11.39 Overtemperature, undertemperature threshold registers – TH_ANx_OT, TH_ANx_UT

Registers TH_ANx_OT and TH_ANx_UT contain the individually programmed overtemperature and undertemperature value for each analog input.

Table 77. TH_ANx_OT

TH_ANx_	_от																	
\$5A to \$60	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0		
Write											ANIV	OT TU						
Read	0	0	0	0	0	0	ANx_OT_TH											
Reset	0	0	0	0	0	0	0	0	1	1	1	0	1	1	0	1		
		Description	on	Overtemp	erature thr	eshold sett	ing for anal	og input x										
ANx_OT_	_TH	00111011	101	Overtemp	erature de	fault set to	ault set to 1.16 V											
		Reset cor	ndition	POR														

Battery cell controller IC

Table 78. TH_ANx_UT

TH_ANx_	_UT																
\$61 to \$67	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0	
Write							ANx_UT_TH										
Read	0	0	0	0	0	O ANX_UI_IH											
Reset	0	0	0	0	0	0	1	1	0	0	0	0	1	1	1	0	
		Description	on	Undertem	perature th	reshold set	ting for ana	log input x				•					
ANx_UT_TH 1100001110 Undertemperature default set to 3.82 V																	
Reset condition POR																	

11.40 Overcurrent threshold register - TH_ISENSE_OC

Registers TH_ISENSE_OC contains the programmed overcurrent threshold in sleep mode.

Table 79. TH_ISENSE_OC

TH_ISEN	SE_OC															
\$68	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write								•		TH ISE	NSE OC		•			
Read	0	0	0	0	TH_ISENSE_OC											
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
TH ISEN	SE 00	Description Sleep mode ISENSE overcurrent threshold, unsigned. Resolution is 1.2 µV/LSB														
IH_ISEN	3E_00	Reset cor	ndition	POR												

11.41 Over coulomb counter threshold registers - TH_COULOMB_CNT

The coulomb counter threshold in sleep mode is given by the following two registers.

Table 80. TH_COULOMB_CNT_MSB

TH_COU	ILOMB_CI	NT_MSB														
\$69	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write		TH COULOMB CNT MSB														
Read	1	TH_COULOMB_CNT_MSB														
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
TH_COU	JLOMB	Description	on	Over cou	lomb count	ing accumu	ulator threst	nold (MSB)	•							
CNT_MS		Reset cor	ndition	POR												

Table 81. TH_COULOMB_CNT_LSB

TH_COU	LOMB_CN	T_LSB														
\$6A	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write							TL	L COLILON	IB CNT L	CD.						
Read							111	I_COULON	IB_CINT_L	36						
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
TH_COU	LOMB_	Descriptio	n	Over coul	omb counti	ng accumu	lator thresh	old (LSB).	Resolution	is V _{2RES}						
CNT_LSE	3	Reset con	dition	POR												

11.42 Silicon revision register – SILICON_REV

Table 82. SILICON REV

SILICON																
\$6B	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write																
Read	0	0	0	0	0	0	0	0	0		F	REV			MREV	
Reset	0	0	0	0	0	0	0	0	0	F	F	F	F	М	М	М
		Descripti	on	Full masl	k revision				•							
		0001		Pass 1.x												
FREV	-	0010		Pass 2.x												
		Reset co	ndition	POR												
		Descripti	on	Metal ma	sk revision											
		000		Pass y.0												
MREV	MREV 0	001		Pass y.1												
		Reset co	ndition	POR												

11.43 EEPROM communication register - EEPROM_CTRL

Table 83. EEPROM CTRL

EEPROM	_CTRL															
\$6C	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write	R/W		1	EEPROM	_ADD						1	DATA_T	 D_WRITE			
Read	BUSY	ERROR	EE_PRESENT	0	0	0	0	0				READ	_DATA			
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
		Description	,	Read/wri	te bit, dire	ects the M	C33772C	to read or	write fron	n EEPRO	М					
R/W		0		Write												
FC/VV		1		Read												
		Reset condi	ition	POR												
FEDDOM	ADD	Description		EEPRON	/ address	to read o	r write									
EEPROM	_ADD	Reset condi	ition	POR												
DATA TO	WOITE	Description		Data to b	e written	into the El	EPROM									
DAIA_IO	_WKIIE	Reset condi	ition	POR												
		Description		Busy bit												
BUSY		0		Indicates	the IC ha	as complet	ted the EE	PROM re	ad or write	e operatio	n					
BU31		1		Indicates	the IC is	in the pro	cess of pe	rforming t	he EEPR	OM read o	r write op	eration				
		Reset condi	ition	POR												
		Description		EEPRON	/I commur	nication er	ror bit.									
ERROR		0		No error	occurred	during the	communi	cation to l	EEPROM							
LIXIXOIX		1		An error	occurred	during the	communi	cation to I	EPROM							
		Reset condi	ition	POR												
		Description		EEPRON	/I detectio	n										
EE_PRES	SENT	0		No EEPF	ROM dete	cted										
LL_I INEC	JEIVI	1		EEPRON	/I has bee	n detected	d and pres	sent								
		Reset condi	ition	POR												
READ_DA	ΔΤΔ	Description		Data rea	d in the E	EPROM a	t address	given by I	EEPROM	_ADD						
NEAD_DA	1171	Reset condi	ition	POR												

Battery cell controller IC

11.44 ECC signature 1 register

Table 84. DED_ENCODE1

DED_ENG	CODE1															
\$6D	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write																
Read		DED_HAMMING_COUT1_23_8														
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
DED_HAI	AMMING_ Description Reports the 16 MSBits to encode in the fuse matrix (ECC)															
COUT1_2	23_8	Reset con	ndition	POR	-											

11.45 ECC signature 2 register

Table 85. DED_ENCODE2

DED_ENG	CODE2															
\$6E	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write																
Read			DED	_HAMMING	G_COUT_1	_7_0	0	0	0	0	0	0	0	0		
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
DED_HAM	MMING_	Descriptio	n	Report the	16 LSBits	to encode	in the fuse	matrix (EC	C)							
COUT_1_	7_0	Reset con	dition	POR												

11.46 FUSE mirror and data control

Table 86. FUSE MIRROR DATA

FUSE_M	IRROR_DA															
\$6F	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write								FMR	DATA							
Read	1							LIVIK_	DAIA							
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
EMD DA	Description Fuse mirror data to read or write															
FMR_DA	IIA	Reset cor	ndition	POR												

Table 87. FUSE_MIRROR_CNTL

FUSE_M	IRROR_CN	ITL														
\$70	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write	w0c ^[1]												FSTM		FST	'
Read	SEC_ ERR_ FLT	0	0			FMR_ADD	R		0	0	0	0	0		FST_ST	
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
		Description	on	ECC error	r, single err	or correction	on				<u>'</u>					
SEC EDI	<u> </u>	0		No error												
SEC_ERI	K_FLI	1		A single e	rror has be	en detecte	d and corre	ected. The	IC is usab	le, must no	be conside	ered defective	ve			
		Reset cor	ndition	POR / Cle	ar on write	0										
EMB AD	DD	Description	on	Fuse mirr	or register	address										
FMR_AD	DK	Reset cor	ndition	POR												
		Description	on	Fuse state	e write mas	k. This bit	controls the	write acc	ess to the	FST[2:0] bit	s					
ГСТМ		0		Writing in	FST bits h	as no effec	t									
FSTM		1		FST bits a	are unlocke	d for writing	g									
		Reset cor	ndition	POR												

Battery cell controller IC

Table 87. FUSE_MIRROR_CNTL...continued

	Description	Fuse state control, write to this register controls the switching of the fuse state machine. Read in this register enables tracing the current state
FST	0 0 0	Refer to Mirror memory access for bit description
	Reset condition	POR
	Description	Fuse state control. Read in this register enables to trace the current state
FST_ST	0 0 0	Refer to Mirror memory access for bit description
	Reset condition	POR

^[1] w0c: write 0 to clear

11.47 Reserved

Table 88. RESERVED

Reserved	i															
\$00, \$12 to \$19, \$33 to \$3A, \$4C to \$53, \$71 to \$7F	bit 15	bit 14	bit 13	bit 12	bit 11	bit 10	bit 9	bit 8	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
Write Read								do not	change							
Reset	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0

11.48 Fuse bank

Table 89. FUSE_BANK

Bank address	Data															
	D15	D14	D13	D12	D11	D10	D9	D8	D7	D6	D5	D4	D3	D2	D1	D0
\$00	GCF_cold_c5					'	GCF_room_c5									
\$01	GCF_cold_c3					GCF_room_c3										
\$02	GCF_hot_c5					GCF_room_c1										
\$03	hot_c6vs5 [2] GCF_hot_i4						GCF_hot_i256					GCF_cold_i256				
\$04	hot_c6vs5 [1] GCF_cold_			CF_cold_i	4 GCF			F_hot_i64				GCF_cold_i64				
\$05	hot_c6vs5 [0] GCF_ANx_ra			itio	GCF_hot_i16				GCF_cold_i16							
\$06	room_c2vs1			cold_c2vs1				GCF_hot_c1								
\$07	GCF_lcTemp			hot_c2vs1				GCF_cold_c1								
\$08	room_c6vs5 cold_c6vs5			hot_c4vs3 cold_			c4vs3	rs3 GCF_stack								
\$09	GCF_cold_Vbgtj2						GCF_i256									
\$0A	GCF_cold_Vbgtj1						GCF_i64									
\$0B	GCF_hot_Vbgtj2					GCF_i16										
\$0C	GCF_hot_Vbgtj1					_	GCF_i4									
\$0D	GCF_room_Vbgtj2					_	GCF_room_Vbgtj1									
\$0E	DED_ENCODE2						GCF_hot_c3 room_c4vs3				c4vs3					
\$0F		DED_ENCODE1														
\$10		Traceability														
\$11		Traceability														
\$12	Reserved							Traceat	oility							

Battery cell controller IC

12 Safety

12.1 Safety features

MC33772C was developed as a Safety Element out of Context (SEooC). All the assumptions of use taken into account are described in the Safety Manual.

MC33772C has been developed to be ASIL-C Qualified. Nevertheless, the MC33772C can be employed within systems performing up to ASIL-D functions, because the MC33772C can support to achieve the corresponding ISO 26262 HW architectural metrics. This holds true only if the system integrator uses all safety mechanisms recommended in the Safety Manual, under the stated conditions of use and the fulfillment of the assumed general and specific requirements stated therein.

Diagnostics and safety features of the device are not described in the present document. To know about them, the user is referred to the MC33772C Safety Manual, whose information content is essential for any safety related application.

13 Typical applications

13.1 Introduction

NXP Semiconductors has developed a battery cell controller IC supporting both centralized and distributed battery management architectures. Centralized battery monitoring systems contain a controller module sensing individual differential cell voltages through a wiring harness. Distributed systems locate monitoring devices close to the lithium-ion batteries and use a communication interface to transfer data to the main controller MCU.

There are significant advantages to using transformers for isolation and communication. The most obvious benefit of the pulse transformers is the high degree of voltage isolation. Transformers specified in this document are automotive qualified and rated at 3750 Vrms. Using pulse transformers allow the NXP battery management system to achieve communication rates of 2.0 Mbit/s with very low radiated emissions.

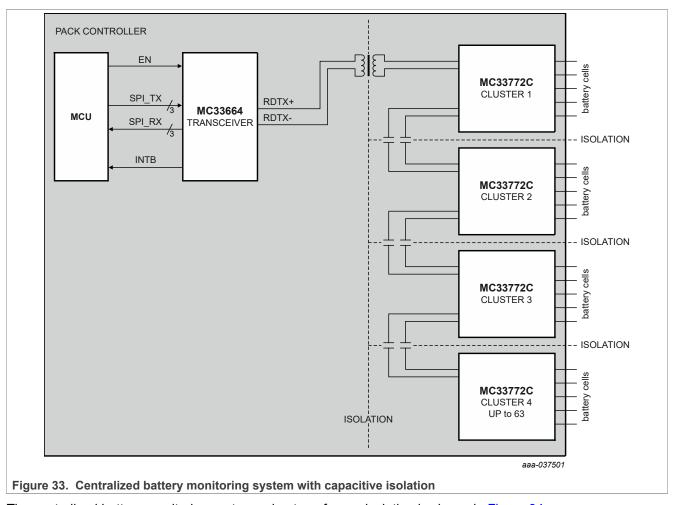
An added benefit to the transformer daisy chain network is the ability to loop the network back to the pack controller. This feature allows the user to verify communication to each node in the daisy chain.

13.1.1 Centralized battery management system

A centralized system is comprised of a single transformer driver with a transformer or capacitive isolation between each battery cell controller IC.

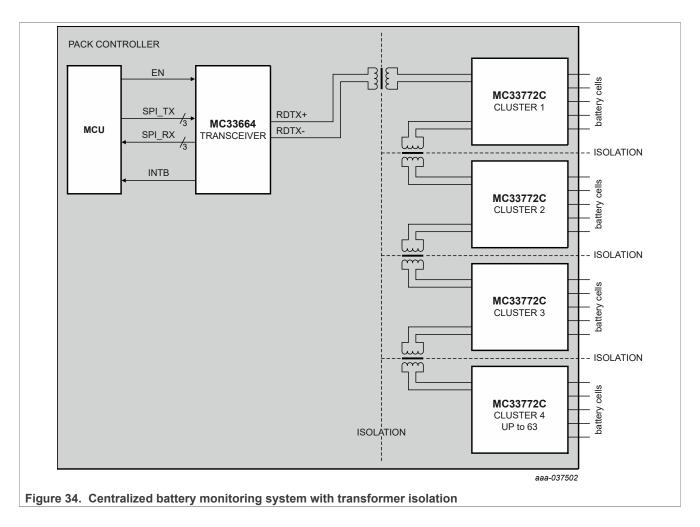
The centralized battery monitoring system using capacitive isolation is shown in Figure 33.

Battery cell controller IC



The centralized battery monitoring system using transformer isolation is shown in Figure 34

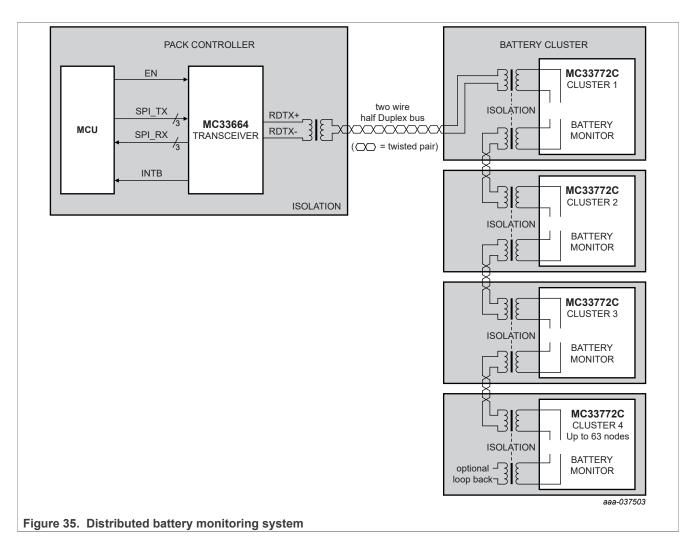
Battery cell controller IC



13.1.2 Distributed battery management system

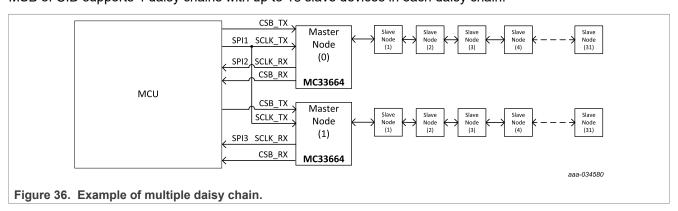
The distributed battery management solution is identical to the centralized system with an additional transformer and daisy chain cable in the pack controller and between each node.

Battery cell controller IC



13.1.3 Multiple daisy chain

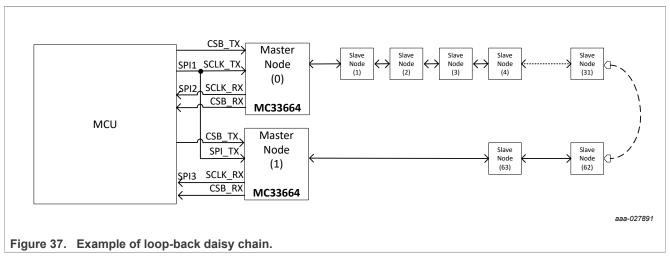
In a distributed system, the MC33772C ICs can be connected in multiple daisy chains. The number of daisy chains supported by the MC33772C IC is configurable with the MSB of the INIT[CID] register. Using one bit MSB of CID supports two daisy chains with up to 31 slave devices in each daisy chain. Similarly, using two bit MSB of CID supports 4 daisy chains with up to 15 slave devices in each daisy chain.



Battery cell controller IC

13.1.4 Loop-Back daisy chain

In a distributed system, the MC33772C IC can also support a loop-back daisy chain with two master nodes connected at two SPI ports of the MCU. The slave devices are connected at each end of the master nodes as shown in the figure.



Note: In the case of a loop-back daisy chain configuration, the MCU shall use only one master node at a time for communicating with the MC33772C IC.

Note: If multiple daisy chains are used in case of loop-back daisy chain communication, then two master nodes forming one complete loop are to be assigned with one daisy chain address.

13.2 MC33772C External Components

This section provides information about recommended external components and how to select them.

13.2.1 Cell terminal filters

Figure 38 and Figure 42 show the recommended second order low-pass filters for cell voltages.

Battery cell controller IC

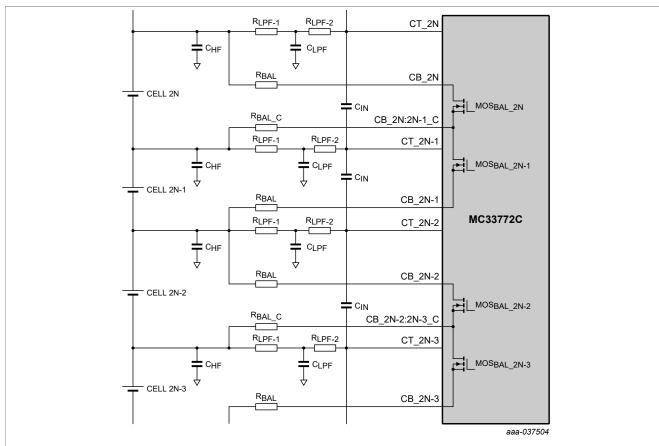


Figure 38. Second order cell terminal filters and cell balancing resistors (internal cell balancing MOSFETs are shown for clarity)

Table 90. CT filter components

ID	Value	Units	Comments
C _{HF}	0.047	μF	Value used and tested at NXP Semiconductors to withstand ESD gun and hot plug
R _{LPF-1}	3	kΩ	Value used and tested to withstand hot plug at NXP. Low-pass filter resistor R_{LPF-1} together with C_{LPF} determine the filter cut-off frequency. This value must not be changed. Component tolerance depends on the wanted accuracy for the bandwidth. See <u>Equation (1)</u> and <u>Equation (2)</u>
C _{LPF}	0.1	μF	This capacitance value together with R _{LPF-1} provides 530 Hz cut-off frequency. Value used and tested to withstand hot plug at NXP. Component tolerance depends on the wanted accuracy for the bandwidth. See Equation (2)
R _{LPF-2}	2	kΩ	Value used and tested to withstand hot plug at NXP. This value must not be changed. No special requirement for the tolerance of this component.
C _{IN}	0.01	μF	Value used and tested to withstand hot plug at NXP. This value must not be changed. No special requirement for the tolerance of this component
R _{BAL}	Х	Ω	Any value is possible, as long as the cell balance current does not exceed 300 mA
R _{BAL_C}	R _{BAL} /5	Ω	Maximum value

Using the arrangement shown in Figure 38, the filter cut-off frequency in Hz, depending on the measurement time constant τ , is given by the following formula.

Battery cell controller IC

$$f_{cut} = 1/(2\pi\tau) \tag{1}$$

$$\tau = R_{LPF-1}C_{LPF} \tag{2}$$

For noisy applications, if the CTREF voltage cannot be kept within the limits described in <u>Table 9</u> footnote <u>6</u>, a setup of dual anti-parallel Schottky diodes can be added between the CTREF battery connector pin and the module ground to limit the voltage drop amplitude in transient. These diodes should be placed close to the corresponding Rlpf-1 resistor (CT_REF pin low pass filter).

13.2.2 Unused cells

If the cluster has less than the maximum number of cells, the usage of cell terminal pins CTx and cell balancing pins CBx has to satisfy some constraints. Each external LPF block is masked as shown in <u>Figure 39</u>, to simplify diagrams representation. A minimum of three cells must be used. At least cells connected to CT_REF/CT1, CT1/CT2 and CT5/CT6. Unused cells must start with CT3. Stacked cells arrangements from 3 to 6 cells are described in <u>Table 91</u>.

Note: For more information, refer to AN12536.

Table 91. Stacked cells

MC33772	Stacked cells					
Cell	6	5	4	3		
1	CT_REF/CT1	CT_REF/CT1	CT_REF/CT1	CT_REF/CT1		
2	CT1/CT2	CT1/CT2	CT1/CT2	CT1/CT2		
3	CT2/CT3	CT3/CT4	CT4/CT5	CT5/CT6		
4	CT3/CT4	CT4/CT5	CT5/CT6	_		
5	CT4/CT5	CT5/CT6	_	_		
6	CT5/CT6	_	_	_		

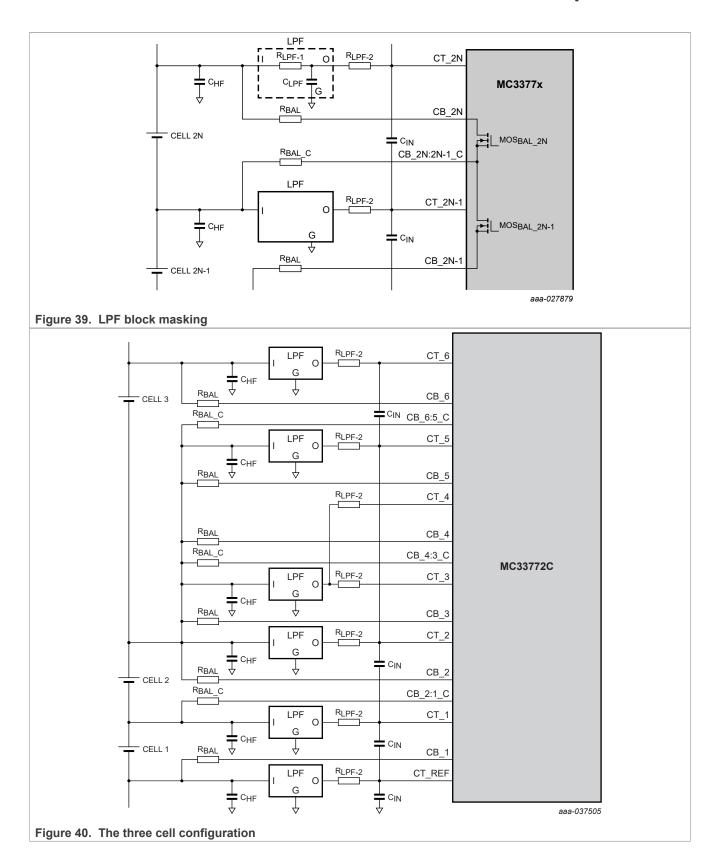
Note:

- CT3 is always populated with the full Low Pass Filter
- Other pins that are not used are shorted directly to CT3

As a general rule, unused CTx have to be terminated to the positive of the cell connected to CT1/CT2. This is also valid for 3 to 4 channels version of MC33772C. As shown, several external components may be removed. Cell balancing resistors (RBAL) of unused cells are to be mounted and terminated at the positive terminal of cell 2. Resistors for hot plug protection RLPF-2 must also be mounted.

Configuration with a number of cells 3, 4 or 5 leads to an application diagram analogous to Figure 40.

Battery cell controller IC



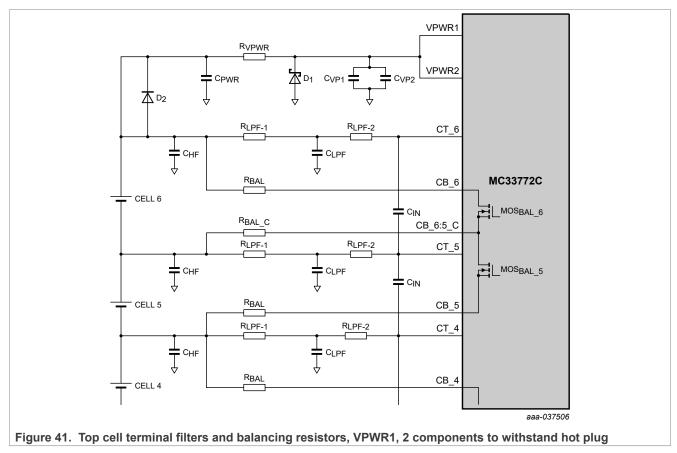
13.2.3 Hot plug protection

The VPWR line, shown in Figure 41, must be protected by a serial resistor in order to limit the inrush current and a parallel capacitor to filter fast voltage variation. A higher value of R_{VPWR} provides better protection. The drawback of higher R_{VPWR} is higher voltage drop. The minimum battery voltage (V_{BAT}) supplying the device through the R_{vpwr} resistor is then equal to Equation (12). As the stack voltage is measured across VPWR1, 2 pins and ground, stack measurement is affected by such voltage drop. Furthermore, voltage drops higher than V_{VPWR} CT have a negative impact on cell measurement accuracy.

$$\min(V_{\text{BAT}}) = \max(V_{\text{PWR}(\text{UV_POR})} + R_{\text{VpWr}} * \left[\max(I_{\text{VPWR}(\text{TPL_TX})}) + \max(I_{\text{LIM_VCOM}(\text{OC})}) + \max(I_{\text{LIM_VANA}(\text{OC})}) \right] \right)$$
(12)

In order to withstand hot plug, it is mandatory to use Zener diodes as shown in Figure 41 close to the VPWR line. In general, all components, whose values are given in Table 92, are mandatory to protect the IC when a connection is made to the battery pack. Changing the value of any external components listed in Table 92 may result in serious IC damage during the connection to the battery pack. Capability of the device to sustain random connection to live voltage for pins VPWRx, CT_x, CB_x, CTREF, GND, ISENSE+ and ISENSE- has been extensively evaluated. Nevertheless, the total number of random combinations related to those pins cannot be entirely tested. Therefore, despite all engineering efforts performed by NXP, it is the responsibility of the system provider to ensure safe connection to the battery pack.

Furthermore, it is the responsibility of the system provider to manage the risk of short circuits on any external components connected to the IC, including external low-pass filters. A short-circuit on the pins connected to the battery can lead to high current flowing through the IC, causing a thermal event on the PCB. The system provider must employ common practices, such as fuse protection on the VPWR line, series of capacitors on the CT pins, appropriate power rating for external resistors, or any other appropriate measure capable to mitigate hazards.



Battery cell controller IC

Table 92. Components to avoid hot plug issues

ID	Value	Units	Comments
D ₂	1	Α	To withstand hot plug when VPWR1/2 and CT_6 are set on different connector lines to connect to upper cell of the monitored cell stack, use specified forward current, e.g., PMEG10010ELR
D ₁	39	V	To protect the IC against transient overvoltage, use the specified Zener voltage, e.g., BZT52H-B39
C _{PWR}	0.047	μF	Value used and tested at NXP to withstand hot plug. This value must not be exceeded
R _{VPWR}	6.8	Ω	Reducing the resistance value may jeopardize the hot plug capability. Power rating is 1/10 W
C _{VP1}	220	nF	To withstand hot plug, this value must not be changed
C _{VP2}	1	nF	Ceramic capacitor
R _{LPF2}	2	kΩ	To withstand hot plug, this value should not be decreased

13.2.4 Current channel filter

The current channel may be filtered as shown in Figure 42. Example component values are given in Table 93.

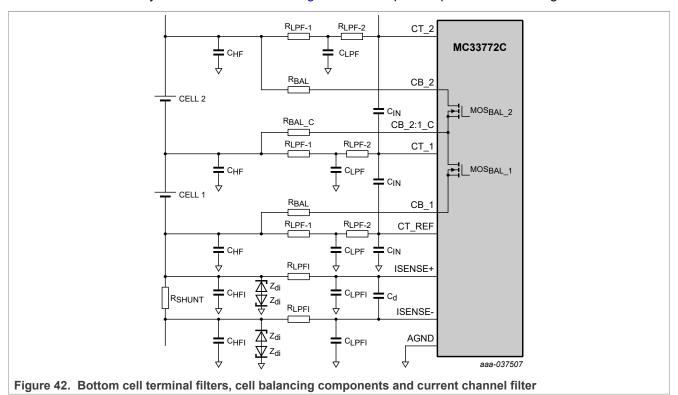


Table 93. ISENSE filter components

ID	Value	Units	Comments
C _{HFI}	47	nF	This component serves to withstand ESD gun and its value must not be changed
R _{LPFI}	127	Ω	Warning: do not exceed 200 Ω . Use 5 % tolerance. Used value is to get both f_{CUTI} = 91.8 Hz and f_{ICM} = 26.67 kHz. See Equation (13), Equation (14), Equation (16), and Equation (17)

Table 93. ISENSE filter components...continued

ID	Value	Units	Comments
C _d	6.8	μF	This example value has been chosen to get f_{CUTI} = 91.8 Hz and $t_{DIAG} \le 31.7$ ms. See Equation (13), Equation (14), and Equation (15). Use 5 % tolerance
C _{LPFI}	47	nF	Value is chosen in order to get: 91.8 Hz, $t_{DIAG} \le 31.7$ ms and $f_{ICM} = 26.67$ kHz. See Equation (13), Equation (14), Equation (15), Equation (16) and Equation (17). Use 5 % tolerance
ZDI	2.0	V	To protect during hot plug in case one of the ISENSE± pin is connected before GND of the device. Recommended MMSZ4679T1G

The signal cutoff frequency (in Hz) arrangement shown in <u>Figure 42</u> of the current channel external filter depends on the measurement time constant τ_1 given by <u>Equation (14)</u>.

$$f_{cutI} = 1/(2\pi\tau_I) \tag{13}$$

$$\tau_{I} = R_{LPFI}(C_{LPFI} + 2C_d) \tag{14}$$

The diagnostic time to detect an open from the shunt to the current filter arrangement shown in <u>Figure 42</u>, is given by:

$$t_{diag} = (C_{LPFI} + C_d) \frac{V_{ISENSE-OL} + |R_{shunt}I_{max}|}{I_{SENSE-OL}}$$
(15)

The current channel external filter arrangement shown in <u>Figure 42</u> of the common mode cutoff frequency in Hz, depends on the measurement time constant τ_{lcm} , given by the following formula, whose numeric result should be selected one detected above the signal cutoff frequency.

$$f_{Icm=1/(2\pi\tau_{Icm})} \tag{16}$$

$$\tau_{lcm} = R_{LPFI}C_{LPFI} \tag{17}$$

Above equations must be taken into account when considering the procedure described in <u>Current measurement diagnostics</u> to detect an open connection between ISENSE $_{\pm}$ and the input filter. Values for V_{ISENSE_OL} and I_{ISENSE_OL} are given in <u>Table 9</u>, values for the shunt resistance R_{SHUNT} and the maximum current I_{MAX} through it are application specific, while example values for the filter capacitors and resistors can be found in <u>Table 93</u>.

13.2.5 Temperature channels

<u>Figure 43</u> shows usage of GPIOx as analog inputs (ANx) for temperature measurements. If not used, each GPIOx may be shorted to GND.

MC33772C

Battery cell controller IC

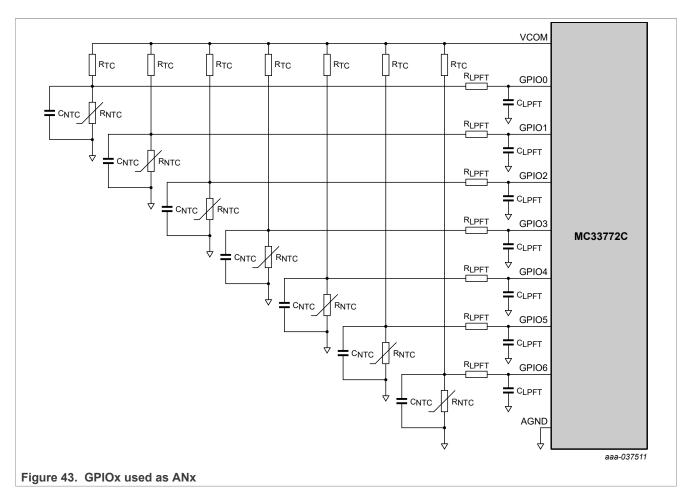


Table 94. ANx filter components

ID	Value	Units	Comments
R _{TC}	6.8	kΩ	Component with 1 % tolerance, for accurate temperature measurement. Proposed value, together with all other proposed values, gives approximately f_{CUTT} = 10 kHz. See Equation (18), Equation (19), Equation (20), and Equation (21)
R _{NTC}	10	kΩ	Nominal resistance value is given at 25 °C, tolerance must be 5 % or better
C _{NTC}	1.2	nF	This component is for ESD protection
R _{LPFT}	3.3	kΩ	Influences the channel bandwidth. See <u>Equation (18)</u> , <u>Equation (19)</u> , <u>Equation (20)</u> , and <u>Equation (21)</u>
C _{LPFT}	1.2	nF	5 % tolerance or better. Influences the channel bandwidth. See <u>Equation (18)</u> , <u>Equation (19)</u> , <u>Equation (20)</u> , and <u>Equation (21)</u>

The signal cutoff frequency (in Hz) for the arrangement shown in Figure 43 of GPIOx used as radiometric analog inputs, depends on the measurement time constant τ_T , given by the following formula. Ideally, the current channel should have the same bandwidth as cell voltage channels.

$$f_{cutT=1/(2\pi\tau_T)} \tag{18}$$

where,

All information provided in this document is subject to legal disclaimers.

© 2024 NXP B.V. All rights reserved.

Battery cell controller IC

$$\tau_{T} = \max(\tau_1, \tau_2) \tag{19}$$

$$\tau_{1} = (R_{LPFT} + (R_{TC}R_{NTC})/(R_{TC} + R_{NTC}))C_{LPFT}$$
(20)

$$\tau_{2} = C_{NTC}(R_{TC}R_{NTC}) / (R_{TC} + R_{NTC}) \tag{21}$$

In case the NTC resistor is located outside of the board and can be submitted to large EMC and ESD Gun constraints, the recommended filter for temperature is 2nd order as shown in Figure 44.

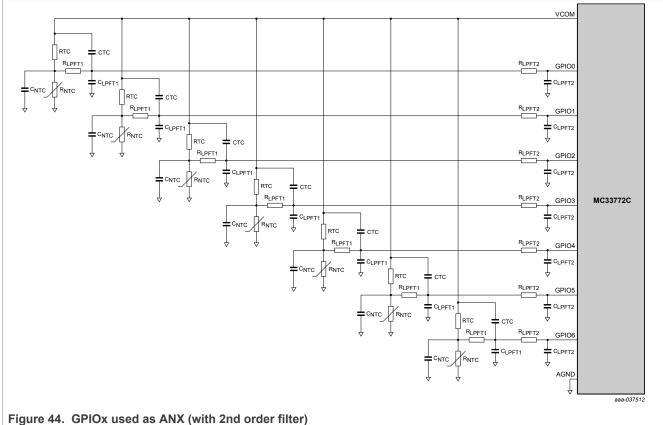


Table 95. ANx second order filter components

Table 50. And 500 mer					
ID	Value	Units	Comments		
R _{TC}	6.8	kΩ	Component with 1 % tolerance, for accurate temperature measurement		
C _{TC}	1.2	nF			
R _{NTC}	10	kΩ	Nominal resistance value is given at 25 °C, tolerance must be 5 % or better		
C _{NTC}	1.2	nF	This component is for ESD protection		
C _{LPFT1}	1.2	nF	5 % tolerance or better		
R _{LPFT1}	3.3	kΩ			

MC33772C

Table 95. ANx second order filter components...continued

ID	Value	Units	Comments	
C _{LPFT2}	1.2	nF	5 % tolerance or better	
R _{LPFT2}	3.3	kΩ		

13.2.6 Centralized applications

13.2.6.1 Centralized applications - Transformer or capacitive isolation - Master node

For capacitive isolation in a centralized system the schematic is split into two segments. The first segment displays the external component of master node as shown in <u>Figure 45</u>. The second segment displays the external components between two MC33772C ICs as shown in <u>Figure 46</u>. In high voltage system applications, a high voltage isolation transformer is recommended between master node and first slave node.

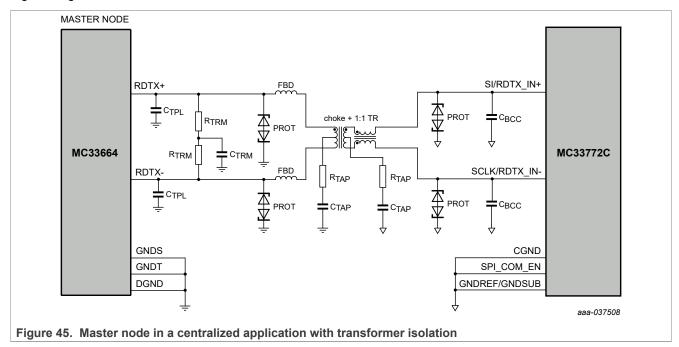


Table 96. Master node components for a centralized application with transformer or capacitive isolation

ID	Value	Units	Comments
C _{TPL}	68	pF	Ceramic capacitor
C _{TRM}	4.7	nF	Ceramic capacitor for split termination of MC33664
R _{TRM}	75	Ω	Split termination resistor for MC33664
PROT	8	V	ESD protection. Use PESD5VOV1BB or equivalent. The indicated voltage is the nominal breakdown voltage
R _{TAP}	150	Ω	Center tap resistor
C _{TAP}	10	nF	Center tap capacitor
C _{BCC}	220	pF	Ceramic capacitor
Choke +1:1 TR	Pulse Electronic HM2103	N/A	Single channel transformer with common mode choke
FBD	120	Ω	Ferrite Bead (optional). Use MMZ1608Y121BTD25 or equivalent

Battery cell controller IC

13.2.6.2 Centralized applications - Capacitive isolation - Slave node

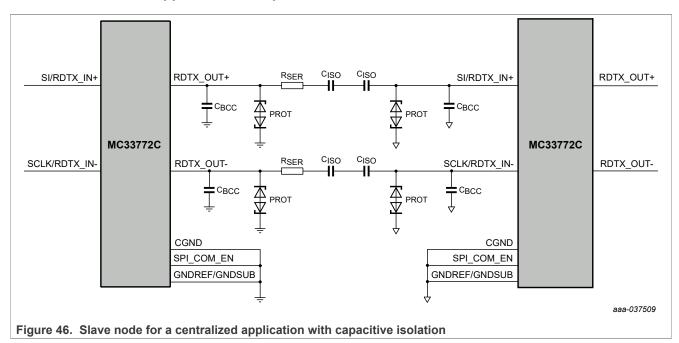


Table 97. Slave node components for a centralized application with capacitive isolation

ID	Value	Units	Comments
C _{BCC}	22	pF	Ceramic capacitor
R _{SER}	62	Ω	Series resistance
C _{ISO}	10	nF	Isolation capacitor
PROT	8	V	ESD protection. Use PESD5V0V1BB or equivalent. The indicated voltage is the nominal breakdown voltage

Battery cell controller IC

13.2.6.3 Centralized applications - Transformer isolation - Slave node

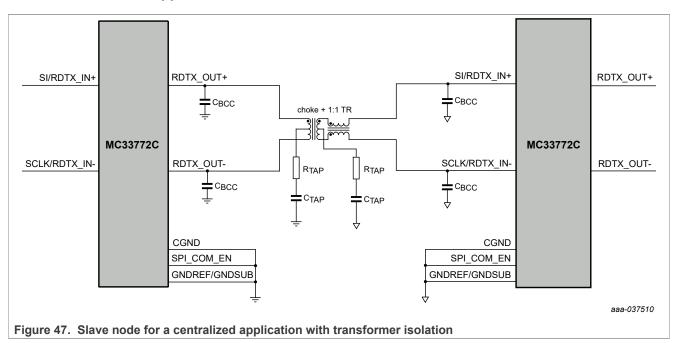


Table 98. Slave node components for a centralized application with transformer isolation

ID	Value	Units	Comments
C _{BCC}	220	pF	Ceramic capacitor
C _{TAP}	10	nF	Center tap capacitor
R _{TAP}	150	Ω	Center tap resistor

Battery cell controller IC

13.2.7 Distributed applications

13.2.7.1 Distributed systems - Master node

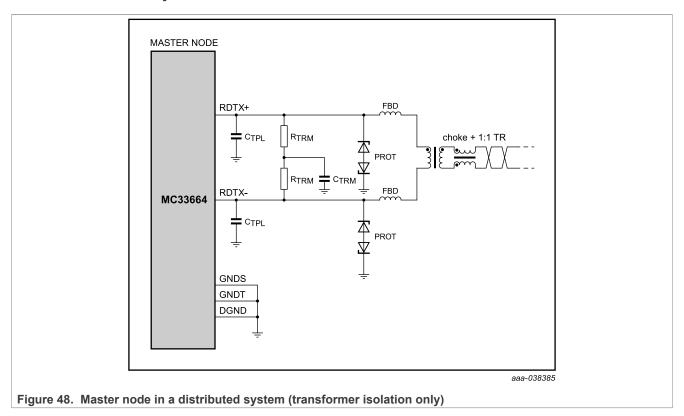


Table 99. Master node components in a distributed system

ID	Value	Units	Comments
C _{TPL}	68	pF	Ceramic capacitor
C _{TRM}	4.7	nF	Ceramic capacitor for split termination of MC33664
R _{TRM}	75	Ω	Split termination resistor for MC33664
PROT	8	V	ESD protection. Use PESD5V0V1BB or equivalent. The indicated voltage is the nominal breakdown voltage
Choke + 1:1 TR	Pulse Electronic HM2103	N/A	Single channel transformer with common mode choke
FBD	470	Ω	Ferrite Bead (optional).Use MMZ1608Q471BTD25 or equivalent

Battery cell controller IC

13.2.7.2 Distributed applications - Slave node

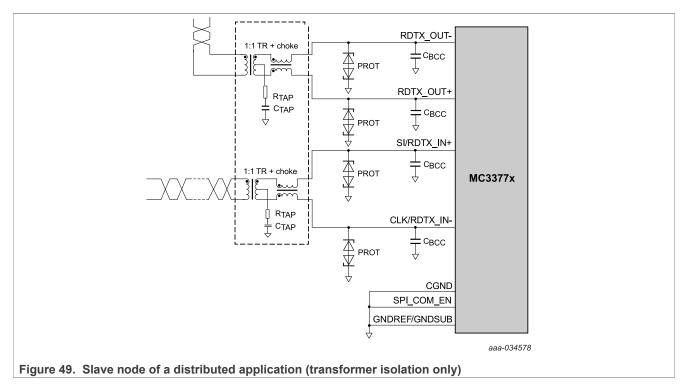


Table 100. Slave node components in a distributed application

ID	Value	Units	Comments
C _{BCC}	220	pF	Ceramic capacitor
PROT	8	V	ESD protection. Use PESD5V0V1BB or equivalent. The indicated voltage is the nominal breakdown voltage
C _{TAP}	10	nF	Center tap capacitor
R _{TAP}	150	Ω	Center tap resistor
1:1 TR + choke	PULSE Electronic HM2102	N/A	Dual channel transformer with common mode choke

14 MC33772CTx - Current Sense

14.1 MC33772CTC0AE

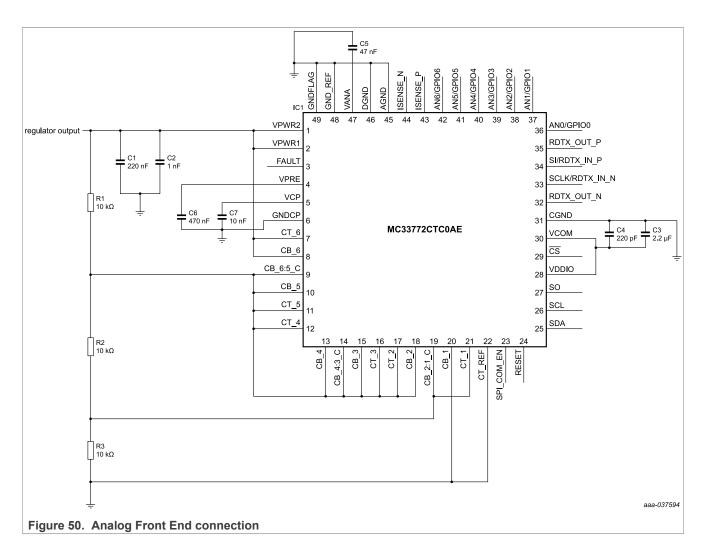
The MC33772CTC0AE part number is configured for current measurement, for instance for Battery Junction Box. It does not allow to monitor any cells, but can monitor temperatures and voltages. It can monitor the current through ISENSE ± or GPIO[5..6]. The MC33772CTC0AE can also monitor up to seven temperatures or voltages thanks to GPIO[6..0].

The MC33772CTC0AE is supporting communication through SPI or TPL. It requires a specific application schematic to connect the Analog Front End as the device will not monitor cells, so cannot be directly supplied from them.

The input voltage has to be 6 V minimum for SPI communication and 7 V minimum for TPL communication. For settings of Analog Front End, refer to Figure 50. For settings of the Current channel using ISENSE ± or GPIO[5..6], refer to ISENSE ± connection of Figure 42.

MC33772C

Battery cell controller IC



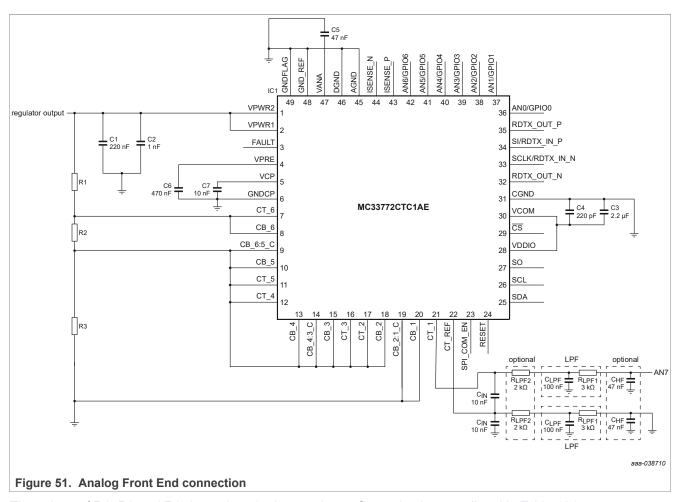
14.2 MC33772CTC1AE

The MC33772CTC1AE part number is configured for current measurement, for instance for Battery Junction Box. It does not allow to monitor any cells, but can monitor temperatures and voltages. It can monitor the current through ISENSE ± or GPIO[5..6]. The MC33772CTC1AE can also monitor up to eight temperatures or voltages thanks to GPIO[6..0] and CT 1.

The MC33772CTC1AE is supporting communication through SPI or TPL. It requires a specific application schematic to connect the Analog Front End as the device will not monitor cells, so cannot be directly supplied from them.

For settings of Analog Front End, refer to Figure 51. For settings of the Current channel using ISENSE ± or GPIO[5..6], refer to ISENSE ± connection of Figure 42.

Battery cell controller IC



The values of R1, R2 and R3 depend on the input voltage. Several values are listed in Table 101.

Table 101. Example of resistors value depending on application

Input voltage	R1	R2	R3
7 V	1 kΩ	18 kΩ	47 kΩ
12 V	4.7 kΩ	47 kΩ	47 kΩ

15 Packaging

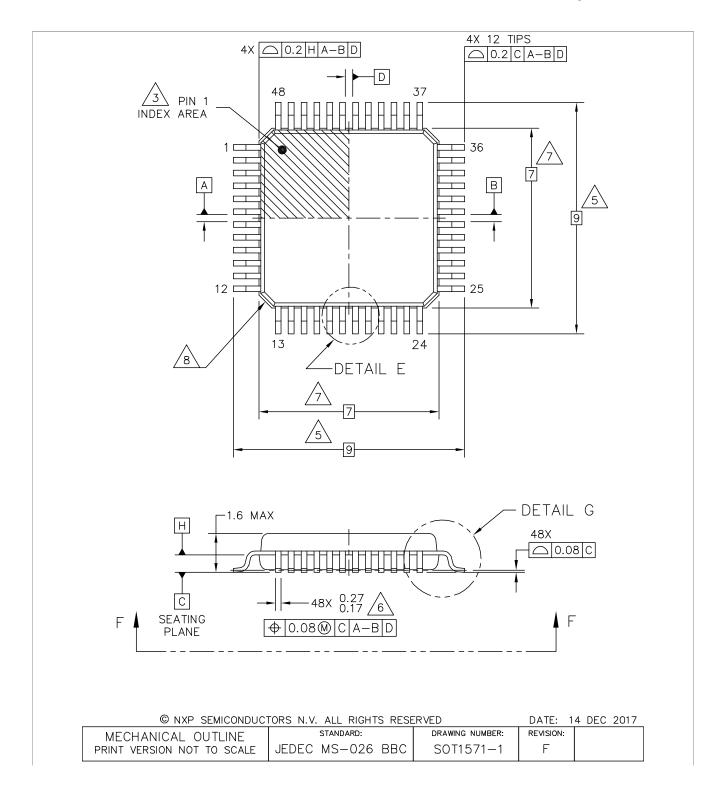
15.1 Package mechanical dimensions

Package dimensions are provided in package drawings. To find the most current package outline drawing, go to www.nxp.com and perform a keyword search for the document number of the drawings.

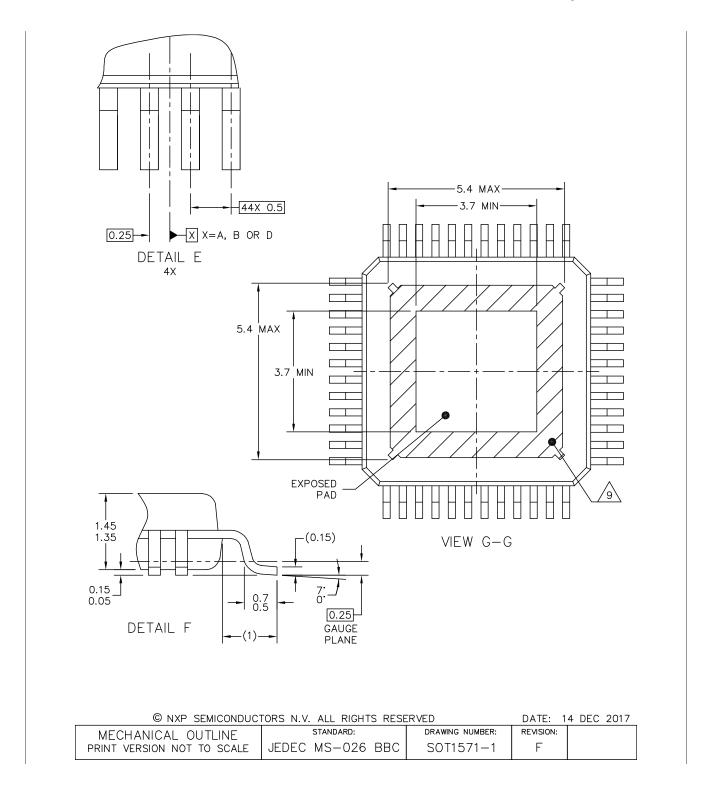
Table 102. Package Outline

Package	Suffix	Package outline drawing number
48-pin LQFP-EP	AE	SOT1571-1

Battery cell controller IC



Battery cell controller IC



Battery cell controller IC

NOTES:

- 1. DIMENSIONS ARE IN MILLIMETERS.
- 2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- 3. PIN 1 FEATURE SHAPE, SIZE AND LOCATION MAY VARY.
- 4. DATUMS A, B AND D TO BE DETERMINED AT DATUM PLANE H.
- 5. DIMENSION TO BE DETERMINED AT SEATING PLANE C.
- THIS DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED THE UPPER LIMIT BY MORE THAN 0.08MM AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD SHALL NOT BE LESS THAN 0.07MM.
- THIS DIMENSION DOES NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25MM PER SIDE. THIS DIMENSION IS MAXIMUM PLASTIC BODY SIZE DIMENSION INCLUDING MOLD MISMATCH.
- & EXACT SHAPE OF EACH CORNER IS OPTIONAL.
- A HATCHED AREA TO BE KEEP OUT ZONE FOR PCB ROUTING.

© NXP SEMICONDUCTORS N.V. ALL RIGHTS RESERVED DATE: 14 DEC 2017						
MECHANICAL OUTLINE	STANDARD:	DRAWING NUMBER:	REVISION:			
PRINT VERSION NOT TO SCALE	JEDEC MS-026 BBC	SOT1571-1	F			

Figure 52. Package outline

16 Revision history

Table 103. Revision history

Document ID	Release date	Description
MC33772C v.4.0	16 July 2024	 Product data sheet Supersedes MC33772C v.3.0 Updated status from confidential to public Updated Revision history and <u>Legal information</u> to confirm with updated NXP standards
MC33772C v.3.0	04 June 2021	 Product data sheet Supersedes MC33772C v.2.0 Section 8.4, Table 9 Changed V_{ANX_RATIO_RES} typical value from VCOM * (30. 5176) to VCOM × 30.51758 Updated min and max for parameter ADC1a_{FV}, ADC1b_{FV} from -6.66 mV to -5 mV and from 6.66 mV to 5 mV Added footnote 15 to parameters V_{IH}, V_{IL} and V_{HYS} regarding use of GPIO0 as wake-up Updated duration of HTOL in footnote 9 Added footnote 22 to t_{TPL_TD} Added footnote 25 to t_{RES} Removed parameters VERR33RT and VERR33RTA Section 9.11: Modified list item number 2 and changed order of paragraphs Section 10.4.1: Removed part of a sentence concerning content of the data field described in Table 25 Section 11.18: Modified description of GPIOx_DR Section 11.24: Added part to description of value 1 for bit RESET_FLT Section 11.24 and Section 11.25 Modified list of bits marked * Added new mark ** Section 11.47, Table 88: Modified table content Section 14.2, Figure 51: Changed coloring of R_{LPF2} resistors Several minor typo corrections throughout the document
MC33772C v.2.0	10 March 2021	Preliminary data sheetSupersedes MC33772C v.1.0
MC33772C v.1.0	25 August 2020	Preliminary data sheet Initial release

Table 104. Revision history

Full revision history available on request

Document ID	Release date	Data sheet status	Change notice	Supersedes		
MC33772C v.3	20210604	Product data sheet	_	MC33772C v.2.0		
Modifications:	 Section 8.4, Table 9 Changed V_{ANX_RATIO_RES} typical value from VCOM * (30.5176) to VCOM × 30.51758 Updated min and max for parameter ADC1a_{FV}, ADC1b_{FV} from -6.66 mV to -5 mV and from 6.66 mV to 5 mV Added footnote 15 to parameters V_{IH}, V_{IL} and V_{HYS} regarding use of GPIO0 as wake-up 					

Battery cell controller IC

Table 104. Revision history...continued

Full revision history available on request

Document ID	Release date	Data sheet status	Change notice	Supersedes					
	 Updated duration 	- Updated duration of HTOL in footnote 9							
	 Added footnote 	- Added footnote 22 to t _{TPL TD}							
	 Added footnote 	 Added footnote 25 to t_{RES} Removed parameters VERR33RT and VERR33RTA Section 9.11: Modified list item number 2 and changed order of paragraphs 							
	- Removed para								
	• <u>Section 9.11</u> : Mod								
	• <u>Section 10.4.1</u> : R	• Section 10.4.1: Removed part of a sentence concerning content of the data field described in Table 25							
	 Section 11.18: Modified description of GPIOx_DR Section 11.24: Added part to description of value 1 for bit RESET_FLT Section 11.24 and Section 11.25 – Modified list of bits marked * – Added new mark ** Section 11.47, Table 88: Modified table content Section 14.2, Figure 51: Changed coloring of R_{LPF2} resistors 								
1									
	Several minor typ	Several minor typo corrections throughout the document							
MC33772C v.2.0	20210310	Preliminary	_	MC33772C v.1.0					
MC33772C v.1.0	20200825	Preliminary	_	_					

Legal information

Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL https://www.nxp.com.

Definitions

Draft — A draft status on a document indicates that the content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included in a draft version of a document and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the Terms and conditions of commercial sale of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at https://www.nxp.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

MC33772C

All information provided in this document is subject to legal disclaimers.

© 2024 NXP B.V. All rights reserved.

Battery cell controller IC

Suitability for use in automotive applications — This NXP product has been qualified for use in automotive applications. If this product is used by customer in the development of, or for incorporation into, products or services (a) used in safety critical applications or (b) in which failure could lead to death, personal injury, or severe physical or environmental damage (such products and services hereinafter referred to as "Critical Applications"), then customer makes the ultimate design decisions regarding its products and is solely responsible for compliance with all legal, regulatory, safety, and security related requirements concerning its products, regardless of any information or support that may be provided by NXP. As such, customer assumes all risk related to use of any products in Critical Applications and NXP and its suppliers shall not be liable for any such use by customer. Accordingly, customer will indemnify and hold NXP harmless from any claims, liabilities, damages and associated costs and expenses (including attorneys' fees) that NXP may incur related to customer's incorporation of any product in a Critical Application.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Translations — A non-English (translated) version of a document, including the legal information in that document, is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

Security — Customer understands that all NXP products may be subject to unidentified vulnerabilities or may support established security standards or specifications with known limitations. Customer is responsible for the design and operation of its applications and products throughout their lifecycles to reduce the effect of these vulnerabilities on customer's applications and products. Customer's responsibility also extends to other open and/or proprietary technologies supported by NXP products for use in customer's applications. NXP accepts no liability for any vulnerability. Customer should regularly check security updates from NXP and follow up appropriately. Customer shall select products with security features that best meet rules, regulations, and standards of the intended application and make the ultimate design decisions regarding its products and is solely responsible for compliance with all legal, regulatory, and security related requirements concerning its products, regardless of any information or support that may be provided by NXP.

NXP has a Product Security Incident Response Team (PSIRT) (reachable at PSIRT@nxp.com) that manages the investigation, reporting, and solution release to security vulnerabilities of NXP products.

NXP B.V. — NXP B.V. is not an operating company and it does not distribute or sell products.

Trademarks

Notice: All referenced brands, product names, service names, and trademarks are the property of their respective owners.

NXP — wordmark and logo are trademarks of NXP B.V.

Tables

Tab. 1.	Part number breakdown	4	Tab. 51.	CB SHORT FLT	81
Tab. 1.	Advanced orderable part table		Tab. 51.	CB_DRV_STS	
Tab. 3.	Premium orderable part table		Tab. 52.	GPIO_CFG1	
Tab. 4.	Current orderable part table		Tab. 54.	GPIO_CFG2	
Tab. 5.	Pin definitions		Tab. 55.	GPIO_STS	
Tab. 6.	Ratings vs. operating requirements		Tab. 56.	AN OT UT FLT	
Tab. 7.			Tab. 50.	GPIO_SHORT_ANX_OPEN_STS	
Tab. 7.	Maximum ratings		Tab. 57.	I_STATUS	
Tab. 9.	Thermal ratingsStatic and dynamic electrical	11	Tab. 56.	COM_STATUS	
1ab. 9.	characteristics	10		FAULT1_STATUS	
Tab 10			Tab. 60.	FAULT2 STATUS	
Tab. 10.	Working mode versus measurements	25	Tab. 61.	-	
Tab. 11.	Recommended capacitor values for power	00	Tab. 62.	FAULT3_STATUS	
T-h 10	supply decoupling		Tab. 63.	FAULT_MASK1	
Tab. 12.	Power supply mode operation	29	Tab. 64.	FAULT_MASK2	
Tab. 13.	ADC conversion sequence multiplexer	00	Tab. 65.	FAULT_MASK3	
T 1 44	inputs		Tab. 66.	WAKEUP_MASK1	
Tab. 14.	Gain compensation		Tab. 67.	WAKEUP_MASK2	
Tab. 15.	Gain format		Tab. 68.	WAKEUP_MASK3	
Tab. 16.	GPIO port configurations		Tab. 69.	CC_NB_SAMPLES	
Tab. 17.	Sequence of read operations		Tab. 70.	COULOMB_CNT1	
Tab. 18.	Sequence of write operations		Tab. 71.	COULOMB_CNT2	
Tab. 19.	SPI command format		Tab. 72.	MEAS_ISENSE1	
Tab. 20.	SPI response format		Tab. 73.	MEAS_ISENSE2	
Tab. 21.	TPL encoding		Tab. 74.	MEAS_xxxx	
Tab. 22.	Data preparation for CRC encoding		Tab. 75.	TH_ALL_CT	
Tab. 23.	Command CRC calculation examples	61	Tab. 76.	TH_CTx	
Tab. 24.	Response CRC calculation examples		Tab. 77.	TH_ANx_OT	
Tab. 25.	Read command table		Tab. 78.	TH_ANx_UT	
Tab. 26.	Read response table	62	Tab. 79.	TH_ISENSE_OC	94
Tab. 27.	Legend for read command, read response		Tab. 80.	TH_COULOMB_CNT_MSB	94
	tables	62	Tab. 81.	TH_COULOMB_CNT_LSB	94
Tab. 28.	Write command table	63	Tab. 82.	SILICON_REV	95
Tab. 29.	Legend for write command and write		Tab. 83.	EEPROM_CTRL	95
	response tables		Tab. 84.	DED_ENCODE1	96
Tab. 30.	Global write command table	63	Tab. 85.	DED_ENCODE2	96
Tab. 31.	Legend for global write command table	64	Tab. 86.	FUSE_MIRROR_DATA	96
Tab. 32.	No operation command table	64	Tab. 87.	FUSE_MIRROR_CNTL	96
Tab. 33.	Legend for no operation command and no		Tab. 88.	RESERVED	97
	operation response tables	64	Tab. 89.	FUSE_BANK	97
Tab. 34.	Command summary table	65	Tab. 90.	CT filter components	103
Tab. 35.	Response summary table	65	Tab. 91.	Stacked cells	104
Tab. 36.	Register table	66	Tab. 92.	Components to avoid hot plug issues	107
Tab. 37.	Mirror memory	70	Tab. 93.	ISENSE filter components	107
Tab. 38.	INIT	72	Tab. 94.	ANx filter components	109
Tab. 39.	SYS_CFG_GLOBAL	72	Tab. 95.	ANx second order filter components	
Tab. 40.	SYS_CFG1		Tab. 96.	Master node components for a centralized	
Tab. 41.	SYS_CFG2			application with transformer or capacitive	
Tab. 42.	SYS DIAG			isolation	111
Tab. 43.	ADC_CFG	76	Tab. 97.	Slave node components for a centralized	
Tab. 44.	ADC2_OFFSET_COMP			application with capacitive isolation	112
Tab. 45.	OV UV EN		Tab. 98.	Slave node components for a centralized	
Tab. 46.	CELL_OV_FLT			application with transformer isolation	113
Tab. 47.	CELL_UV_FLT		Tab. 99.	Master node components in a distributed	
Tab. 48.	TPL CFG			system	114
Tab. 49.	CBx CFG		Tab. 100.	Slave node components in a distributed	
Tab. 50.	CB_OPEN_FLT			application	115
				• •	_

Battery cell controller IC

Tab. 101.	Example of resistors value depending on application	117		Revision history	
Tab. 102.	Package Outline		100. 101.	To	
Figur	es				
Fig. 1.	Simplified application diagram, SPI use		Fig. 31.	Command and response mode – example	
	case	2		CRC encoder	
Fig. 2.	Simplified application diagram, TPL use case	3	Fig. 32. Fig. 33.	MC33772C calibration registers Centralized battery monitoring system with	66
Fig. 3.	Simplified internal block diagram		J	capacitive isolation	99
Fig. 4.	Pinout diagram		Fig. 34.	Centralized battery monitoring system with	
Fig. 5.	Low-voltage SPI interface timing		J	transformer isolation	.100
Fig. 6.	Transformer communication signaling		Fig. 35.	Distributed battery monitoring system	
Fig. 7.	Recommended decoupling of power		Fig. 36.	Example of multiple daisy chain	
ŭ	supplies	26	Fig. 37.	Example of loop-back daisy chain	
Fig. 8.	Operating mode state diagram		Fig. 38.	Second order cell terminal filters and cell	
Fig. 9.	ADC converter: incremental phase (left)		J	balancing resistors (internal cell balancing	
Ū	and cyclic phase (right)	32		MOSFETs are shown for clarity)	103
Fig. 10.	ADC conversion sequence in normal mode		Fig. 39.	LPF block masking	
Fig. 11.	ADC1-A voltage measurement chain		Fig. 40.	The three cell configuration	.105
Fig. 12.	Current measurement channel		Fig. 41.	Top cell terminal filters and balancing	
Fig. 13.	Current measurement channel (gain vs.		· ·	resistors, VPWR1, 2 components to	
	input signal amplitude)	38		withstand hot plug	.106
Fig. 14.	Coulomb counter different behaviors		Fig. 42.	Bottom cell terminal filters, cell balancing	
Fig. 15.	GPIO internal input structure	44		components and current channel filter	107
Fig. 16.	Heartbeat daisy chain	46	Fig. 43.	GPIOx used as ANx	.109
Fig. 17.	Memories		Fig. 44.	GPIOx used as ANX (with 2nd order filter)	110
Fig. 18.	Mirror memory control	50	Fig. 45.	Master node in a centralized application	
Fig. 19.	SPI interface termination	52		with transformer isolation	111
Fig. 20.	SPI transmission	54	Fig. 46.	Slave node for a centralized application	
Fig. 21.	TPL Pulses	55		with capacitive isolation	.112
Fig. 22.	SOM	55	Fig. 47.	Slave node for a centralized application	
Fig. 23.	EOM	55		with transformer isolation	113
Fig. 24.	Logic 1	56	Fig. 48.	Master node in a distributed system	
Fig. 25.	Logic 0	56		(transformer isolation only)	.114
Fig. 26.	Bus traffic example	57	Fig. 49.	Slave node of a distributed application	
Fig. 27.	Bus traffic with receive error and recovery			(transformer isolation only)	.115
Fig. 28.	Transformer communication waveforms	58	Fig. 50.	Analog Front End connection	.116
Fig. 29.	MC33772C system wake-up	58	Fig. 51.	Analog Front End connection	.117
Fig. 30.	Pack controller system wake-up	59	Fig. 52.	Package outline	.118

Contents

1	General description	1	9.10	Internal IC temperature	47
2	Features		9.11	Internal temperature fault	
3	Simplified application diagram	2	9.12	Storage of parameters in an optional	
4	Applications			EEPROM	48
5	Ordering information		9.12.1	Error Correction Code (ECC)	
5.1	Part numbers definition		9.12.2	Mirror memory	
5.2	Part numbers list		9.12.3	Optional EEPROM	
6	Block diagram		10	Communication	
7	Pinning information		10.1	SPI communication	
7.1	Pinout diagram		10.2	TPL communication	
7.2	Pin definitions		10.2.1	TPL Encoding	
8	General product characteristics		10.2.2	Command message bit order	
8.1	Ratings and operating requirements		10.2.3	Response message bit order	
0.1	relationship	a	10.2.4	Transformer communication format	
8.2	Maximum ratings		10.2.5	Transformer communication timing	
8.3	Thermal characteristics		10.2.6	Transformer communication wake-up	
8.4	Electrical characteristics		10.2.6.1	MC33772C System wake-up	
8.5	Timing diagrams		10.2.6.1		
9	Functional description		10.2.0.2	Pack controller system wake-up CRC generation	
9.1			10.3	Commands	
	Introduction Power supplies and reset				
9.2			10.4.1	Read command and response	
9.2.1	Decoupling of power supplies		10.4.2	Local write command	
9.2.2	VPWR overvoltage, low-voltage		10.4.3	Global write command	
9.2.3	VCOM supply		10.4.4	No operation command	
9.2.4	VANA supply		10.4.5	Command and response summary	
9.2.5	VPRE supply		10.5	I2C communication interface	
9.2.6	VCP supply	27	11	Registers	
9.2.7	VDDIO supply	27	11.1	Register map	
9.2.8	Power on reset (POR)		11.2	Initialization register – INIT	71
9.2.9	Hardware and software reset		11.3	System configuration global register SYS_	
9.3	Modes of operation			CFG_GLOBAL	72
9.3.1	Reset mode		11.4	System configuration register 1 – SYS_	
9.3.2	Idle mode	30		CFG1	72
9.3.3	Init mode	30	11.5	System configuration register 2 – SYS_	
9.3.4	Normal mode			CFG2	
9.3.5	Sleep mode		11.6	System diagnostics register – SYS_DIAG	
9.3.6	Diagnostic mode	31	11.7	ADC configuration register – ADC_CFG	76
9.4	Analog to digital converters ADC1-A,		11.8	Current measurement chain offset	
	ADC1-B, ADC2	31		compensation - ADC2_OFFSET_COMP	77
9.4.1	High precision voltage reference	32	11.9	Cell select register – OV_UV_EN	78
9.4.2	Measurement sequence	32	11.10	Cell terminal overvoltage fault register –	
9.4.2.1	Voltage averaging	34		CELL_OV_FLT	79
9.4.3	Measurement processing	34	11.11	Cell terminal undervoltage fault register –	
9.5	Cell terminal voltage measurement			CELL_UV_FLT	79
9.6	Current measurement		11.12	TPL register – TPL CFG	
9.6.1	Gain correction of the current channel	39	11.13	Cell balance configuration register – CBx_	
9.7	Coulomb counting			CFG	80
9.8	GPIOx port control and diagnostics		11.14	Cell balance open load fault detection	
9.8.1	GPIOx used as digital I/O			register – CB_OPEN_FLT	80
9.8.2	GPIO0 used as wake-up input or fault pin		11.15	Cell balance shorted load fault detection	
<u>-</u>	activation input	45		register – CB_SHORT_FLT	81
9.8.3	FAULT pin daisy chain operation		11.16	Cell balance driver on/off status register –	• '
9.8.4	GPIO2 used as ADC trigger			CB DRV STS	81
9.8.5	GPIOx used as analog		11.17	GPIO configuration register 1 – GPIO_	01
9.8.6	GPIO5, GPIO6 used as ISENSE		11.17	CFG1	Ω1
9.9	Cell balance control			O. O	01
J.J	Ocii Dalalioe Colliioi	+ <i>1</i>			

NXP Semiconductors

MC33772C

Battery cell controller IC

11.18	GPIO configuration register 2 – GPIO_
	CFG282
11.19	GPIO status register – GPIO_STS82
11.20	Overtemperature/undertemperature fault
	register – AN_OT_UT_FLT82
11.21	GPIO open short register – GPIO_SHORT_
11.21	ANX_OPEN_STS83
11.22	Current measurement status register – I_
11.22	STATUS
44.00	
11.23	Communication status register – COM_
	STATUS 83
11.24	Fault status register 1 – FAULT1_STATUS 84
11.25	Fault status register 2 – FAULT2_STATUS 86
11.26	Fault status register 3 – FAULT3_STATUS 88
11.27	Fault mask register 1 – FAULT_MASK1 88
11.28	Fault mask register 2 – FAULT MASK2 88
11.29	Fault mask register 3 – FAULT MASK3 89
11.30	Wake-up mask register 1 – WAKEUP_
	MASK189
11.31	Wake-up mask register 2 – WAKEUP_
11.51	MASK290
11.32	Wake-up mask register 3 – WAKEUP_
11.32	
44.00	MASK390
11.33	Coulomb count number of samples register
44.04	- CC_NB_SAMPLES90
11.34	Coulomb count register – COULOMB_CNT 90
11.35	Current measurement registers – MEAS_
	ISENSE1 and MEAS_ISENSE291
11.36	Measurement registers – MEAS_xxxx92
11.37	Overvoltage undervoltage threshold
	register – TH_ALL_CT93
11.38	Overvoltage undervoltage threshold
	register – TH_CTx93
11.39	Overtemperature, undertemperature
	threshold registers – TH_ANx_OT, TH_
	ANx UT
11.40	Overcurrent threshold register – TH_
	ISENSE OC
11.41	Over coulomb counter threshold registers –
	TH COULOMB CNT94
11.42	Silicon revision register – SILICON REV 95
11.43	EEPROM communication register -
11.40	EEPROM_CTRL95
11.44	ECC signature 1 register96
11.44	
	ECC signature 2 register
11.46	FUSE mirror and data control96
11.47	Reserved97
11.48	Fuse bank97
12	Safety 98
12.1	Safety features
13	Typical applications98
13.1	Introduction
13.1.1	Centralized battery management system 98
13.1.2	Distributed battery management system100
13.1.3	Multiple daisy chain101
13.1.4	Loop-Back daisy chain 102

13.2	MC33772C External Components	102
13.2.1	Cell terminal filters	102
13.2.2	Unused cells	104
13.2.3	Hot plug protection	106
13.2.4	Current channel filter	107
13.2.5	Temperature channels	108
13.2.6	Centralized applications	111
13.2.6.1	Centralized applications - Transformer or	
	capacitive isolation - Master node	111
13.2.6.2	Centralized applications - Capacitive	
	isolation - Slave node	112
13.2.6.3	Centralized applications - Transformer	
	isolation - Slave node	113
13.2.7	Distributed applications	
13.2.7.1	Distributed systems - Master node	
13.2.7.2	Distributed applications - Slave node	115
14	MC33772CTx - Current Sense	115
14.1	MC33772CTC0AE	115
14.2	MC33772CTC1AE	116
15	Packaging	
15.1	Package mechanical dimensions	117
16	Revision history	121
	Legal information	123

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

Document feedback